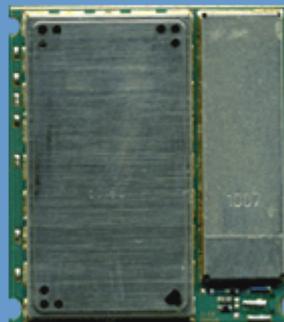




CINTERION
WIRELESS MODULES

EES3

Version: 01.100b
DocId: EES3_HD_v01.100b



Hardware Interface Description

Document Name: **EES3 Hardware Interface Description**

Version: **01.100b**

Date: **2009-08-12**

DocId: **EES3_HD_v01.100b**

Status: **Confidential / Released**

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0 Document History

Preceding document: "EES3 Hardware Interface Description" Version 01.100a

New document: "EES3 Hardware Interface Description" Version **01.100b**

Chapter	What is new
3.3.1.1	Removed URC "Shutdown after Illegal Powerup".
3.3.2	Table 8 : Changed values of PU = Pull up: typ. -200 μ A and max. -350 μ A
3.10	Added remark on bit rate tolerance for autobauding.
5.2	Table 22 : Removed line on automatic shutdown.

Preceding document: "EES3 Hardware Interface Description" Version 01.100

New document: "EES3 Hardware Interface Description" Version 01.100a

Chapter	What is new
3.3 , 3.3.1.6 , 5.5	Revised timing for EMERG_OFF signal throughout document.
4	Slightly revised chapter.
5.2	Added remark on deferred shutdown during emergency calls.
5.5	Corrected VCHARGE properties: $V_{I,max} = 7.0V$

Preceding document: "EES3 Hardware Interface Description" Version 01.000

New document: "EES3 Hardware Interface Description" Version 01.100

Chapter	What is new
3.3.2	Corrected defined state for DSR0 to O,L (see Table 8).
5.3	Corrected storage conditions (see Table 24).

New document: "EES3 Hardware Interface Description" Version 01.000

Chapter	What is new
--	Initial document setup.

1 Introduction

This document¹ describes the hardware of the Cinterion EES3 module that connects to the cellular device application and the air interface. It helps you quickly retrieve interface specifications, electrical and mechanical details and information on the requirements to be considered for integrating further components.

1.1 Related Documents

- [1] EES3 AT Command Set
- [2] EES3 Release Note
- [3] DSB75 Support Box - Evaluation Kit for Cinterion Wireless Modules
- [4] Application Note 02: Audio Interface Design for GSM Applications
- [5] Application Note 07: Rechargeable Lithium Batteries in GSM Applications
- [6] Application Note 16: Updating Firmware
- [7] Application Note 22: Using TTY / CTM Equipment
- [8] Application Note 24: Application Developer's Guide
- [9] Application Note 26: Power Supply Design for Wireless Applications
- [10] Application Note 32: Integrating USB into GSM Applications
- [11] Application Note 48: SMT Module Integration
- [12] Multiplexer User's Guide
- [13] Multiplex Driver Developer's Guide
- [14] Multiplexer Driver Installation Guide
- [15] Remote SAT User's Guide

1.2 Terms and Abbreviations

Abbreviation	Description
ADC	Analog-to-Digital Converter
AGC	Automatic Gain Control
ANSI	American National Standards Institute
ARFCN	Absolute Radio Frequency Channel Number
ARP	Antenna Reference Point
ASC0 / ASC1	Asynchronous Controller. Abbreviations used for first and second serial interface of EES3
B	Thermistor Constant
BER	Bit Error Rate
BTS	Base Transceiver Station
CB or CBM	Cell Broadcast Message
CE	Conformité Européene (European Conformity)
CHAP	Challenge Handshake Authentication Protocol

1. The document is effective only if listed in the appropriate Release Notes as part of the technical documentation delivered with your Cinterion product.

Abbreviation	Description
CPU	Central Processing Unit
CS	Coding Scheme
CSD	Circuit Switched Data
CTS	Clear to Send
DAC	Digital-to-Analog Converter
DAI	Digital Audio Interface
dBm0	Digital level, 3.14dBm0 corresponds to full scale, see ITU G.711, A-law
DCE	Data Communication Equipment (typically modems, e.g. Cinterion GSM module)
DCS 1800	Digital Cellular System, also referred to as PCN
DRX	Discontinuous Reception
DSB	Development Support Box
DSP	Digital Signal Processor
DSR	Data Set Ready
DTE	Data Terminal Equipment (typically computer, terminal, printer or, for example, GSM application)
DTR	Data Terminal Ready
DTX	Discontinuous Transmission
EFR	Enhanced Full Rate
EGSM	Enhanced GSM
EIRP	Equivalent Isotropic Radiated Power
EMC	Electromagnetic Compatibility
ERP	Effective Radiated Power
ESD	Electrostatic Discharge
ETS	European Telecommunication Standard
FCC	Federal Communications Commission (U.S.)
FDMA	Frequency Division Multiple Access
FR	Full Rate
GMSK	Gaussian Minimum Shift Keying
GPIO	General Purpose Input/Output
GPRS	General Packet Radio Service
GSM	Global Standard for Mobile Communications
HiZ	High Impedance
HR	Half Rate
I/O	Input/Output
IC	Integrated Circuit
IMEI	International Mobile Equipment Identity
ISO	International Standards Organization
ITU	International Telecommunications Union

Abbreviation	Description
kbps	kbits per second
LED	Light Emitting Diode
Li-Ion / Li+	Lithium-Ion
Li battery	Rechargeable Lithium Ion or Lithium Polymer battery
Mbps	Mbits per second
MMI	Man Machine Interface
MO	Mobile Originated
MS	Mobile Station (GSM module), also referred to as TE
MSISDN	Mobile Station International ISDN number
MT	Mobile Terminated
NTC	Negative Temperature Coefficient
OEM	Original Equipment Manufacturer
PA	Power Amplifier
PAP	Password Authentication Protocol
PBCCH	Packet Switched Broadcast Control Channel
PCB	Printed Circuit Board
PCL	Power Control Level
PCM	Pulse Code Modulation
PCN	Personal Communications Network, also referred to as DCS 1800
PCS	Personal Communication System, also referred to as GSM 1900
PDU	Protocol Data Unit
PLL	Phase Locked Loop
PPP	Point-to-point protocol
PSK	Phase Shift Keying
PSU	Power Supply Unit
PWM	Pulse Width Modulation
R&TTE	Radio and Telecommunication Terminal Equipment
RAM	Random Access Memory
RF	Radio Frequency
RMS	Root Mean Square (value)
RoHS	Restriction of the use of certain hazardous substances in electrical and electronic equipment.
ROM	Read-only Memory
RTC	Real Time Clock
RTS	Request to Send
Rx	Receive Direction
SAR	Specific Absorption Rate
SELV	Safety Extra Low Voltage

Abbreviation	Description
SIM	Subscriber Identification Module
SMD	Surface Mount Device
SMS	Short Message Service
SMT	Surface Mount Technology
SPI	Serial Peripheral Interface
SRAM	Static Random Access Memory
TA	Terminal adapter (e.g. GSM module)
TDMA	Time Division Multiple Access
TE	Terminal Equipment, also referred to as DTE
Tx	Transmit Direction
UART	Universal asynchronous receiver-transmitter
URC	Unsolicited Result Code
USB	Universal Serial Bus
USSD	Unstructured Supplementary Service Data
VSWR	Voltage Standing Wave Ratio

1.3 Regulatory and Type Approval Information

1.3.1 Directives and Standards

EES3 is designed to comply with the directives and standards listed below.

It is the responsibility of the application manufacturer to ensure compliance of the final product with all provisions of the applicable directives and standards as well as with the technical specifications provided in the "EES3 Hardware Interface Description".¹

Table 1: Directives

99/05/EC	Directive of the European Parliament and of the council of 9 March 1999 on radio equipment and telecommunications terminal equipment and the mutual recognition of their conformity (in short referred to as R&TTE Directive 1999/5/EC). The product is labeled with the CE conformity mark CE 0682
2002/95/EC	Directive of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS) 

Table 2: Standards of North American type approval

CFR Title 47	Code of Federal Regulations, Part 22 and Part 24 (Telecommunications, PCS); US Equipment Authorization FCC
UL 60 950	Product Safety Certification (Safety requirements) 
NAPRD.03 V3.13	Overview of PCS Type certification review board Mobile Equipment Type Certification and IMEI control PCS Type Certification Review board (PTCRB)
RSS133 (Issue2)	Canadian Standard

Table 3: Standards of European type approval

3GPP TS 51.010-1	Digital cellular telecommunications system (Phase 2); Mobile Station (MS) conformance specification
ETSI EN 301 511 V9.0.2	Candidate Harmonized European Standard (Telecommunications series) Global System for Mobile communications (GSM); Harmonized standard for mobile stations in the GSM 900 and DCS 1800 bands covering essential requirements under article 3.2 of the R&TTE directive (1999/5/EC) (GSM 13.11 version 7.0.1 Release 1998)
GCF-CC V3.28	Global Certification Forum - Certification Criteria
ETSI EN 301 489-1 V1.4.1	Candidate Harmonized European Standard (Telecommunications series) Electro Magnetic Compatibility and Radio spectrum Matters (ERM); Electro Magnetic Compatibility (EMC) standard for radio equipment and services; Part 1: Common Technical Requirements

1. Manufacturers of applications which can be used in the US shall ensure that their applications have a PTCRB approval. For this purpose they can refer to the PTCRB approval of the respective module.

Table 3: Standards of European type approval

ETSI EN 301 489-7 V1.2.1 (2000-09)	Candidate Harmonized European Standard (Telecommunications series) Electro Magnetic Compatibility and Radio spectrum Matters (ERM); Electro Magnetic Compatibility (EMC) standard for radio equipment and services; Part 7: Specific conditions for mobile and portable radio and ancillary equipment of digital cellular radio telecommunications systems (GSM and DCS)
IEC/EN 60950-1 (2001)	Safety of information technology equipment (2000)

Table 4: Requirements of quality

IEC 60068	Environmental testing
DIN EN 60529	IP codes

Table 5: Standards of the Ministry of Information Industry of the People’s Republic of China

SJ/T 11363-2006	“Requirements for Concentration Limits for Certain Hazardous Substances in Electronic Information Products” (2006-06).
SJ/T 11364-2006	<p data-bbox="513 891 1181 958">“Marking for Control of Pollution Caused by Electronic Information Products” (2006-06).</p> <p data-bbox="513 981 1181 1191">According to the “Chinese Administration on the Control of Pollution caused by Electronic Information Products” (ACPEIP) the EPUP, i.e., Environmental Protection Use Period, of this product is 20 years as per the symbol shown here, unless otherwise marked. The EPUP is valid only as long as the product is operated within the operating limits described in the Cinterion Wireless Modules Hardware Interface Description.</p> <p data-bbox="513 1214 1399 1317">Please see Table 6 for an overview of toxic or hazardous substances or elements that might be contained in product parts in concentrations above the limits defined by SJ/T 11363-2006.</p> 

Table 6: Toxic or hazardous substances or elements with defined concentration limits

部件名称 Name of the part	有毒有害物质或元素 Hazardous substances					
	铅 (Pb)	汞 (Hg)	镉 (Cd)	六价铬 (Cr(VI))	多溴联苯 (PBB)	多溴二苯醚 (PBDE)
金属部件 (Metal Parts)	○	○	○	○	○	○
电路模块 (Circuit Modules)	X	○	○	○	○	○
电缆及电缆组件 (Cables and Cable Assemblies)	○	○	○	○	○	○
塑料和聚合物部件 (Plastic and Polymeric parts)	○	○	○	○	○	○

O:
表示该有毒有害物质在该部件所有均质材料中的含量均在SJ/T11363-2006 标准规定的限量要求以下。
Indicates that this toxic or hazardous substance contained in all of the homogeneous materials for this part is below the limit requirement in SJ/T11363-2006.

X:
表示该有毒有害物质至少在该部件的某一均质材料中的含量超出SJ/T11363-2006标准规定的限量要求。
Indicates that this toxic or hazardous substance contained in at least one of the homogeneous materials used for this part *might exceed* the limit requirement in SJ/T11363-2006.

1.3.2 SAR requirements specific to portable mobiles

Mobile phones, PDAs or other portable transmitters and receivers incorporating a GSM module must be in accordance with the guidelines for human exposure to radio frequency energy. This requires the Specific Absorption Rate (SAR) of portable EES3 based applications to be evaluated and approved for compliance with national and/or international regulations.

Since the SAR value varies significantly with the individual product design manufacturers are advised to submit their product for approval if designed for portable use. For European and US markets the relevant directives are mentioned below. It is the responsibility of the manufacturer of the final product to verify whether or not further standards, recommendations or directives are in force outside these areas.

Products intended for sale on US markets

ES 59005/ANSI C95.1 Considerations for evaluation of human exposure to Electromagnetic Fields (EMFs) from Mobile Telecommunication Equipment (MTE) in the frequency range 30MHz - 6GHz

Products intended for sale on European markets

EN 50360 Product standard to demonstrate the compliance of mobile phones with the basic restrictions related to human exposure to electromagnetic fields (300MHz - 3GHz)

1.3.3 Safety Precautions

The following safety precautions must be observed during all phases of the operation, usage, service or repair of any cellular terminal or mobile incorporating EES3. Manufacturers of the cellular terminal are advised to convey the following safety information to users and operating personnel and to incorporate these guidelines into all manuals supplied with the product. Failure to comply with these precautions violates safety standards of design, manufacture and intended use of the product. Cinterion Wireless Modules assumes no liability for customer's failure to comply with these precautions.

	<p>When in a hospital or other health care facility, observe the restrictions on the use of mobiles. Switch the cellular terminal or mobile off, if instructed to do so by the guidelines posted in sensitive areas. Medical equipment may be sensitive to RF energy. The operation of cardiac pacemakers, other implanted medical equipment and hearing aids can be affected by interference from cellular terminals or mobiles placed close to the device. If in doubt about potential danger, contact the physician or the manufacturer of the device to verify that the equipment is properly shielded. Pacemaker patients are advised to keep their hand-held mobile away from the pacemaker, while it is on.</p>
	<p>Switch off the cellular terminal or mobile before boarding an aircraft. Make sure it cannot be switched on inadvertently. The operation of wireless appliances in an aircraft is forbidden to prevent interference with communications systems. Failure to observe these instructions may lead to the suspension or denial of cellular services to the offender, legal action, or both.</p>
	<p>Do not operate the cellular terminal or mobile in the presence of flammable gases or fumes. Switch off the cellular terminal when you are near petrol stations, fuel depots, chemical plants or where blasting operations are in progress. Operation of any electrical equipment in potentially explosive atmospheres can constitute a safety hazard.</p>
	<p>Your cellular terminal or mobile receives and transmits radio frequency energy while switched on. Remember that interference can occur if it is used close to TV sets, radios, computers or inadequately shielded equipment. Follow any special regulations and always switch off the cellular terminal or mobile wherever forbidden, or when you suspect that it may cause interference or danger.</p>
	<p>Road safety comes first! Do not use a hand-held cellular terminal or mobile when driving a vehicle, unless it is securely mounted in a holder for speakerphone operation. Before making a call with a hand-held terminal or mobile, park the vehicle. Speakerphones must be installed by qualified personnel. Faulty installation or operation can constitute a safety hazard.</p>
	<p>IMPORTANT! Cellular terminals or mobiles operate using radio signals and cellular networks. Because of this, connection cannot be guaranteed at all times under all conditions. Therefore, you should never rely solely upon any wireless device for essential communications, for example emergency calls. Remember, in order to make or receive calls, the cellular terminal or mobile must be switched on and in a service area with adequate cellular signal strength. Some networks do not allow for emergency calls if certain network services or phone features are in use (e.g. lock functions, fixed dialing etc.). You may need to deactivate those features before you can make an emergency call. Some networks require that a valid SIM card be properly inserted in the cellular terminal or mobile.</p>

2 Product Concept

2.1 Key Features at a Glance

Feature	Implementation
<i>General</i>	
Frequency bands	Quad band: GSM 850/900/1800/1900MHz
GSM class	Small MS
Output power (according to Release 99)	Class 4 (+33dBm \pm 2dB) for EGSM850 Class 4 (+33dBm \pm 2dB) for EGSM900 Class 1 (+30dBm \pm 2dB) for GSM1800 Class 1 (+30dBm \pm 2dB) for GSM1900 Class E2 (+27dBm \pm 3dB) for GSM 850 8-PSK Class E2 (+27dBm \pm 3dB) for GSM 900 8-PSK Class E2 (+26dBm +3 /-4dB) for GSM 1800 8-PSK Class E2 (+26dBm +3 /-4dB) for GSM 1900 8-PSK The values stated above are maximum limits. According to Release 99, the maximum output power in a multislot configuration may be lower. The nominal reduction of maximum output power varies with the number of uplink timeslots used and amounts to 3.0dB for 2Tx, 4.8dB for 3Tx and 6.0dB for 4Tx.
Power supply	3.2V to 4.5V
Ambient operating temperature according to IEC 60068-2	Normal operation: -30°C to +75°C Restricted operation: +75°C to +85°C, -30°C to -40°C
Physical	Dimensions: 29.6mm x 33.9mm x 3.2mm Weight: approx. 5.5g
RoHS	All hardware components fully compliant with EU RoHS Directive
<i>GSM / GPRS / EGPRS features</i>	
Data transfer	GPRS: <ul style="list-style-type: none"> • Multislot Class 12 • Full PBCCH support • Mobile Station Class B • Coding Scheme 1 – 4 EGPRS: <ul style="list-style-type: none"> • Multislot Class 12 • Mobile Station Class B • Modulation and Coding Scheme MCS 1-9 CSD: <ul style="list-style-type: none"> • V.110, RLP, non-transparent • 2.4, 4.8, 9.6, 14.4kbps • USSD PPP-stack for GPRS data transfer
SMS	Point-to-point MT and MO Cell broadcast Text and PDU mode Storage: SIM card plus 25 SMS locations in mobile equipment Transmission of SMS alternatively over CSD or GPRS. Preferred mode can be user defined.
Fax	Group 3; Class 1

Feature	Implementation
Audio	<p>Speech codecs:</p> <ul style="list-style-type: none"> • Half rate HR (ETS 06.20) • Full rate FR (ETS 06.10) • Enhanced full rate EFR (ETS 06.50/06.60/06.80) • Adaptive Multi Rate AMR <p>Speakerphone operation, echo cancellation, noise suppression, DTMF, 7 ringing tones</p>
<i>Software</i>	
AT commands	Hayes 3GPP TS 27.007, TS 27.005, Cinterion AT commands for RIL compatibility
Microsoft™ compatibility	RIL for Pocket PC and Smartphone
SIM Application Toolkit	SAT Release 99
TCP/IP stack	Access by AT commands
Remote SIM Access	<p>EES3 supports Remote SIM Access. RSA enables EES3 to use a remote SIM card via its serial interface and an external application, in addition to the SIM card locally attached to the dedicated lines of the application interface. The connection between the external application and the remote SIM card can be a Bluetooth wireless link or a serial link.</p> <p>The necessary protocols and procedures are implemented according to the “SIM Access Profile Interoperability Specification of the Bluetooth Special Interest Group” (SAP).</p>
Firmware update	Generic update from host application over ASC0, ASC1 or USB.
<i>Interfaces</i>	
Module interface	<p>Surface mount device with solderable connection pads (SMT application interface).</p> <p>Land grid array (LGA) technology ensures high solder joint reliability and provides the possibility to use an optional module mounting socket.</p> <p>For more information on how to integrate SMT modules see also [11]. This application note comprises chapters on module mounting and application layout issues as well as on additional SMT application development equipment.</p>
2 serial interfaces	<p>ASC0:</p> <ul style="list-style-type: none"> • 8-wire modem interface with status and control lines, unbalanced, asynchronous • Adjustable baud rates: 300bps to 921,600bps • Autobauding: 1,200bps to 460,800bps • Supports RTS0/CTS0 hardware handshake and software XON/XOFF flow control. • Multiplex ability according to GSM 07.10 Multiplexer Protocol. <p>ASC1:</p> <ul style="list-style-type: none"> • 4-wire, unbalanced asynchronous interface • Adjustable baud rates: 300bps to 921,600bps • Supports RTS1/CTS1 hardware handshake and software XON/XOFF flow control
USB	Supports a USB 2.0 Full Speed (12Mbit/s) slave interface.

Feature	Implementation
I ² C	I ² C bus for 7-bit addressing and transmission rates up to 400kbps. Programmable with AT [^] SSPI command. Alternatively, all lines of the I ² C interface are configurable as SPI.
SPI	Serial Peripheral Interface for transmission rates up to 6.5 Mbps. Programmable with AT [^] SSPI command. If the SPI is active the I ² C interface is not available.
Audio	2 analog interfaces 1 digital interface (PCM)
SIM interface	Supported SIM cards: 3V, 1.8V
Antenna	50Ω.
<i>Power on/off, Reset</i>	
Power on/off	Switch-on by hardware signal IGT Switch-off by AT command (AT [^] SMSO) Automatic switch-off in case of critical temperature and voltage conditions.
Reset	Orderly shutdown and reset by AT command Emergency reset by hardware signals EMERG_OFF and IGT.
<i>Special features</i>	
Charging	Supports management of rechargeable Lithium Ion and Lithium Polymer batteries
Real time clock	Timer functions via AT commands
Phonebook	SIM and phone
TTY/CTM support	Integrated CTM modem

2.2 EES3 System Overview

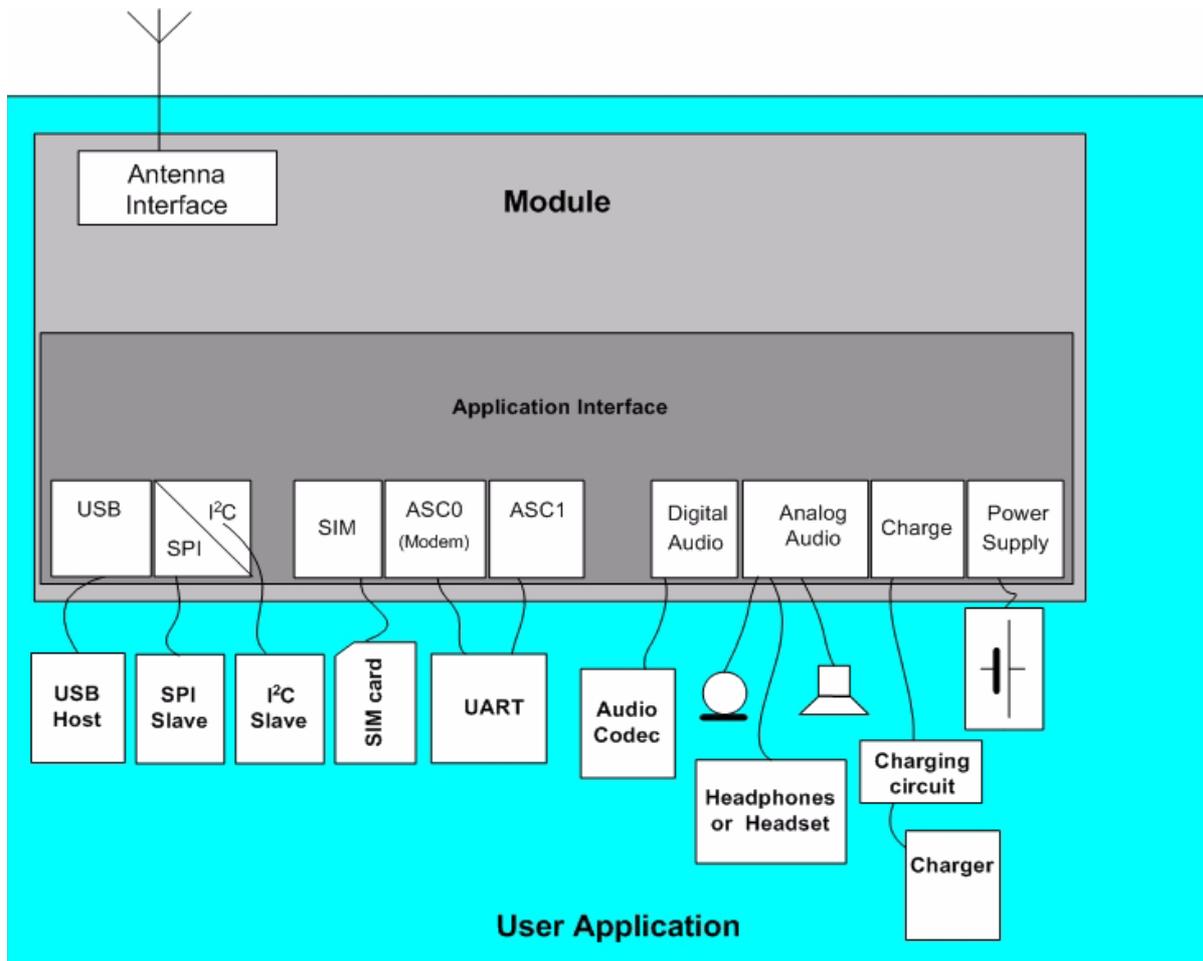


Figure 1: EES3 system overview

2.3 Circuit Concept

Figure 2 shows a block diagram of the EES3 module and illustrates the major functional components:

Baseband block:

- Digital baseband processor with DSP
- Analog processor with power supply unit (PSU)
- Flash / PSRAM (stacked)
- Application interface (SMT with connecting pads)

RF section:

- RF transceiver
- RF power amplifier
- RF front
- Antenna pad

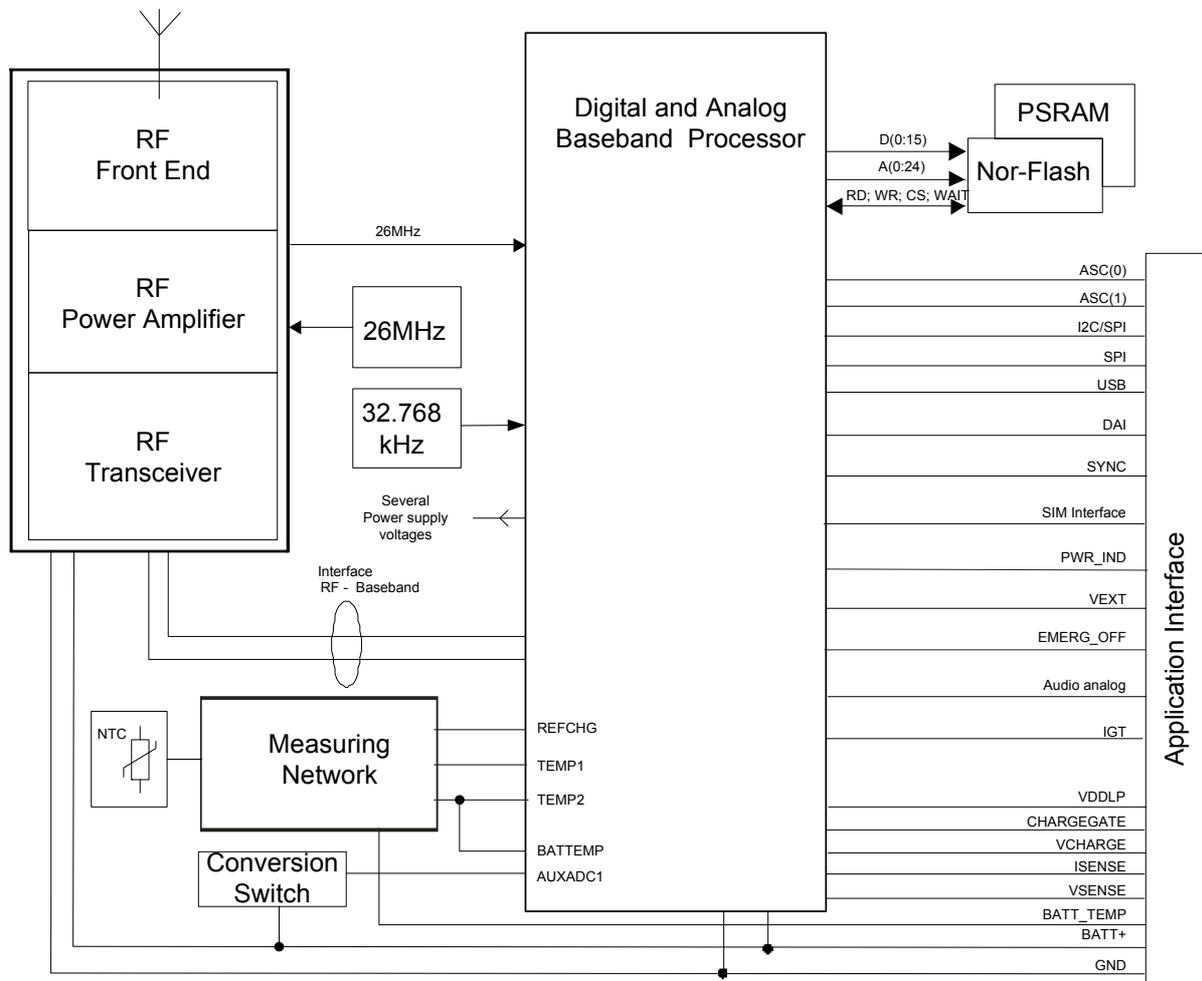


Figure 2: EES3 block diagram

3 Application Interface

EES3 is equipped with an SMT application interface that connects to the external application. The host interface incorporates several sub-interfaces described in the following sections:

- Power supply - see [Section 3.2](#)
- Charger interface – see [Section 3.5](#)
- SIM interface - see [Section 3.9](#)
- Serial interface ASC0 - see [Section 3.10](#)
- Serial interface ASC1 - see [Section 3.11](#)
- Serial interface USB - see [Section 3.12](#)
- Serial interface I²C - see [Section 3.13](#)
- Two analog audio interfaces - see [Section 3.15](#)
- Digital audio interface (DAI) - see [Section 3.15](#) and [3.5.5](#)
- Status and control lines: IGT, EMERG_OFF, PWR_IND, SYNC - see [Table 27](#).

3.1 Operating Modes

The table below briefly summarizes the various operating modes referred to in the following chapters.

Table 7: Overview of operating modes

Normal operation	GSM / GPRS SLEEP	Various power save modes set with AT+CFUN command. Software is active to minimum extent. If the module was registered to the GSM network in IDLE mode, it is registered and paging with the BTS in SLEEP mode, too. Power saving can be chosen at different levels: The NON-CYCLIC SLEEP mode (AT+CFUN=0) disables the AT interface. The CYCLIC SLEEP modes AT+CFUN=7 and 9 alternately activate and deactivate the AT interfaces to allow permanent access to all AT commands.
	GSM IDLE	Software is active. Once registered to the GSM network, paging with BTS is carried out. The module is ready to send and receive.
	GSM TALK	Connection between two subscribers is in progress. Power consumption depends on network coverage individual settings, such as DTX off/on, FR/EFR/HR, hopping sequences, antenna.
	GPRS IDLE EGPRS IDLE	Module is ready for GPRS data transfer, but no data is currently sent or received. Power consumption depends on network settings and GPRS configuration (e.g. multislot settings).
	GPRS DATA EGPRS DATA	GPRS data transfer in progress. Power consumption depends on network settings (e.g. power control level), uplink / downlink data rates, GPRS configuration (e.g. used multislot settings) and reduction of maximum output power.
POWER DOWN	Normal shutdown after sending the AT^SMSO command. Only a voltage regulator is active for powering the RTC. Software is not active. Interfaces are not accessible. Operating voltage (connected to BATT+) remains applied.	
Airplane mode	Airplane mode shuts down the radio part of the module, causes the module to log off from the GSM/GPRS network and disables all AT commands whose execution requires a radio connection. Airplane mode can be controlled by using the AT commands AT^SCFG and AT+CALA: <ul style="list-style-type: none"> • With AT^SCFG=MEopMode/Airplane/OnStart the module can be configured to enter the Airplane mode each time when switched on or reset. • The parameter AT^SCFG=MEopMode/Airplane can be used to switch back and forth between Normal mode and Airplane mode any time during operation. • Setting an alarm time with AT+CALA followed by AT^SMSO wakes the module up into Airplane mode at the scheduled time. 	
Charge-only mode	Limited operation for battery powered applications. Enables charging while module is detached from GSM network. Limited number of AT commands is accessible. Charge-only mode applies when the charger is connected if the module was powered down with AT^SMSO.	
Charge mode during normal operation	Normal operation (SLEEP, IDLE, TALK, GPRS/EGPRS IDLE, GPRS/EGPRS DATA) and charging running in parallel. Charge mode changes to Charge-only mode when the module is powered down before charging has been completed.	

See [Table 13](#) for the various options proceeding from one mode to another.

3.2 Power Supply

EES3 needs to be connected to a power supply at the SMT application interface (3 lines each BATT+ and GND).

The power supply of EES3 has to be a single voltage source at BATT+. It must be able to provide the peak current during the uplink transmission.

All the key functions for supplying power to the device are handled by the power management section of the analog controller. This IC provides the following features:

- Stabilizes the supply voltages for the GSM baseband using low drop linear voltage regulators and a DC-DC step down switching regulator.
- Switches the module's power voltages for the power-up and -down procedures.
- Delivers, across the VEXT line, a regulated voltage for an external application. This voltage is not available in Power-down mode.
- SIM switch to provide SIM power supply.

3.2.1 Minimizing Power Losses

When designing the power supply for your application please pay specific attention to power losses. Ensure that the input voltage $V_{\text{BATT+}}$ never drops below 3.2V on the EES3 board, not even in a transmit burst where current consumption can rise to typical peaks of 2A. It should be noted that EES3 switches off when exceeding these limits. Any voltage drops that may occur in a transmit burst should not exceed 400mV.

The measurement network monitors outburst and inburst values. The drop is the difference of both values. The maximum drop (D_{max}) since the last start of the module will be saved. In IDLE and SLEEP mode, the module switches off if the minimum battery voltage ($V_{\text{batt min}}$) is reached.

Example:

$$V_{\text{I min}} = 3.2\text{V}$$

$$D_{\text{max}} = 0.4\text{V}$$

$$V_{\text{batt min}} = V_{\text{I min}} + D_{\text{max}}$$

$$V_{\text{batt min}} = 3.2\text{V} + 0.4\text{V} = 3.6\text{V}$$

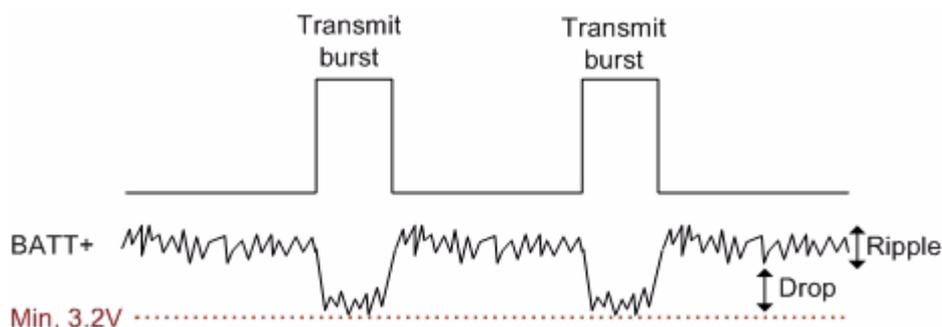


Figure 3: Power supply limits during transmit burst

3.2.2 Measuring the Supply Voltage V_{BATT+}

To measure the supply voltage V_{BATT+} it is possible to define two reference points GND and BATT+. GND should be the module's baseband shielding, while BATT+ should be a test pad on the external application the module is mounted on. The external BATT+ reference point has to be connected to and positioned close to the SMT application interface's BATT+ pads 68 or 74 as shown in [Figure 4](#).

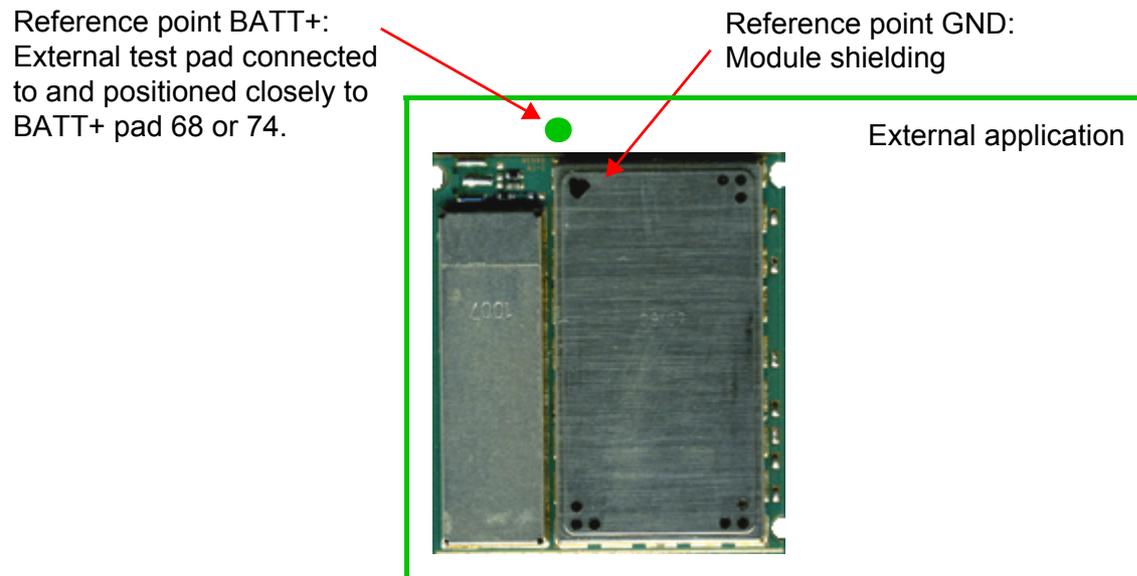


Figure 4: Position of reference points BATT+ and GND

3.2.3 Monitoring Power Supply by AT Command

To monitor the supply voltage you can also use the AT[^]SBV command which returns the value related to the reference points BATT+ and GND.

The module continuously measures the voltage at intervals depending on the operating mode of the RF interface. The duration of measuring ranges from 0.5s in TALK/DATA mode to 50s when EES3 is in IDLE mode or Limited Service (deregistered). The displayed voltage (in mV) is averaged over the last measuring period before the AT[^]SBV command was executed.

3.3 Power Up / Power Down Scenarios

In general, be sure not to turn on EES3 while it is beyond the safety limits of voltage and temperature stated in [Chapter 5](#). EES3 would immediately switch off after having started and detected these inappropriate conditions. In extreme cases this can cause permanent damage to the module.

3.3.1 Turn on EES3

EES3 can be started in a variety of ways as described in the following chapters:

- Hardware driven start-up by IGT line: starts Normal mode or Airplane mode (see [3.3.1.1](#))
- Software controlled reset by AT+CFUN command: starts Normal mode or Airplane mode (see [3.3.1.4](#))
- Hardware driven start-up by VCHARGE line: starts charging algorithm and charge-only mode (see [3.3.1.3](#))
- Wake-up from Power-down mode by using RTC interrupt: starts Airplane mode

The option whether to start into Normal mode or Airplane mode depends on the settings made with the AT^SCFG command or AT+CALA. With AT+CALA, followed by AT^SMSO the module can be configured to restart into Airplane mode at a scheduled alarm time. Switching back and forth between Normal mode and Airplane mode is possible any time during operation by using the AT^SCFG command.

After startup or mode change the following URCs indicate the module's ready state:

- "SYSSTART" indicates that the module has entered Normal mode.
- ^SYSSTART AIRPLANE MODE" indicates that the module has entered Airplane mode.
- ^SYSSTART CHARGE ONLY MODE" indicates that the module has entered the Charge-only mode.

These URCs are indicated only if the module is set to a fixed bit rate, i.e. they do not appear if autobauding is enabled (AT+IPR≠0). Detailed explanations on AT^SCFG, AT+CFUN, AT+CALA, Airplane mode and AT+IPR can be found in [\[1\]](#).

3.3.1.1 Turn on EES3 Using Ignition Line IGT

When the EES3 module is in Power-down mode or Charge-only mode, it can be started to Normal mode or Airplane mode by driving the IGT (ignition) line to ground. This must be accomplished with an open drain/collector driver to avoid current flowing into this line.

The module will start up when both of the following two conditions are met:

- The supply voltage applied at BATT+ must be in the operating range.
- The IGT line needs to be driven low for at least 400ms in Power-down mode or at least 2s in Charge-only mode.

Considering different strategies of host application design the figures below show two approaches to meet this requirement: The example in [Figure 5](#) assumes that IGT is activated after BATT+ has already been applied. The example in [Figure 6](#) assumes that IGT is held low before BATT+ is switched on. In either case, to power on the module, ensure that low state of IGT takes at least 400ms (Power-down mode) or 2s (Charge-only mode) from the moment the voltage at BATT+ is available. For Charge-only mode see also [Section 3.5.7](#).

Assertion of CTS indicates that the module is ready to receive data from the host application. In addition, if configured to a fixed bit rate (AT+IPR≠0), the module will send the URC “^SYSSTART” or “^SYSSTART AIRPLANE MODE” which notifies the host application that the first AT command can be sent to the module. The duration until this URC is output varies with the SIM card and may take a couple of seconds.

Please note that no “^SYSSTART” or “^SYSSTART AIRPLANE MODE” URC will be generated if autobauding (AT+IPR=0) is enabled.

To allow the application to detect the ready state of the module we recommend using hardware flow control which can be set with AT\Q or AT+IFC (see [1] for details). The default setting of EES3 is AT\Q0 (no flow control) which shall be altered to AT\Q3 (RTS/CTS handshake). If the application design does not integrate RTS/CTS lines the host application shall wait at least for the “^SYSSTART” or “^SYSSTART AIRPLANE MODE” URC. However, if the URCs are neither used (due to autobauding) then the only way of checking the module’s ready state is polling. To do so, try to send characters (e.g. “at”) until the module is responding.

See also [Section 3.3.2](#) "Signal States after Startup".

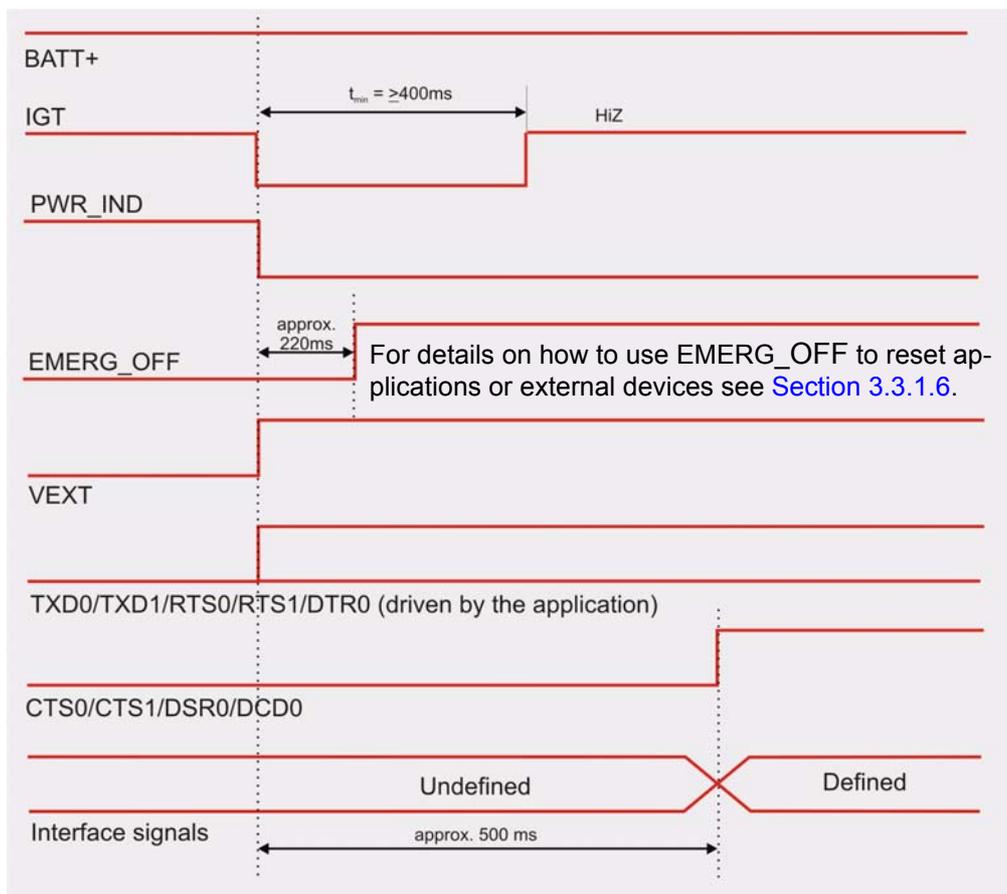


Figure 5: Powerup with operating voltage at BATT+ applied before activating IGT

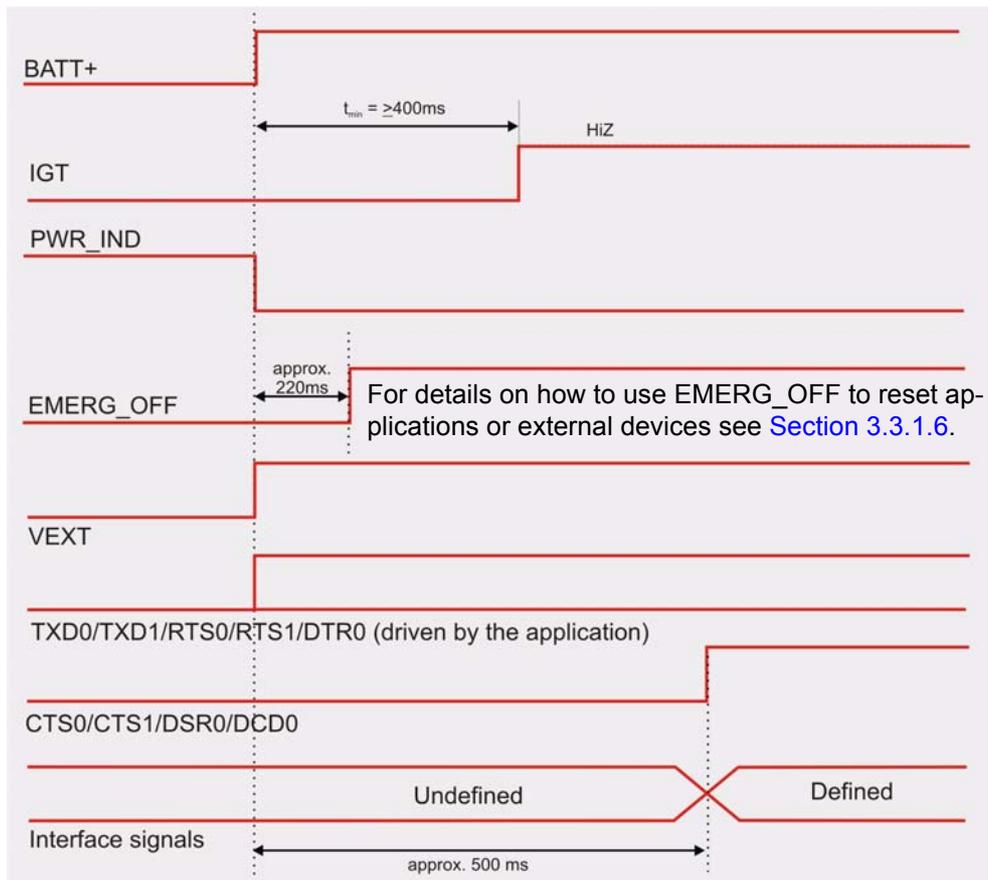


Figure 6: Powerup with IGT held low before switching on operating voltage at BATT+

3.3.1.2 Configuring the IGT Line for Use as ON/OFF Switch

The IGT line can be configured for use in two different switching modes: You can set the IGT line to switch on the module only, or to switch it on and off. The switching mode is determined by the parameter "MEShutdown/OnIgnition" of the AT^SCFG command. This approach is useful for application manufacturers who wish to have an ON/OFF switch installed on the host device.

By factory default, the ON/OFF switch mode of IGT is disabled:

```
at^scfg=meshutdown/onignition          # Query the current status of IGT.
^SCFG: "MEShutdown/OnIgnition","off"   # IGT can be used only to switch on EES3.
                                         IGT works as described in Section 3.3.1.1.
OK
```

To configure IGT for use as ON/OFF switch:

```
at^scfg=meshutdown/onignition,on       # Enable the ON/OFF switch mode of IGT.
^SCFG: "MEShutdown/OnIgnition","on"    # IGT can be used to switch on and off EES3.
OK
```

We strongly recommend taking great care before changing the switching mode of the IGT line. To ensure that the IGT line works properly as ON/OFF switch it is of vital importance that the following conditions are met.

Switch-on condition: If the EES3 is off, the IGT line must be asserted for at least 400ms before being released. The module switches on after 400ms.

Switch-off condition: If the EES3 is on, the IGT line must be asserted for at least 1s before being released. The module switches off after the line is released. The switch-off routine is identical with the procedure initiated by AT^SMSO, i.e. the software performs an orderly shutdown as described in [Section 3.3.3.1](#). Before switching off the module wait at least 2 seconds after startup.

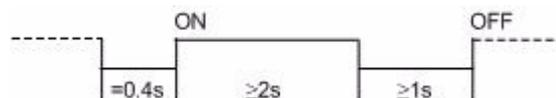


Figure 7: Timing of IGT if used as ON/OFF switch

3.3.1.3 Turn on EES3 Using the VCHARGE Signal

As detailed in [Section 3.5.7](#), the charging adapter can be connected regardless of the module's operating mode.

If the charger is connected to the charger input of the external charging circuit and the module's VCHARGE line while EES3 is off, and the battery voltage is above the undervoltage lockout threshold, processor controlled fast charging starts (see [Section 3.5.6](#)). EES3 enters a restricted mode, referred to as Charge-only mode where only the charging algorithm will be launched.

During the Charge-only mode EES3 is neither logged on to the GSM network nor are the serial interfaces fully accessible. To switch from Charge-only mode to Normal mode the ignition line (IGT) must be pulled low for at least 2 seconds. When released, the IGT line goes high and causes the module to enter the Normal mode. See also [Section 3.5.7](#).

3.3.1.4 Reset EES3 via AT+CFUN Command

To reset and restart the EES3 module use the command AT+CFUN. You can enter AT+CFUN=,1 or AT+CFUN=x,1, where x may be in the range from 0 to 9. See [\[1\]](#) for details.

If configured to a fix baud rate (AT+IPR≠0), the module will send the URC "`^SYSSTART`" or "`^SYSSTART AIRPLANE MODE`" to notify that it is ready to operate. If autobauding is enabled (AT+IPR=0) there will be no notification. To register to the network SIM PIN authentication is necessary after restart.

3.3.1.5 Reset or Turn off EES3 in Case of Emergency

Caution: Use the EMERG_OFF line only when, due to serious problems, the software is not responding for more than 5 seconds. Pulling the EMERG_OFF line causes the loss of all information stored in the volatile memory. Therefore, this procedure is intended only for use in case of emergency, e.g. if EES3 does not respond, if reset or shutdown via AT command fails.

The EMERG_OFF signal is available on the application interface. To control the EMERG_OFF line it is recommended to use an open drain / collector driver.

The EMERG_OFF line can be used to switch off or to reset the module. In any case the EMERG_OFF line must be pulled to ground for ≥ 10 ms. Then, after releasing the EMERG_OFF line the module restarts if IGT is held low for at least 400ms. Otherwise, if IGT is not low the module switches off. In this case, it can be restarted any time as described in [Section 3.3.1.1](#).

After hardware driven restart, notification via "`^SYSSTART`" or "`^SYSSTART AIRPLANE`" URC is the same as in case of restart by IGT or AT command. To register to the network SIM PIN authentication is necessary after restart.

3.3.1.6 Using EMERG_OFF Signal to Reset Application(s) or External Device(s)

When the module starts up, while IGT is held low for 400ms, the EMERG_OFF signal goes low for approximately 220ms as shown in [Figure 5](#) and [Figure 6](#). During this period, EMERG_OFF becomes an output which can be used to reset application(s) or external device(s) connected to the module.

After this period, i.e. during operation of the module, the EMERG_OFF is an input.

Specifications of the input and output mode of EMERG_OFF can be found in [Table 28](#).

3.3.2 Signal States after Startup

Table 8 describes the various states each interface signal passes through after startup and during operation.

As shown in Figure 5 and Figure 6 signals are in an undefined state while the module is initializing. Once the startup initialization has completed, i.e. when the software is running, all signals are in defined state. The state of several signals will change again once the respective interface is activated or configured by AT command.

Table 8: Signal states

Signal name	Undefined state during startup	Defined state after startup initialization	Active state after configuration by AT command		
			SPI	I ² C	DAI
SYNC	O, L	O, L			
CCIN	I, PU(100k)	I, PU(100k)			
CCRST	O, L	O, L			
CCIO	O, L	O, L			
CCCLK	O, L	O, L			
CCVCC	O, L	2.9V			
RXD0	I, PU	O, H			
TXD0	I, PU	I, PD(330k)			
CTS0	O, L	O, L ¹			
RTS0	I, PU	I, PD(330k)			
DTR0	I, PU	I			
DCD0	O, L	O, H			
DSR0	O, L	O, L ¹			
RING0	I, PU	O, H ²			
RXD1	O, H	O, H			
TXD1	I, PD(330k)	I, PD(330k)			
CTS1	L	O, L ¹			
RTS1	I, PD(330k)	I, PD(330k)			
SPIDI	I	Tristate	I	Tristate	
SPICS	I	O, H	O, L	Tristate	
I2CDAT_SPIDO	I	Tristate	O, L/H	IO	
I2CCLK_SPICLK	I	Tristate	O, L/H	O, OD	
DAC_OUT	O, L	O, L			
DAI0	I	O, L			O, L
DAI1	I	Tristate			I
DAI2	I	O, L ³			O, L
DAI3	I	O, L			O, L

Table 8: Signal states

Signal name	Undefined state during startup	Defined state after startup initialization	Active state after configuration by AT command		
			SPI	I ² C	DAI
DAI4	I	Tristate			I
DAI5	I	Tristate			I
DAI6	I	Tristate			I

1. Before reaching the defined state the signal has the intermediate state O, H for about 2s.
2. Before reaching the defined state the signal has the intermediate states O, H for about 2s and O, L for about 1s.
3. Before reaching the defined state the signal has the intermediate state O, H for about 0.5s.

Abbreviations used in [Table 8](#):

L = Low level H = High level L/H = Low or high level I = Input O = Output	OD = Open Drain PD = Pull down with min +15µA and max. +100µA PD(...k) = Fix pull down resistor PU = Pull up with typ. -200µA and max. -350µA PU(...k) = Fix pull up resistor
---	---

3.3.3 Turn off EES3

EES3 can be turned off as follows:

- Normal shutdown: Software controlled by AT^SMSO command
- Automatic shutdown: Takes effect if board or battery temperature is out of range or if undervoltage or overvoltage conditions occur.

3.3.3.1 Turn off EES3 Using AT Command

The best and safest approach to powering down EES3 is to issue the AT^SMSO command. This procedure lets EES3 log off from the network and allows the software to enter into a secure state and save data before disconnecting the power supply. The mode is referred to as Power-down mode. In this mode, only the RTC stays active.

Before switching off the device sends the following response:

```
^SMSO: MS OFF
OK
^SHUTDOWN
```

After sending AT^SMSO do not enter any other AT commands. There are two ways to verify when the module turns off:

- Wait for the URC “^SHUTDOWN”. It indicates that data have been stored non-volatile and the module turns off in less than 1 second.
- Also, you can monitor the PWR_IND signal. High state of PWR_IND definitely indicates that the module is switched off.

Be sure not to disconnect the supply voltage V_{BATT+} before the URC “^SHUTDOWN” has been issued and the PWR_IND signal has gone high. Otherwise you run the risk of losing data. Signal states during turn-off are shown in [Figure 8](#).

While EES3 is in Power-down mode the application interface is switched off and must not be fed from any other source. Therefore, your application must be designed to avoid any current flow into any digital lines of the application interface, especially of the serial interfaces. No special care is required for the USB interface which is protected from reverse current.

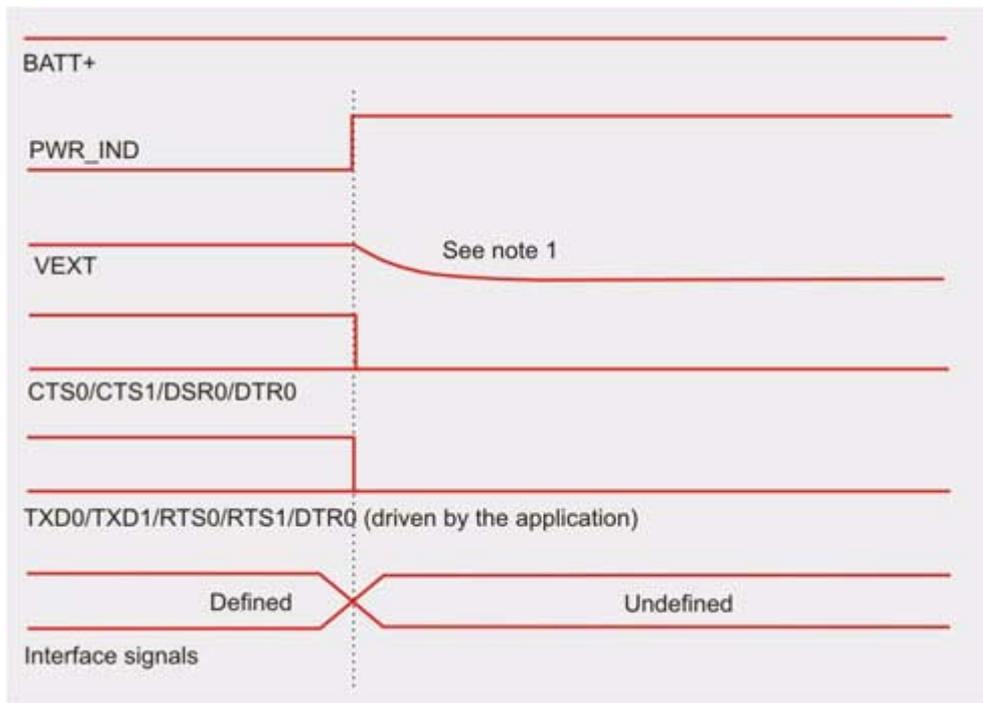


Figure 8: Signal states during turn-off procedure

Note 1: Depending on capacitance load from host application.

3.3.3.2 Turn on/off EES3 Applications with Integrated USB

In a Windows environment, the USB COM port emulation causes the USB port of EES3 to appear as a virtual COM port (VCOM port). The VCOM port emulation is only present when Windows can communicate with the module, and is lost when the module shuts down. Therefore, the host application or Terminal program must be disconnected from the USB VCOM port each time the module is restarted.

Restart after shutdown with AT^SMSO:

After entering the power-down command AT^SMSO on one of the interfaces (ASC0, ASC1, USB) the host application or Terminal program used on the USB VCOM port must be closed before the module is restarted by activating the IGT line.

Software reset with AT+CFUN=x,1:

Likewise, when using the reset command AT+CFUN=x,1 on one of the interfaces (ASC0, ASC1, USB) ensure that the host application or Terminal program on the USB VCOM port be closed down before the module restarts.

Note that if AT+CFUN=x,1 is entered on the USB interface the application or Terminal program on the USB VCOM port must be closed immediately after the response OK is returned.

3.3.4 Automatic Shutdown

Automatic shutdown takes effect if:

- the EES3 board is exceeding the critical limits of overtemperature or undertemperature
- the battery is exceeding the critical limits of overtemperature or undertemperature
- undervoltage or overvoltage is detected

See Charge-only mode described in [Section 3.5.7](#) for exceptions.

The automatic shutdown procedure is equivalent to the Power-down initiated with the AT^SMSO command, i.e. EES3 logs off from the network and the software enters a secure state avoiding loss of data.

Alert messages transmitted before the device switches off are implemented as Unsolicited Result Codes (URCs). The presentation of these URCs can be enabled or disabled with the two AT commands AT^SBC and AT^SCTM. The URC presentation mode varies with the condition, please see [Section 3.3.4.1](#) to [Section 3.3.4.3](#) for details. For further instructions on AT commands refer to [\[1\]](#).

3.3.4.1 Thermal Shutdown

The board temperature is constantly monitored by an internal NTC resistor located on the PCB. The NTC that detects the battery temperature must be part of the battery pack circuit as described in [Section 3.5.3](#). The values detected by either NTC resistor are measured directly on the board or the battery and therefore, are not fully identical with the ambient temperature.

Each time the board or battery temperature goes out of range or back to normal, EES3 instantly displays an alert (if enabled).

- URCs indicating the level "1" or "-1" allow the user to take appropriate precautions, such as protecting the module from exposure to extreme conditions. The presentation of the URCs depends on the settings selected with the AT^SCTM write command:
 AT^SCTM=1: Presentation of URCs is always enabled.
 AT^SCTM=0 (default): Presentation of URCs is enabled during the 2 minute guard period after start-up of EES3. After expiry of the 2 minute guard period, the presentation will be disabled, i.e. no URCs with alert levels "1" or "-1" will be generated.
- URCs indicating the level "2" or "-2" are instantly followed by an orderly shutdown, except in cases described in [Section 3.3.4.2](#). The presentation of these URCs is always enabled, i.e. they will be output even though the factory setting AT^SCTM=0 was never changed.

The maximum temperature ratings are stated in [Section 5.2](#). Refer to [Table 9](#) for the associated URCs.

Table 9: Temperature dependent behavior

Sending temperature alert (2min after EES3 start-up, otherwise only if URC presentation enabled)	
^SCTM_A: 1	Caution: Battery close to overtemperature limit.
^SCTM_B: 1	Caution: Board close to overtemperature limit, i.e., board is 5°C below overtemperature limit.
^SCTM_A: -1	Caution: Battery close to undertemperature limit.
^SCTM_B: -1	Caution: Board close to undertemperature limit, i.e., board is 5°C above undertemperature limit.
^SCTM_A: 0	Battery back to uncritical temperature range.
^SCTM_B: 0	Board back to uncritical temperature range, i.e., board is 6°C below its over- or above its undertemperature limit.
Automatic shutdown (URC appears no matter whether or not presentation was enabled)	
^SCTM_A: 2	Alert: Battery equal or beyond overtemperature limit. EES3 switches off.
^SCTM_B: 2	Alert: Board equal or beyond overtemperature limit. EES3 switches off.
^SCTM_A: -2	Alert: Battery equal or below undertemperature limit. EES3 switches off.
^SCTM_B: -2	Alert: Board equal or below undertemperature limit. EES3 switches off.

3.3.4.2 Deferred Shutdown at Extreme Temperature Conditions

In the following cases, automatic shutdown will be deferred if a critical temperature limit is exceeded:

- While an emergency call is in progress.
- During a two minute guard period after power-up. This guard period has been introduced in order to allow for the user to make an emergency call. The start of emergency call extends the guard period until the end of the call. Any other network activity may be terminated by shutdown upon expiry of the guard time. The guard period starts again when the module registers to the GSM network the first time after power-up.

If the temperature is still out of range after the guard period expires or the call ends, the module switches off immediately (without another alert message).

CAUTION! Automatic shutdown is a safety feature intended to prevent damage to the module. Extended usage of the deferred shutdown functionality may result in damage to the module, and possibly other severe consequences.

3.3.4.3 Undervoltage Shutdown

If the measured battery voltage is no more sufficient to set up a call the following URC will be presented:

^SBC: Undervoltage.

The message will be reported, for example, when you attempt to make a call while the voltage is close to the shutdown threshold of 3.2V and further power loss is caused during the transmit burst. In IDLE mode, the shutdown threshold is the sum of the module's minimum supply voltage (3.2V) and the value of the maximum voltage drop resulting from earlier calls. This means that in IDLE mode the actual shutdown threshold may be higher than 3.2V. Therefore, to properly calculate the actual shutdown threshold application manufacturers are advised to measure the maximum voltage drops that may occur during transmit bursts.

To remind you that the battery needs to be charged soon, the URC appears several times before the module switches off.

This type of URC does not need to be activated by the user. It will be output automatically when fault conditions occur.

3.3.4.4 Overvoltage Shutdown

The overvoltage shutdown threshold is 100mV above the maximum supply voltage V_{BATT+} specified in [Table 28](#).

When the supply voltage approaches the overvoltage shutdown threshold the module will send the following URC:

^SBC: Overvoltage warning

This alert is sent once.

When the overvoltage shutdown threshold is exceeded the module will send the following URC

^SBC: Overvoltage shutdown

before it shuts down cleanly:

This type of URC does not need to be activated by the user. It will be output automatically when fault conditions occur.

Keep in mind that several EES3 components are directly linked to BATT+ and, therefore, the supply voltage remains applied at major parts of EES3, even if the module is switched off. Especially the power amplifier is very sensitive to high voltage and might even be destroyed.

3.4 Automatic GPRS Multislot Class Change

Temperature control is also effective for operation in EGPRS Multislot Class 12, EGPRS Multislot Class 10, GPRS Multislot Class 10 and GPRS Multislot Class 12. If the board temperature rises close to the limit specified for normal operation (see [Section 5.2](#) for temperature limits) while data are transmitted over EGPRS or GPRS, the module automatically reverts:

- from EGPRS Multislot Class 12 (4Tx slots) to EGPRS Multislot Class 10 (2Tx slots),
- from EGPRS Multislot Class 10 (2Tx slots) to EGPRS Multislot Class 8 (1Tx),
- from GPRS Multislot Class 12 (4Tx slots) to GPRS Multislot Class 8 (1Tx)
- from GPRS Multislot Class 10 (2Tx slots) to GPRS Multislot Class 8 (1Tx)

This reduces the power consumption and, consequently, causes the board's temperature to decrease. Once the temperature drops by 5 degrees, EES3 returns to the higher Multislot Class. If the temperature stays at the critical level or even continues to rise, EES3 will not switch back to the higher class.

After a transition from a higher Multislot Class to a lower Multislot Class a possible switchback to the higher Multislot Class is blocked for one minute.

Please note that there is not one single cause of switching over to a lower Multislot Class. Rather it is the result of an interaction of several factors, such as the board temperature that depends largely on the ambient temperature, the operating mode and the transmit power. Furthermore, take into account that there is a delay until the network proceeds to a lower or, accordingly, higher Multislot Class. The delay time is network dependent. In extreme cases, if it takes too much time for the network and the temperature cannot drop due to this delay, the module may even switch off as described in [Section 3.3.4.1](#).

3.5 Charging Control

EES3 integrates a charging management for rechargeable Lithium Ion and Lithium Polymer batteries. You can skip this chapter if charging is not your concern, or if you are not using the implemented charging algorithm.

The following sections contain an overview of charging and battery specifications. Please refer to [5] for greater detail, especially regarding requirements for batteries and chargers, appropriate charging circuits, recommended batteries and an analysis of operational issues typical of battery powered GSM/GPRS applications.

3.5.1 Hardware Requirements

EES3 has no on-board charging circuit. To benefit from the implemented charging management you are required to install a charging circuit within your application according to the [Figure 54](#).

3.5.2 Software Requirements

Use the command `AT^SBC`, parameter `<current>`, to enter the current consumption of the host application. This information enables the EES3 module to correctly determine the end of charging and terminate charging automatically when the battery is fully charged. If the `<current>` value is inaccurate and the application draws a current higher than the final charge current, either charging will not be terminated or the battery fails to reach its maximum voltage. Therefore, the termination condition is defined as: current consumption dependent on operating mode of the ME plus current consumption of the external application. If used the current flowing over the VEXT line of the application interface must be added, too.

The parameter `<current>` is volatile, meaning that the factory default (0mA) is restored each time the module is powered down or reset. Therefore, for better control of charging, it is recommended to enter the value every time the module is started.

See [1] for details on `AT^SBC`.

3.5.3 Battery Pack Requirements

The charging algorithm has been optimized for rechargeable Lithium batteries that meet the characteristics listed below and in [Table 10](#). It is recommended that the battery pack you want to integrate into your EES3 application is compliant with these specifications. This ensures reliable operation, proper charging and, particularly, allows you to monitor the battery capacity using the AT^SBC command. Failure to comply with these specifications might cause AT^SBC to deliver incorrect battery capacity values.

- Li-Ion or Lithium Polymer battery pack specified for a maximum charging voltage of 4.2V and a capacity higher than 500mAh.
- Since charging and discharging largely depend on the battery temperature, the battery pack should include an NTC resistor. If the NTC is not inside the battery it must be in thermal contact with the battery. The NTC resistor must be connected between BATT_TEMP and GND. The B value of the NTC should be in the range: $10k\Omega \pm 5\% @ 25^{\circ}C$, $B_{25/85} = 3423K$ to $B = 3435K \pm 3\%$ (alternatively acceptable: $10k\Omega \pm 2\% @ 25^{\circ}C$, $B_{25/50} = 3370K \pm 3\%$). Please note that the NTC is indispensable for proper charging, i.e. the charging process will not start if no NTC is present.
- Ensure that the pack incorporates a protection circuit capable of detecting overvoltage (protection against overcharging), undervoltage (protection against deep discharging) and overcurrent. Due to the discharge current profile typical of GSM applications, the circuit must be insensitive to pulsed current.
- On the EES3 module, a built-in measuring circuit constantly monitors the supply voltage. In the event of undervoltage, it causes EES3 to power down. Undervoltage thresholds are specific to the battery pack and must be evaluated for the intended model. When you evaluate undervoltage thresholds, consider both the current consumption of EES3 *and* of the application circuit.
- The internal resistance of the battery and the protection should be as low as possible. It is recommended not to exceed 150m Ω , even in extreme conditions at low temperature. The battery cell must be insensitive to rupture, fire and gassing under extreme conditions of temperature and charging (voltage, current).
- The battery pack must be protected from reverse pole connection. For example, the casing should be designed to prevent the user from mounting the battery in reverse orientation.
- It is recommended that the battery pack be approved to satisfy the requirements of CE conformity.

[Figure 9](#) shows the circuit diagram of a typical battery pack design that includes the protection elements described above.

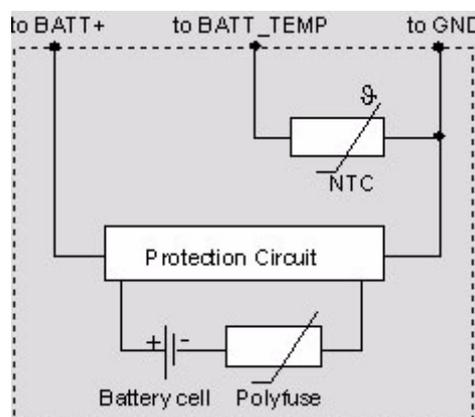


Figure 9: Battery pack circuit diagram

Table 10: Specifications of battery packs suited for use with EES3

Battery type	Rechargeable Lithium Ion or Lithium Polymer battery
Nominal voltage	3.6V / 3.7V
Capacity	> 500mAh
NTC	10k Ω \pm 5% @ 25°C approx. 5k Ω @ 45°C approx. 26.2k Ω @ 0°C B value range: B (25/85)=3423K to B =3435K \pm 3%
Overcharge detection voltage	4.325 \pm 0.025V
Deep discharge detection voltage	2.4V
Deep discharge release voltage	2.6V
Overcurrent detection	3 \pm 0.5A
Overcurrent detection delay time	4 ~ 16ms
Short detection delay time	50 μ s
Internal resistance	<130m Ω <i>Note: A maximum internal resistance of 150mΩ should not be exceeded even after 500 cycles and under extreme conditions.</i>

3.5.4 Batteries Tested for Use with EES3

When you choose a battery for your EES3 application you can take advantage of one of the following two batteries offered by VARTA Microbattery GmbH. Both batteries meet all requirements listed above. They have been thoroughly tested by Cinterion Wireless Modules and proved to be suited for EES3.

- LIP 653450 TC, type Lithium Ion
 This battery is listed in the standard product range of VARTA. It is incorporated in a shrink sleeve and has been chosen for integration into the reference setup.
- PLF 503759C.PCM, type PoLiFlex® Lithium Polymer
 This battery has been especially designed by VARTA for use with electronic applications like mobile phones, PDAs, MP3 players, security and telematic devices. It has almost the same properties as the above Li-Ion battery. It is type Polymer, is smaller, lighter and comes without casing.

Specifications, construction drawings and sales contacts for both VARTA batteries can be found in [\[5\]](#).

3.5.5 Charger Requirements

For using the implemented charging algorithm and the reference charging circuit recommended in [5] and in Figure 54, the charger has to meet the following requirements:

Output voltage: up to 7.0V (stabilized voltage)

Output current: 500mA

Chargers with a higher output current are acceptable too, but please consider that only 500mA will be applied when a 0.3Ohms shunt resistor is connected between VSENSE and ISENSE. See [5] for further details.

3.5.6 Implemented Charging Technique

If all requirements listed above are met (appropriate external charging circuit of application, battery pack, charger, AT^SBC settings) then charging is enabled in various stages depending on the battery condition:

Trickle charging:

- Trickle charge current flows over the VCHARGE line.
- Trickle charging is done when a charger is present (connected to VCHARGE) and the battery is deeply discharged or has undervoltage.
 - If deeply discharged (Deep Discharge Lockout at $V_{BATT+} = 0...2.5V$) the battery is charged at 30mA.
 - In case of undervoltage (Undervoltage Lockout at $V_{BATT+} = 2.5...3.0V$) the battery is charged at 60mA.
 - If $V_{BATT+} = 3.0V... 3.2V$ the battery is charged at 100mA.

Software controlled charging:

- Controlled over CHARGE_GATE.
- Temperature conditions: 0°C to 45°C
- Software controlled charging is done when the charger is present (connected to VCHARGE) and the battery voltage is at least above the undervoltage threshold. Software controlled charging passes the following stages:
 - Power ramp: Depending on the discharge level of the battery (i.e. the measured battery voltage V_{BATT+}) the software adjusts the maximum charge current for charging the battery. The duration of power ramp charging is very short (less than 30 seconds).
 - Fast charging: Battery is charged with constant current (approx. 500mA) until the battery voltage reaches 4.2V (approx. 80% of the battery capacity).
 - Top-up charging: The battery is charged with constant voltage of 4.2V at stepwise reducing charge current until full battery capacity is reached.

Duration of charging:

- EES3 provides a software controlled timer set to 4 hours as a safety feature to prevent permanent charging of defective batteries. The duration of software controlled charging depends on the battery capacity and the level of discharge. Normally, charging stops when the battery is fully charged or, at the latest, when the software timer expires after 4 hours. If the software timer expires a charging error occurs, i.e., the AT^SBC's battery connecting status (<bcs>) is 4. To prevent this time out the charge current should be adjusted to the battery capacity.

3.5.7 Operating Modes during Charging

Of course, the battery can be charged regardless of the module's operating mode. When the GSM module is in Normal mode (SLEEP, IDLE, TALK, GPRS IDLE or GPRS DATA mode), it remains operational while charging is in progress (provided that sufficient voltage is applied). The charging process during the Normal mode is referred to as *Charge mode*.

If the charger is connected to the charger input of the external charging circuit and the module's VCHARGE line while EES3 is in Power-down mode, EES3 goes into *Charge-only mode*.

While the charger remains connected it is not possible to switch the module off by using the AT^SMSO command or the automatic shutdown mechanism. Instead the following applies:

- If the module is in Normal mode and the charger is connected (Charge mode) the AT^SMSO command causes the module to shut down shortly and then start into the Charge-only mode.
- In Charge-only mode the AT^SMSO command is not usable.
- In Charge-only mode the module neither switches off when the battery or the module exceeds the critical limits of overtemperature or undertemperature.

In these cases you can only switch the module off by disconnecting the charger.

To proceed from Charge-only mode to another operating mode you have the following options, provided that the battery voltage is at least above the undervoltage threshold.

- To switch from Charge-only mode to Normal mode you have two ways:
 - Hardware driven: The ignition line (IGT) must be pulled low for at least 2 seconds. When released, the IGT line goes high and causes the module to enter the Normal mode.
 - AT command driven: Set the command `AT^SCFG=MEopMode/Airplane,off` (please do so although the current status of Airplane mode is already "off"). The module will enter the Normal mode, indicated by the "`^SYSSTART`" URC.
- To switch from Charge-only mode to Airplane mode set the command `AT^SCFG=MEopMode/Airplane,on`. The mode is indicated by the URC "`^SYSSTART AIRPLANE MODE`".
- If `AT^SCFG=MEopMode/Airplane/OnStart,on` is set, driving the ignition line (IGT) activates the Airplane mode. The mode is indicated by the URC "`^SYSSTART AIRPLANE MODE`".

Table 11: AT commands available in Charge-only mode

AT command	Use
AT+CALA	Set alarm time, configure Airplane mode.
AT+CCLK	Set date and time of RTC.
AT^SBC	Query status of charger connection.
AT^SBV	Monitor supply voltage.
AT^SCTM	Query temperature range, enable/disable URCs to report critical temperature ranges
AT^SCFG	Enable/disable parameters MEopMode/Airplane or MEopMode/Airplane/OnStart

Table 12: Comparison Charge-only and Charge mode

Mode	How to activate mode	Description of mode
Charge mode	Connect charger to charger input of host application charging circuit and module's VCHARGE line while EES3 is <ul style="list-style-type: none"> • operating, e.g. in IDLE or TALK mode • in SLEEP mode 	<ul style="list-style-type: none"> • Battery can be charged while GSM module remains operational and registered to the GSM network. • In IDLE and TALK mode, the serial interfaces are accessible. All AT commands can be used to full extent. <p><i>Note: If the module operates at maximum power level (PCL5) and GPRS Class 12 at the same time the current consumption is higher than the current supplied by the charger.</i></p>
Charge-only mode	Connect charger to charger input of host application charging circuit and module's VCHARGE line while EES3 is <ul style="list-style-type: none"> • in Power-down mode • in Normal mode: Connect charger to the VCHARGE line, then enter AT^SMSO. <p><i>Note: While trickle charging is in progress, be sure that the host application is switched off. If the application is fed from the trickle charge current the module might be prevented from proceeding to software controlled charging since the current would not be sufficient.</i></p>	<ul style="list-style-type: none"> • Battery can be charged while GSM module is deregistered from GSM network. • Charging runs smoothly due to constant current consumption. • The AT interface is accessible and allows to use the commands listed below.

3.6 Power Saving

Intended for power saving, SLEEP mode reduces the functionality of the EES3 to a minimum and thus minimizes the current consumption. Settings can be made using the AT+CFUN command. For details see [1]. SLEEP mode falls in two categories:

- NON-CYCLIC SLEEP mode: AT+CFUN = 0
- CYCLIC SLEEP modes, AT+CFUN = 7 or 9.

The functionality level AT+CFUN=1 is where power saving is switched off. This is the default after startup.

NON-CYCLIC SLEEP mode permanently blocks the serial interface. The benefit of the CYCLIC SLEEP mode is that the serial interface remains accessible and that, in intermittent wake-up periods, characters can be sent or received without terminating the selected mode. This allows the EES3 to wake up for the duration of an event and, afterwards, to resume power saving. Please refer to [1] for a summary of all SLEEP modes and the different ways of waking up the module.

For CYCLIC SLEEP mode both the EES3 and the application must be configured to use hardware flow control. This is necessary since the CTSx signal is set/reset every 0.9-2.7 seconds in order to indicate to the application when the UART is active. Please refer to [1] for details on how to configure hardware flow control for the EES3.

Note: Although not explicitly stated, all explanations given in this section refer equally to ASC0 and ASC1, and accordingly to CTS0 and CTS1 or RTS0 and RTS1.

3.6.1 Network Dependency of SLEEP Modes

The power saving possibilities of SLEEP modes depend on the network the module is registered in. The paging timing cycle varies with the base station. The duration of a paging interval can be calculated from the following formula:

$$t = 4.615 \text{ ms (TDMA frame duration)} * 51 \text{ (number of frames)} * \text{DRX value.}$$

DRX (Discontinuous Reception) is a value from 2 to 9, resulting in paging intervals from 0.47-2.12 seconds. The DRX value of the base station is assigned by the network operator.

In the pauses between listening to paging messages, the module resumes power saving, as shown in Figure 10.



Figure 10: Power saving and paging

The varying pauses explain the different potential for power saving. The longer the pause the less power is consumed.

3.6.2 Timing of the CTSx Signal in CYCLIC SLEEP Mode 7

Figure 11 illustrates the CTSx signal timing in CYCLIC SLEEP mode 7 (CFUN=7).

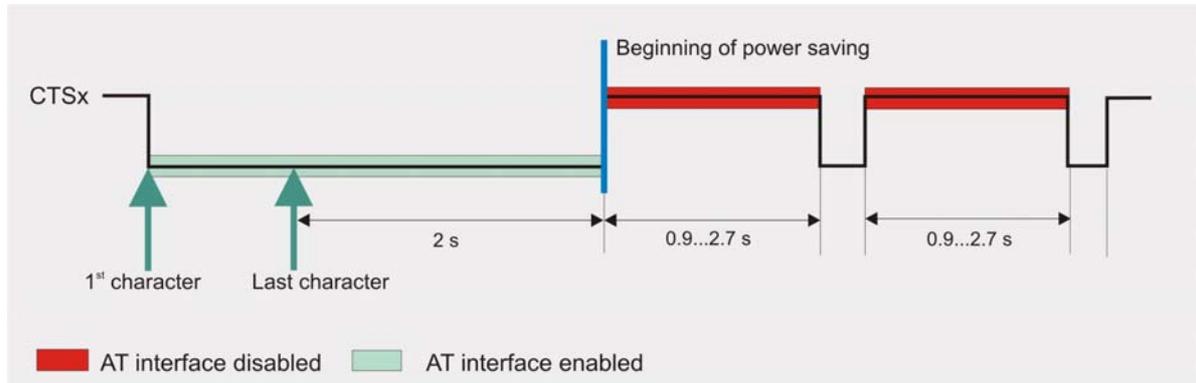


Figure 11: Timing of CTSx signal (if CFUN= 7)

With regard to programming or using timeouts, the UART must take the varying CTS inactivity periods into account.

3.6.3 Timing of the RTSx Signal in CYCLIC SLEEP Mode 9

In SLEEP mode 9 the falling edge of RTSx can be used to temporarily wake up the ME. In this case the activity time is at least the time set with `AT^SCFG="PowerSaver/Mode9/ Timeout", <psm9to>` (default 2 seconds). RTSx has to be asserted for at least a dedicated debounce time in order to wake up the ME. The debounce time specifies the minimum time period an RTSx signal has to remain asserted for the signal to be recognized as wake up signal and being processed. The debounce time is defined as $8 \times 4.615 \text{ ms}$ (TDMA frame duration) and is used to prevent bouncing or other fluctuations from being recognized as signals. Toggling RTSx while the ME is awake has no effect on the AT interface state, the regular hardware flow control via CTS/RTS is unaffected by this RTSx behaviour.

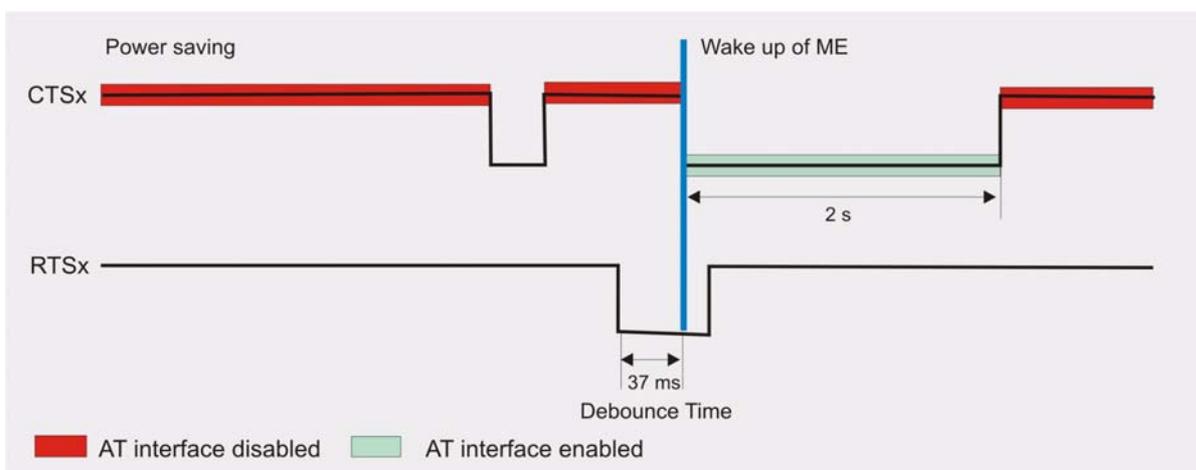


Figure 12: Timing of RTSx signal (if CFUN = 9)

3.7 Summary of State Transitions (Except SLEEP Mode)

The following table shows how to proceed from one mode to another (grey column = present mode, white columns = intended modes).

Table 13: State transitions of EES3 (except SLEEP mode)

Intended mode -->	POWER DOWN	Normal mode ¹	Charge-only mode ²	Airplane mode
Present mode				
POWER DOWN mode	---	If AT^SCFG=MeOpMode/Airplane/OnStart,off: IGT >400 ms at low level, then release IGT	Connect charger to VCHARGE	If AT^SCFG=MeOpMode/Airplane/OnStart,on: IGT >400 ms at low level, then release IGT. Regardless of AT^SCFG configuration: scheduled wake-up set with AT+CALA.
Normal mode	AT^SMSO	---	AT^SMSO if charger is connected	AT^SCFG=MeOpMode/Airplane,on. If AT^SCFG=MeOpMode/Airplane/OnStart,on: IGT >2s at low level, then release IGT
Charge-only mode	Disconnect charger	Hardware driven: If AT^SCFG=MeOpMode/Airplane/OnStart,off: IGT >2s at low level, then release IGT AT command driven: AT^SCFG= MeOpMode/Airplane,off	---	AT^SCFG=MeOpMode/Airplane,on. If AT^SCFG=MeOpMode/Airplane/OnStart,on: IGT >2s at low level, then release IGT
Airplane mode	AT^SMSO	AT^SCFG=MeOpMode/Airplane,off	AT^SMSO if charger is connected	---

1. Normal mode covers TALK, DATA, GPRS, IDLE and SLEEP modes

2. See [Section 3.5.7](#) for details on the charging mode

3.8 RTC Backup

The internal Real Time Clock of EES3 is supplied from a separate voltage regulator in the analog controller which is also active when EES3 is in POWER DOWN status. An alarm function is provided that allows to wake up EES3 to Airplane mode without logging on to the GSM network.

In addition, you can use the VDDL P line to backup the RTC from an external capacitor or a battery (rechargeable or non-chargeable). The capacitor is charged by the BATT+ line of EES3. If the voltage supply at BATT+ is disconnected the RTC can be powered by the capacitor. The size of the capacitor determines the duration of buffering when no voltage is applied to EES3, i.e. the larger the capacitor the longer EES3 will save the date and time.

A serial 1kΩ resistor placed on the board next to VDDL P limits the charge current of an empty capacitor or battery.

The following figures show various sample configurations. Please refer to [Table 27](#) for the parameters required.

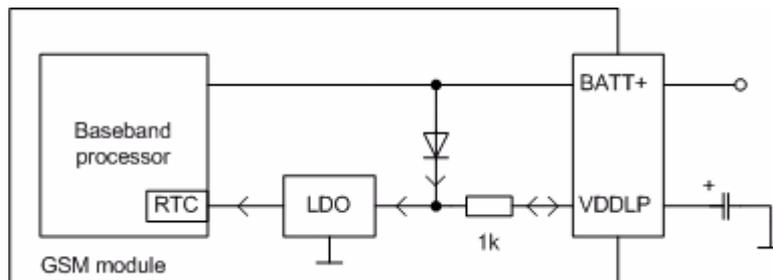


Figure 13: RTC supply from capacitor

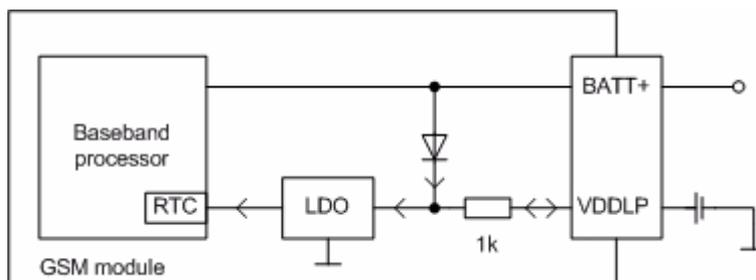


Figure 14: RTC supply from rechargeable battery

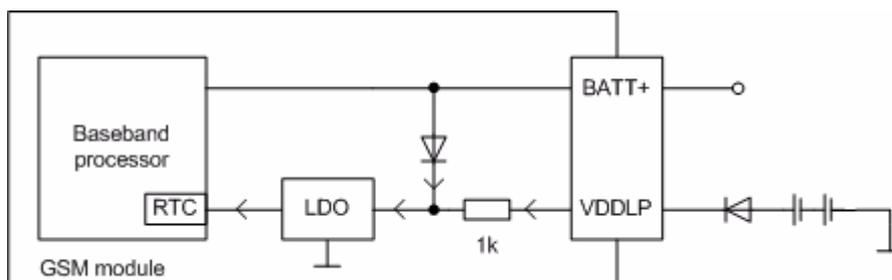


Figure 15: RTC supply from non-chargeable battery

3.9 SIM Interface

The baseband processor has an integrated SIM interface compatible with the ISO 7816 IC Card standard. This is wired to the host interface in order to be connected to an external SIM card holder. Six pads on the SMT application interface are reserved for the SIM interface.

The SIM interface supports 3V and 1.8V SIM cards. Please refer to [Table 27](#) for electrical specifications of the SIM interface lines depending on whether a 3V or 1.8V SIM card is used.

The CCIN signal serves to detect whether a tray (with SIM card) is present in the card holder. Using the CCIN line is mandatory for compliance with the GSM 11.11 recommendation if the mechanical design of the host application allows the user to remove the SIM card during operation. To take advantage of this feature, an appropriate SIM card detect switch is required on the card holder. For example, this is true for the model supplied by Molex, which has been tested to operate with EES3 and is part of the Cinterion Wireless Modules reference equipment submitted for type approval. See [Chapter 8](#) for Molex ordering numbers.

Table 14: Signals of the SIM interface (SMT application interface)

Signal	Description
CCGND	Separate ground connection for SIM card to improve EMC. A design example for grounding the SIM interface is shown in Figure 54 .
CCCLK	Chipcard clock, various clock rates can be set in the baseband processor.
CCVCC	SIM supply voltage.
CCIO	Serial data line, input and output.
CCRST	Chipcard reset, provided by baseband processor.
CCIN	Input on the baseband processor for detecting a SIM card tray in the holder. If the SIM is removed during operation the SIM interface is shut down immediately to prevent destruction of the SIM. The CCIN line is active low. The CCIN signal is mandatory for applications that allow the user to remove the SIM card during operation. The CCIN signal is solely intended for use with a SIM card. It must not be used for any other purposes. Failure to comply with this requirement may invalidate the type approval of EES3.

The total cable length between the SMT application interface pads on EES3 and the connector of the external SIM card holder must not exceed 100mm in order to meet the specifications of 3GPP TS 51.010-1 and to satisfy the requirements of EMC compliance.

To avoid possible cross-talk from the CCCLK signal to the CCIO signal be careful that both lines are not placed closely next to each other. A useful approach is using the GND line to shield the CCIO line from the CCCLK line.

Note: No guarantee can be given, nor any liability accepted, if loss of data is encountered after removing the SIM card during operation. Also, no guarantee can be given for properly initializing any SIM card that the user inserts after having removed a SIM card during operation. In this case, the application must restart EES3.

3.10 Serial Interface ASC0

EES3 offers an 8-wire unbalanced, asynchronous modem interface ASC0 conforming to ITU-T V.24 protocol DCE signalling. The electrical characteristics do not comply with ITU-T V.28. The significant levels are 0V (for low data bit or active state) and 2.9V (for high data bit or inactive state). For electrical characteristics please refer to [Table 27](#).

EES3 is designed for use as a DCE. Based on the conventions for DCE-DTE connections it communicates with the customer application (DTE) using the following signals:

- Port TXD @ application sends data to the module's TXD0 signal line
- Port RXD @ application receives data from the module's RXD0 signal line

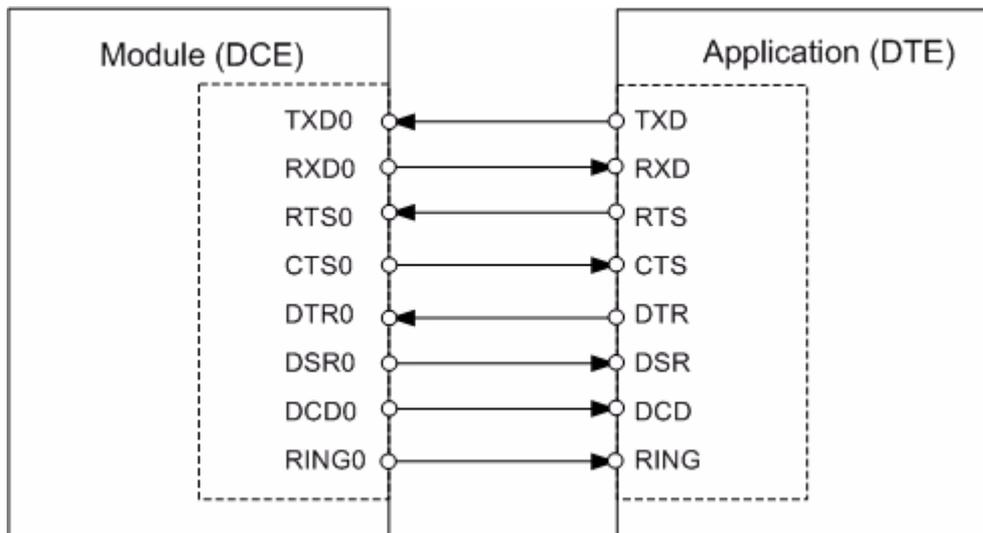


Figure 16: Serial interface ASC0

Features:

- Includes the data lines TXD0 and RXD0, the status lines RTS0 and CTS0 and, in addition, the modem control lines DTR0, DSR0, DCD0 and RING0.
- ASC0 is primarily designed for controlling voice calls, transferring CSD, fax and GPRS data and for controlling the GSM module with AT commands.
- Full Multiplex capability allows the interface to be partitioned into three virtual channels, yet with CSD and fax services only available on the first logical channel. Please note that when the ASC0 interface runs in Multiplex mode, ASC1 cannot be used. For more details on Multiplex mode see [\[12\]](#).
- The DTR0 signal will only be polled once per second from the internal firmware of EES3.
- The RING0 signal serves to indicate incoming calls and other types of URCs (Unsolicited Result Code). It can also be used to send pulses to the host application, for example to wake up the application from power saving state. See [\[1\]](#) for details on how to configure the RING0 line by AT^SCFG.
- By default, configured for 8 data bits, no parity and 1 stop bit. The setting can be changed using the AT command AT+ICF and, if required, AT^STPB. For details see [\[1\]](#).
- ASC0 can be operated at fixed bit rates from 300 bps to 921600 bps.
- Autobauding supports bit rates from 1200 to 460800 bps. To employ autobauding, the bit rate tolerance of the sender should - as a rule - be less than 2%. With bit rates ≤ 19200 bps however, the sender's bit rate tolerance must be less than 1%.
- Autobauding is not compatible with multiplex mode.
- Supports RTS0/CTS0 hardware flow control and XON/XOFF software flow control.

Table 15: DCE-DTE wiring of ASC0

V.24 circuit	DCE		DTE	
	Line function	Signal direction	Line function	Signal direction
103	TXD0	Input	TXD	Output
104	RXD0	Output	RXD	Input
105	RTS0	Input	RTS	Output
106	CTS0	Output	CTS	Input
108/2	DTR0	Input	DTR	Output
107	DSR0	Output	DSR	Input
109	DCD0	Output	DCD	Input
125	RING0	Output	RING	Input

3.11 Serial Interface ASC1

EES3 offers a 4-wire unbalanced, asynchronous modem interface ASC1 conforming to ITU-T V.24 protocol DCE signalling. The electrical characteristics do not comply with ITU-T V.28. The significant levels are 0V (for low data bit or active state) and 2.9V (for high data bit or inactive state). For electrical characteristics please refer to [Table 27](#).

EES3 is designed for use as a DCE. Based on the conventions for DCE-DTE connections it communicates with the customer application (DTE) using the following signals:

- Port TXD @ application sends data to module's TXD1 signal line
- Port RXD @ application receives data from the module's RXD1 signal line

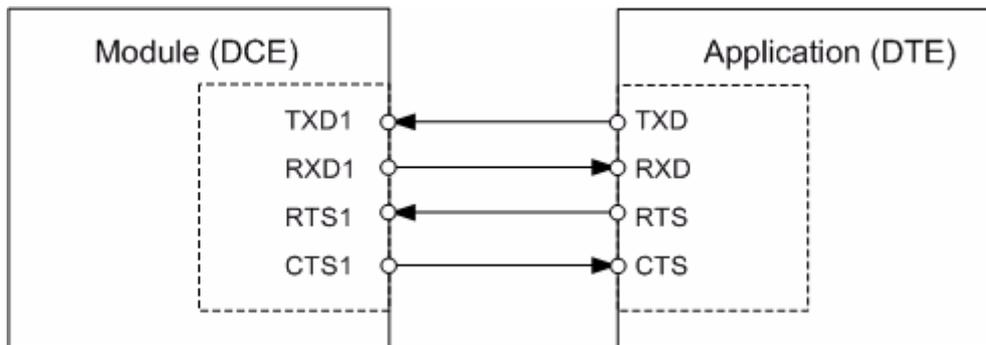


Figure 17: Serial interface ASC1

Features

- Includes only the data lines TXD1 and RXD1 plus RTS1 and CTS1 for hardware hand-shake.
- On ASC1 no RING line is available. The indication of URCs on the second interface depends on the settings made with the AT^SCFG command. For details refer to [\[1\]](#).
- Configured for 8 data bits, no parity and 1 or 2 stop bits.
- ASC1 can be operated at fixed bit rates from 300 bps to 921600 bps. Autobauding is not supported on ASC1.
- Supports RTS1/CTS1 hardware flow control and XON/XOFF software flow control.

Table 16: DCE-DTE wiring of ASC1

V.24 circuit	DCE		DTE	
	Line function	Signal direction	Line function	Signal direction
103	TXD1	Input	TXD	Output
104	RXD1	Output	RXD	Input
105	RTS1	Input	RTS	Output
106	CTS1	Output	CTS	Input

3.12 USB Interface

EES3 supports a USB 2.0 Full Speed (12Mbit/s) device interface. The USB interface is primarily intended for use as command and data interface and for downloading firmware. The USB I/O-lines are capable of driving the signal at min 3.0V. They are 5V I/O compliant.

The USB host is responsible for supplying, across the VUSB_IN line, power to the module's USB interface, but not to other EES3 interfaces. This is because EES3 is designed as a self-powered device compliant with the "Universal Serial Bus Specification Revision 2.0"¹.

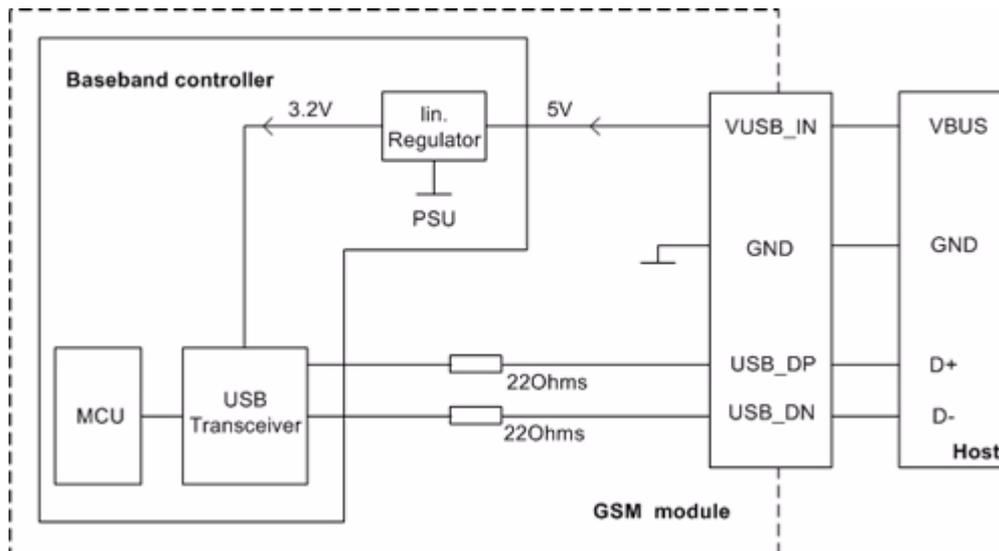


Figure 18: USB circuit

To properly connect the module's USB interface to the host a USB 2.0 compatible connector is required. For more information on how to install a USB modem driver and on how to integrate USB into EES3 applications see [10]. This Application Note also lists a selection of USB 2.0 hubs the module has been tested to operate with.

1. The specification is ready for download on <http://www.usb.org/developers/docs/>

3.13 I²C Interface

I²C is a serial, 8-bit oriented data transfer bus for bit rates up to 400kbps in Fast mode. It consists of two lines, the serial data line I2CDAT and the serial clock line I2CCLK.

The EES3 module acts as a single master device, e.g. the clock I2CCLK is driven by module. I2CDAT is a bi-directional line. Each device connected to the bus is software addressable by a unique 7-bit address, and simple master/slave relationships exist at all times. The module operates as master-transmitter or as master-receiver. The customer application transmits or receives data only on request of the module.

To configure and activate the I²C bus use the AT[^]SSPI command. If the I²C bus is active the two lines I2CCLK and I2DAT are locked for use as SPI lines. Vice versa, the activation of the SPI locks both lines for I²C. Detailed information on the AT[^]SSPI command as well explanations on the protocol and syntax required for data transmission can be found in [1].

The I²C interface can be powered from an external supply or via the VEXT line of EES3. If connected to the VEXT line the I²C interface will be properly shut down when the module enters the Power-down mode. If you prefer to connect the I²C interface to an external power supply, take care that VCC of the application is in the range of VEXT and that the interface is shut down when the PWR_IND signal goes high. See figures below as well as [Chapter 7](#) and [Figure 54](#).

In the application I2CDAT and I2CCLK lines need to be connected to a positive supply voltage via a pull-up resistor.

For electrical characteristics please refer to [Table 27](#).

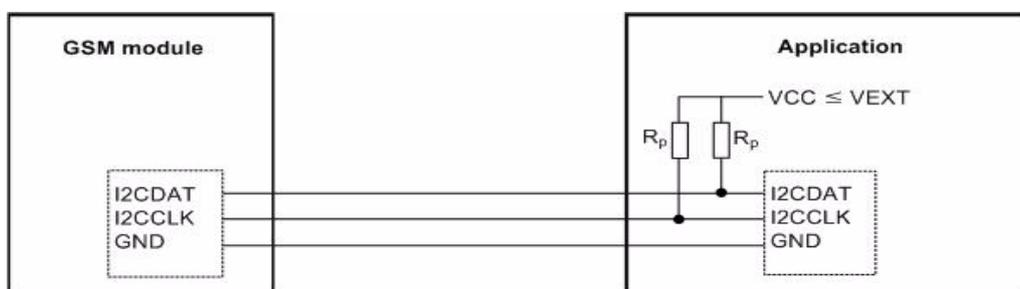


Figure 19: I²C interface connected to VCC of application

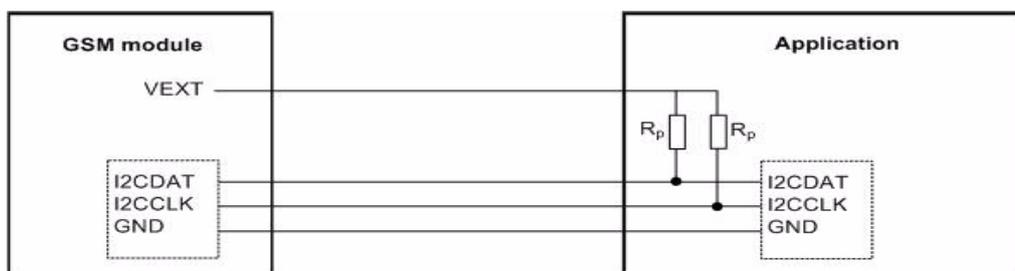


Figure 20: I²C interface connected to VEXT line of EES3

Note: Good care should be taken when creating the PCB layout of the host application: The traces of I2CCLK and I2CDAT should be equal in length and as short as possible.

3.14 SPI Interface

The SPI (serial peripheral interface) is a synchronous serial interface for control and data transfer between the EES3 module and the connected application. Only one application can be connected to the module's SPI. The interface supports transmission rates up to 6.5 Mbit/s. It consists of four lines, the two data lines SPIDI/SPIDO, the clock line SPICLK and the chip select line SPICS.

The EES3 module acts as a single master device, e.g. the clock SPICLK is driven by module. Whenever the SPICS line is in a low state, the SPI bus is activated and data can be transferred from the module and vice versa. The SPI interface uses two independent lines for data input (SPIDI) and data output (SPIDO).

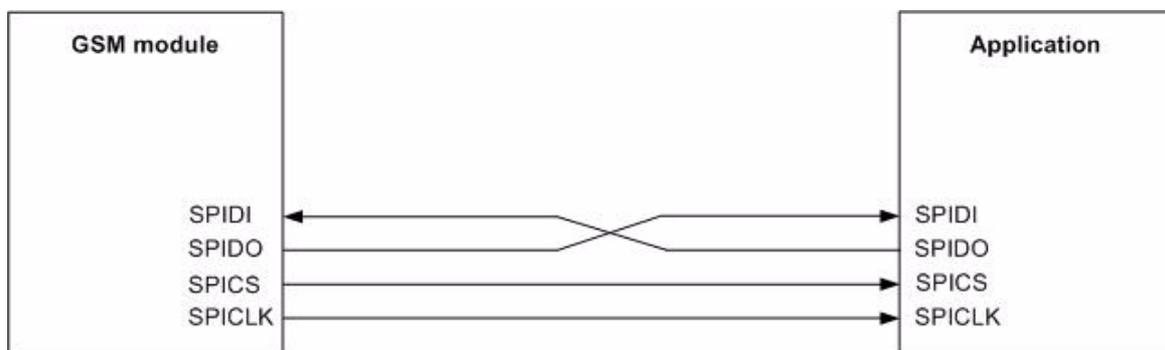


Figure 21: SPI interface

To configure and activate the SPI bus use the AT[^]SSPI command. If the SPI bus is active the two lines I2CCLK and I2DAT are locked for use as I2C lines. Detailed information on the AT[^]SSPI command as well explanations on the SPI modes required for data transmission can be found in [1].

In general, SPI supports four operation modes. The modes are different in clock phase and clock polarity. The module's SPI mode can be configured by using the AT command AT[^]SSPI. Make sure the module and the connected slave device works with the same SPI mode.

Figure 22 shows the characteristics of the four SPI modes. The SPI modes 0 and 3 are the most common used modes.

For electrical characteristics please refer to Table 27.

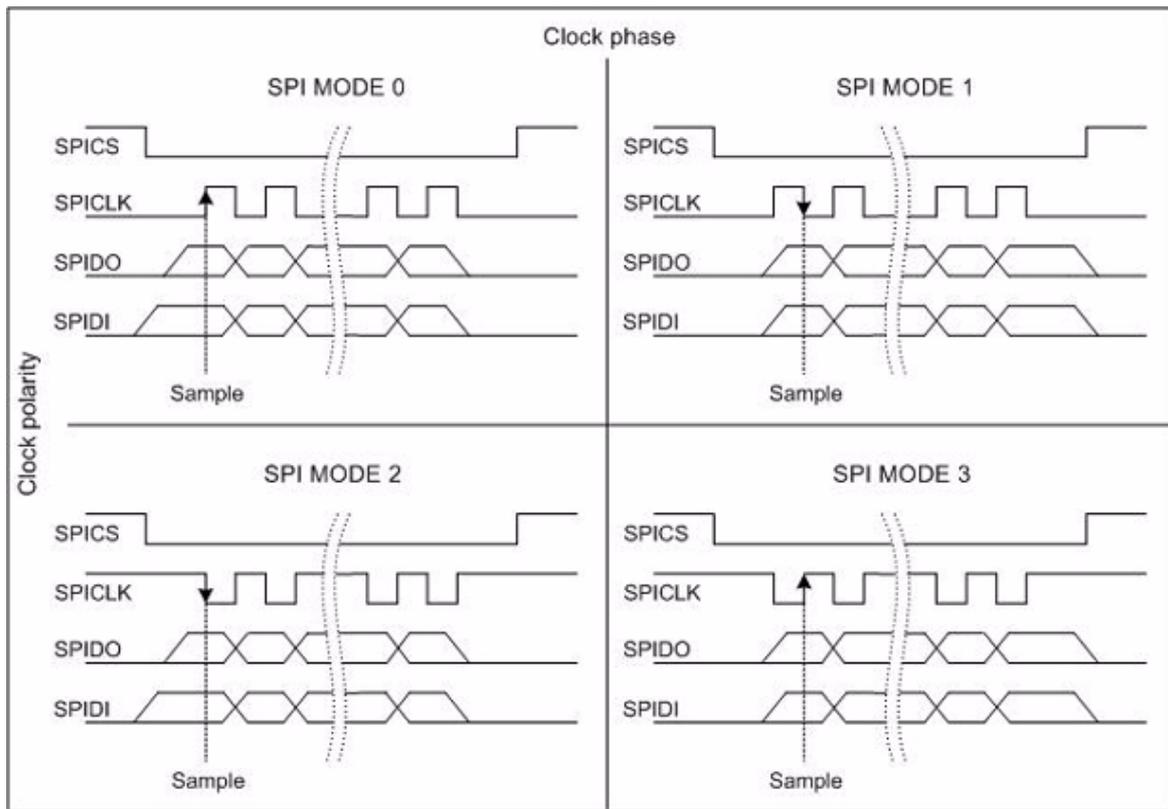


Figure 22: Characteristics of SPI modes

3.15 Audio Interfaces

EES3 comprises three audio interfaces available on the SMT application interface:

- Two analog audio interfaces.
- Serial digital audio interface (DAI) designed for PCM (Pulse Code Modulation).

This means you can connect up to three different audio devices, although only one interface can be operated at a time. Using the AT^SAIC command you can easily switch back and forth.

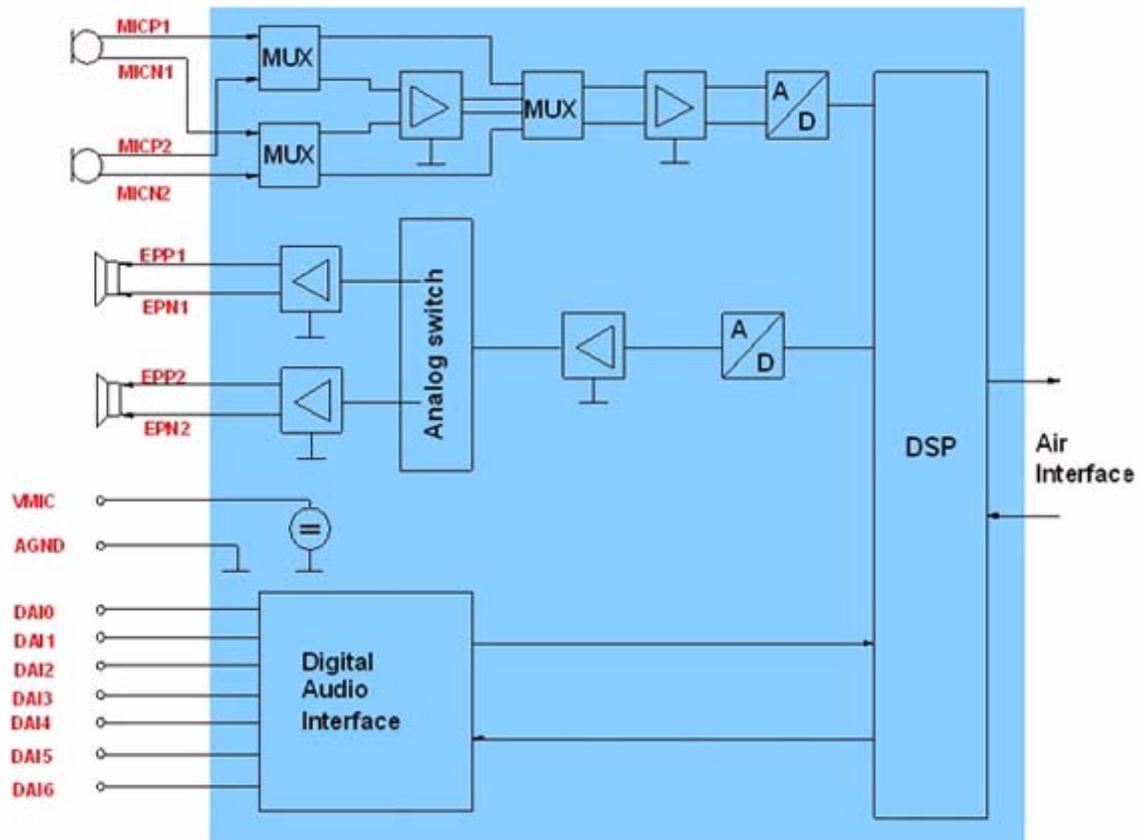


Figure 23: Audio block diagram

To suit different types of accessories the audio interfaces can be configured for different audio modes via the AT^SNFS command. The electrical characteristics of the voiceband part vary with the audio mode. For example, sending and receiving amplification, sidetone paths, noise suppression etc. depend on the selected mode and can be altered with AT commands (except for mode 1).

Both analog audio interfaces can be used to connect headsets with microphones or speakerphones. Headsets can be operated in audio mode 3, speakerphones in audio mode 2. Audio mode 5 can be used for direct access to the speech coder without signal pre or post processing.

When shipped from factory, all audio parameters of EES3 are set to interface 1 and audio mode 1. This is the default configuration optimized for the Votronic HH-SI-30.3/V1.1/0 handset and used for type approving the Cinterion Wireless Modules reference configuration. Audio mode 1 has fix parameters which cannot be modified. To adjust the settings of the Votronic handset simply change to another audio mode.

3.15.1 Speech Processing

The speech samples from the ADC or DAI are handled by the DSP of the baseband controller to calculate e.g. amplifications, sidetone, echo cancellation or noise suppression depending on the configuration of the active audio mode. These processed samples are passed to the speech encoder. Received samples from the speech decoder are passed to the DAC or DAI after post processing (frequency response correction, adding sidetone etc.).

Full rate, half rate, enhanced full rate, adaptive multi rate (AMR), speech and channel encoding including voice activity detection (VAD) and discontinuous transmission (DTX) and digital GMSK modulation are also performed on the GSM baseband processor.

3.15.2 Microphone Circuit

EES3 has two identical analog microphone inputs. There is no on-board microphone supply circuit, except for the internal voltage supply VMIC and the dedicated audio ground line AGND. Both lines are well suited to feed a balanced audio application or a single-ended audio application.

The AGND line on the EES3 board is especially provided to achieve best grounding conditions for your audio application. As there is less current flowing than through other GND lines of the module or the application, this solution will avoid hum and buzz problems.

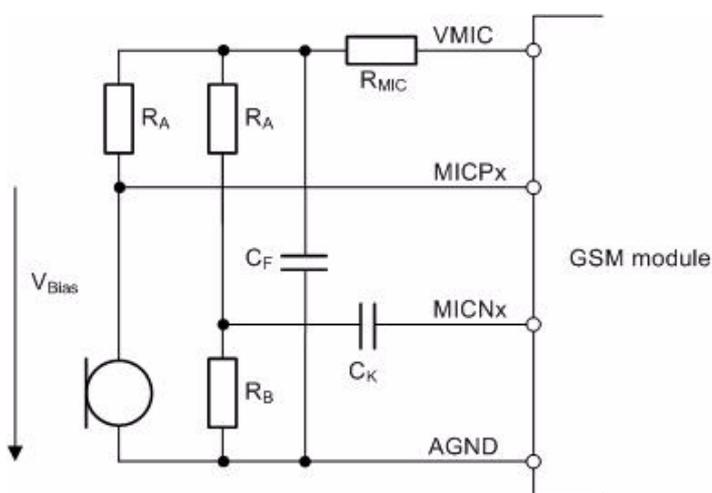
While EES3 is in Power-down mode, the input voltage at any MIC line must not exceed $\pm 0.3V$ relative to AGND (see also [Section 5.1](#)). In any other operating state the voltage applied to any MIC line must be in the range of 2.4V to 0V, otherwise undervoltage shutdown may be caused. Consider that the maximum full scale input voltage is $V_{pp} = 1.6V$.

If VMIC is used to generate the MICP line bias voltage as shown in the following examples consider that VMIC is switched off (0V) outside a call. Audio signals applied to MICP in this case must not fall below -0.3V.

If higher input levels are used especially in the line input configuration the signal level must be limited to $600mV_{pp}$ outside a call, or $AT^{\wedge}SNFM=,1$ should be used to switch on VMIC permanently.

3.15.2.1 Single-ended Microphone Input

Figure 24 as well as Figure 54 show an example of how to integrate a single-ended microphone input.



$R_A = \text{typ. } 2\text{k}$
 $R_B = \text{typ. } 5\text{k}$
 $R_{VMIC} = \text{typ. } 470\Omega$

$C_K = \text{typ. } 100\text{nF}$
 $C_F = \text{typ. } 22\mu\text{F}$

$V_{MIC} = \text{typ. } 2.5\text{V}$

$V_{bias} = 1.0\text{V} \dots 1.6\text{V}, \text{typ. } 1.5\text{V}$

Figure 24: Single ended microphone input

R_A has to be chosen so that the DC voltage across the microphone falls into the bias voltage range of 1.0V to 1.6V and the microphone feeding current meets its specification.

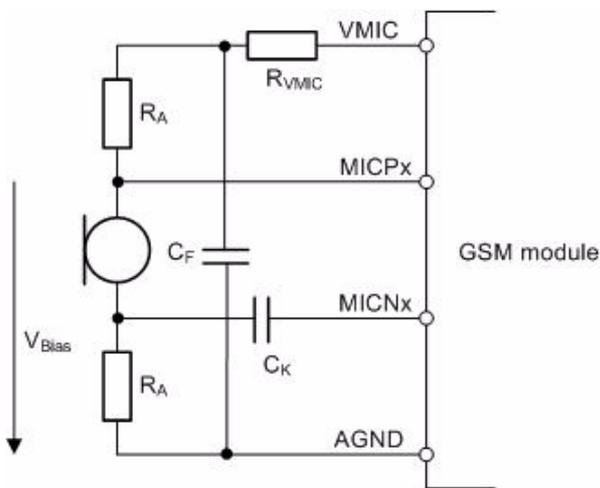
The MICNx input is automatically self biased to the MICPx DC level. It is AC coupled via C_K to a resistive divider which is used to optimize supply noise cancellation by the differential microphone amplifier in the module.

The VMIC voltage should be filtered if gains larger than 20dB are used. The filter can be attached as a simple first order RC-network (R_{VMIC} and C_F).

This circuit is well suited if the distance between microphone and module is kept short. Due to good grounding the microphone can be easily ESD protected as its housing usually connects to the negative terminal.

3.15.2.2 Differential Microphone Input

Figure 25 shows a differential solution for connecting an electret microphone.



$$R_A = \text{typ. } 1\text{k}$$

$$R_{VMIC} = 470\Omega$$

$$C_K = \text{typ. } 100\text{nF}$$

$$C_F = \text{typ. } 22\mu\text{F}$$

$$V_{MIC} = \text{typ. } 2.5\text{V}$$

$$V_{\text{bias}} = 1.0\text{V} \dots 1.6\text{V, typ. } 1.5\text{V}$$

Figure 25: Differential microphone input

The advantage of this circuit is that it can be used if the application involves longer lines between microphone and module.

While VMIC is switched off, the input voltage at any MIC line should not exceed $\pm 0.25\text{V}$ relative to AGND (see also [Section 5.1](#)). In this case no bias voltage has to be supplied from the customer circuit to the MIC line and any signal voltage should be smaller than $V_{pp} = 0.5\text{V}$.

VMIC can be used to generate the MICP line bias voltage as shown below. In this case the bias voltage is only applied if VMIC is switched on.

Only if VMIC is switched on, can the voltage applied to any MIC line be in the range of 2.4V to 0V. If these limits are exceeded undervoltage shutdown may be caused.

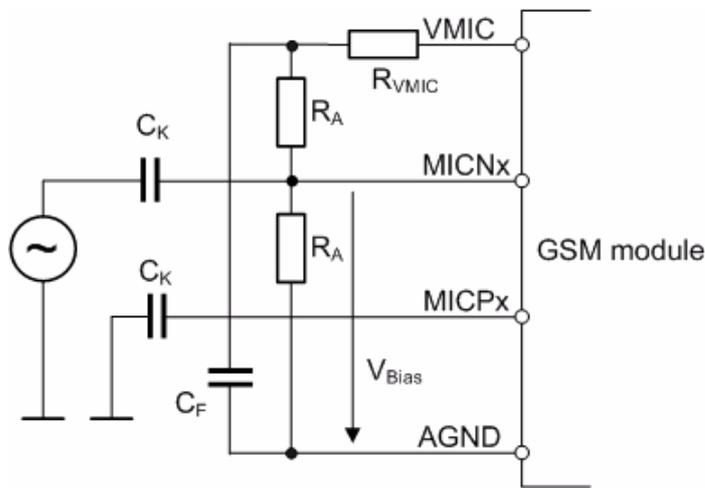
Consider that the maximum full scale input voltage is $V_{pp} = 1.6\text{V}$.

The behavior of VMIC can be controlled with the parameter `micVccCtl` of the AT command `AT^SNFM` (see [\[1\]](#)):

- `micVccCtl=2` (default). VMIC is controlled automatically by the module. VMIC is always switched on while the internal audio circuits of the module are active (e.g., during a call). VMIC can be used as indicator for active audio in the module.
- `micVccCtl=1`. VMIC is switched on continuously. This setting can be used to supply the microphone in order to use the signal in other customer circuits as well. However, this setting leads to a higher current consumption in SLEEP modes.
- `micVccCtl=0`. VMIC is permanently switched off.

3.15.2.3 Line Input Configuration with OpAmp

Figure 26 shows an example of how to connect an opamp into the microphone circuit.



$$R_A = \text{typ. } 47\text{k}$$

$$R_{VMIC} = 470\text{Ohm}$$

$$C_k = \text{typ. } 100\text{nF}$$

$$C_F = \text{typ. } 22\mu\text{F}$$

$$V_{MIC} = \text{typ. } 2.5\text{V}$$

$$V_{bias} = \text{typ. } \frac{1}{2} V_{MIC} = 1.25\text{V}$$

Figure 26: Line input configuration with OpAmp

The AC source (e.g. an opamp) and its reference potential have to be AC coupled to the MICNx resp. MICPx input terminals. The voltage divider between VMIC and AGND is necessary to bias the input amplifier. MICPx is automatically self biased to the MICNx DC level.

The VMIC voltage should be filtered if gains larger than 20dB are used. The filter can be attached as a simple first order RC-network (R_{VMIC} and C_F). If a high input level and a lower gain are applied the filter is not necessary.

Consider that if VMIC is switched off, the signal voltage should be limited to $V_{pp} = 0.5\text{V}$ and any bias voltage must not be applied. Otherwise VMIC can be switched on permanently by using $AT^{\wedge}SNFM=,1$. In this case the current consumption in SLEEP modes is higher.

If desired, MICPx via C_k can also be connected to the inverse output of the AC source instead of connecting it to the reference potential for differential line input.

3.15.3 Loudspeaker Circuit

The GSM module comprises two analog differential speaker outputs: EP1 and EP2. Output EP1 is able to drive a load of 8Ohms while the output EP2 can drive a load of 32Ohms. Interface EP2 can also be connected in single ended configuration. [Figure 27](#) shows an example of a differential loudspeaker configuration.

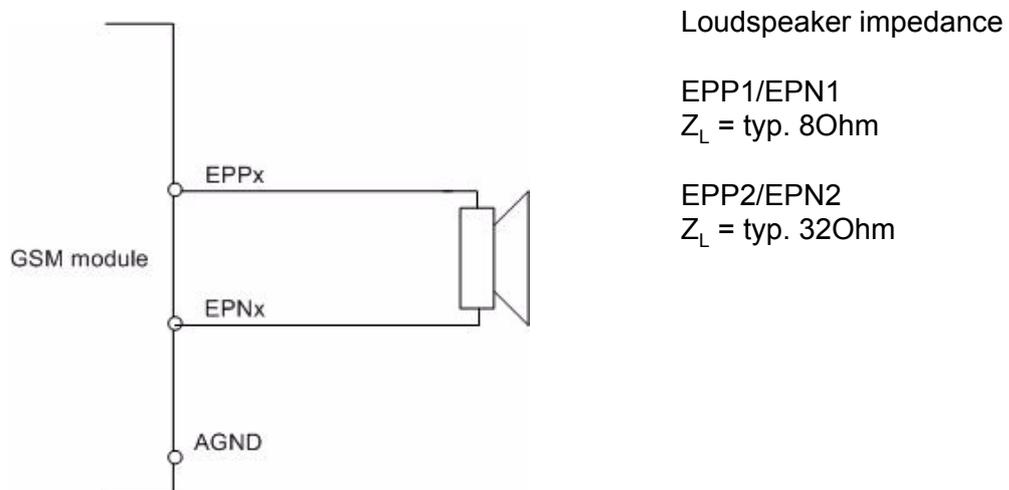


Figure 27: Differential loudspeaker configuration

3.15.4 Digital Audio Interface (DAI)

The DAI can be used to connect audio devices capable of PCM (Pulse Code Modulation) or for type approval. The following chapters describe the PCM interface functionality.

The PCM functionality allows the use of a codec like for example the MC145483. This codec replaces the analog audio inputs and outputs during a call, if digital audio is selected by AT^SA-IC.

The PCM interface is configurable with the AT^SAIC command (see [\[1\]](#)) and supports the following features:

- Master and slave mode
- Short frame and long frame synchronization
- 256 kHz or 512 kHz bit clock frequency

For the PCM interface configuration the parameters <clock>, <mode> and <framemode> of the AT^SAIC command are used. The following table lists possible combinations:

Table 17: Configuration combinations for the PCM interface

Configuration	<clock>	<mode>	<framemode>
Master, 256kHz, short frame	0	0	0
Master, 256kHz, long frame	0	0	1
Master, 512kHz, short frame	1	0	0
Master, 512kHz, long frame	1	0	1
Slave, 256kHz, short frame	0 or 1 ¹	1	0
Slave, 256kHz, long frame	0 or 1	1	1
Slave, 512kHz, short frame	0 or 1	1	0
Slave, 512kHz, long frame	0 or 1	1	1

1. In slave mode the BCLKIN signal is directly used for data shifting. Therefore, the clock frequency setting is not evaluated and may be either 0 or 1.

In all configurations the PCM interface has the following common features:

- 16 Bit linear
- 8kHz sample rate
- the most significant bit MSB is transferred first
- 125µs frame duration
- common frame sync signal for transmit and receive

Table 18 shows the assignment of the DAI0...6 signals to the PCM interface signals. To avoid hardware conflicts different lines are used as inputs and outputs for frame sync and clock signals in master or slave operation. The table shows also which line is used for master or slave. The data lines (TXDAI and RXDAI) however are used in both modes. Unused inputs should be tied to GND via pull down resistors. In addition, DAI1 requires a 47kOhm pull down resistor to be placed as close as possible to the module. Unused outputs must be left open.

Table 18: Overview of DAI signal functions

Signal name	Function for PCM Interface		Input/Output
DAI0	TXDAI	Master/Slave	O
DAI1	RXDAI	Master/Slave	I
DAI2	FS (Frame sync)	Master	O
DAI3	BITCLK	Master	O
DAI4	FSIN	Slave	I
DAI5	BCLKIN	Slave	I
DAI6	nc		I

3.15.4.1 Master Mode

To clock input and output PCM samples the PCM interface delivers a bit clock (BITCLK) which is synchronous to the GSM system clock. The frequency of the bit clock is 256kHz or 512kHz. Any edge of this clock deviates less than $\pm 100\text{ns}$ (Jitter) from an ideal 256-kHz clock respectively deviates less than $\pm 320\text{ns}$ from an ideal 512-kHz clock.

The frame sync signal (FS) has a frequency of 8kHz and is high for one BITCLK period before the data transmission starts if short frame is configured. If long frame is selected the frame sync signal (FS) is high during the whole transfer of the 16 data bits. Each frame has a duration of $125\mu\text{s}$ and contains 32 respective 64 clock cycles.

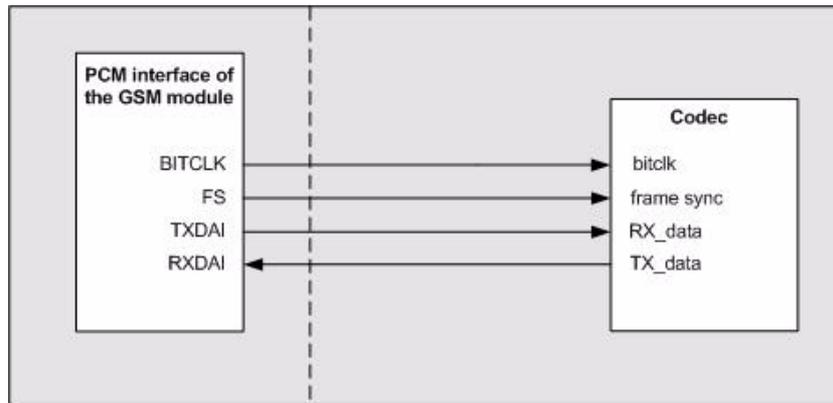


Figure 28: Master PCM interface Application

The timing of a PCM **short frame** is shown in Figure 29. The 16-bit TXDAI and RXDAI data is transferred simultaneously in both directions during the first 16 clock cycles after the frame sync pulse. The duration of a frame sync pulse is one BITCLK period, starting at the rising edge of BITCLK. TXDAI data is shifted out at the next rising edge of BITCLK. RXDAI data (i.e. data transmitted from the host application to the module's RXDAI line) is sampled at the falling edge of BITCLK.

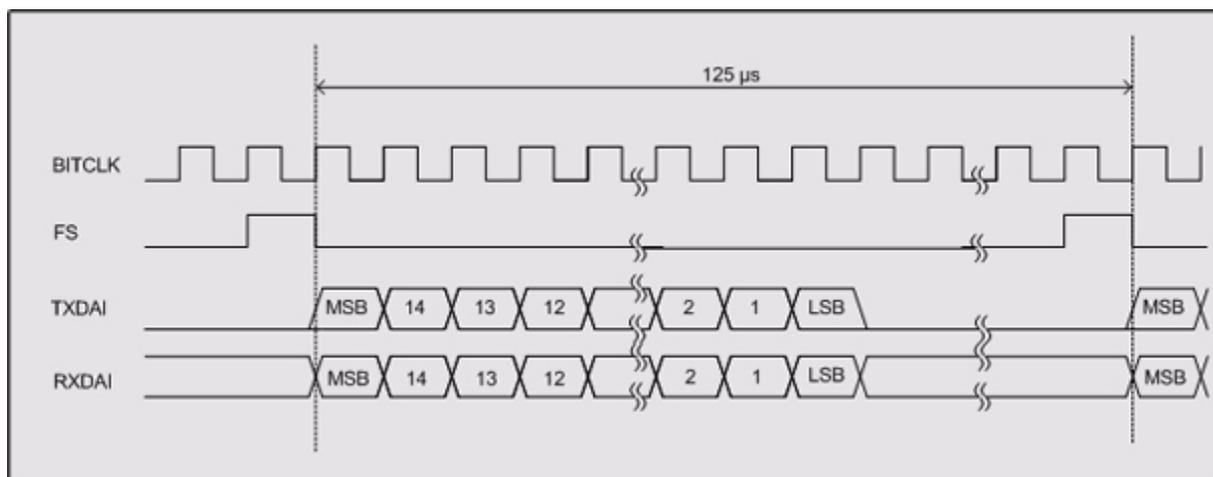


Figure 29: Short Frame PCM timing

The timing of a PCM **long frame** is shown in [Figure 30](#). The 16-bit TXDAI and RXDAI data is transferred simultaneously in both directions while the frame sync pulse FS is high. For this reason the duration of a frame sync pulse is 16 BITCLK periods, starting at the rising edge of BITCLK. TXDAI data is shifted out at the same rising edge of BITCLK. RXDAI data (i.e. data transmitted from the host application to the module's RXDAI line) is sampled at the falling edge of BITCLK.

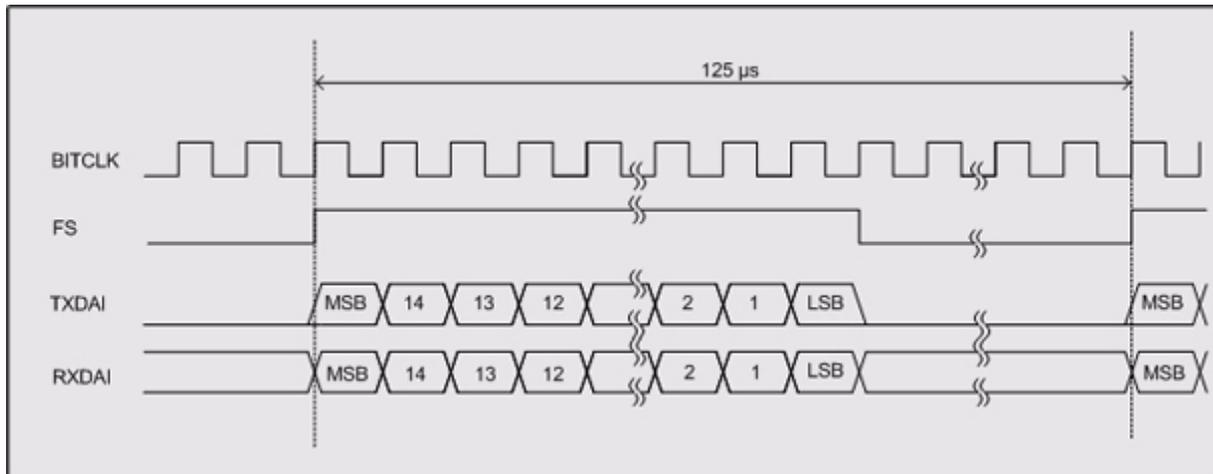


Figure 30: Long Frame PCM timing

3.15.4.2 Slave Mode

In slave mode the PCM interface is controlled by an external bit clock and an external frame sync signal applied to the BCLKIN and FSIN lines and delivered either by the connected codec or another source. The bit clock frequency has to be in the range of 256kHz -125ppm to 512kHz +125ppm.

Data transfer starts at the falling edge of FSIN if the short frame format is selected, and at the rising edge of FSIN if long frame format is selected. With this edge control the frame sync signal is independent of the frame sync pulse length.

TXDAI data is shifted out at the rising edge of BCLKIN. RXDAI data (i.e. data transmitted from the host application to the module's RXDAI line) is sampled at the falling edge of BCLKIN.

The deviation of the external frame rate from the internal frame rate must not exceed ± 125 ppm. The internal frame rate of nominal 8kHz is synchronized to the GSM network.

The difference between the internal and the external frame rate is equalized by doubling or skipping samples. This happens for example every second, if the difference is 125ppm.

The resulting distortion can be neglected in speech signals.

The lines BITCLK and FS remain low in slave mode.

The below [Figure 31](#) shows the typical slave configuration. The external codec delivers the bit clock and the frame sync signal. If the codec itself is not able to run in master mode as for example the MC145483, a third party has to generate the clock and the frame sync signal.

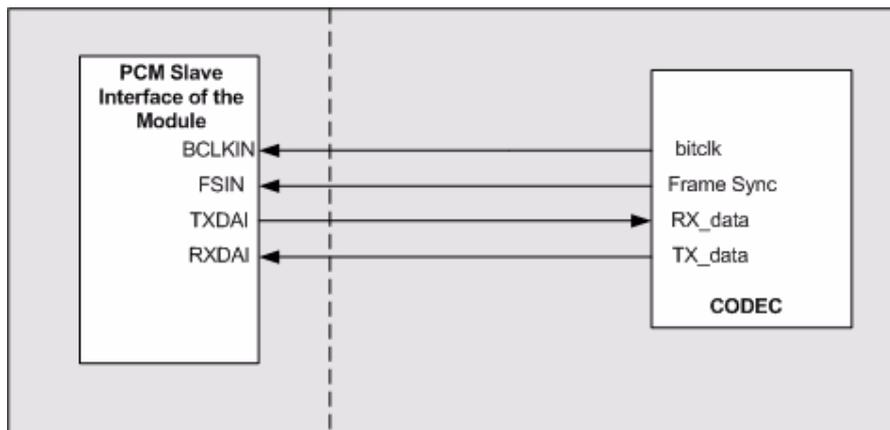


Figure 31: Slave PCM interface application

The following figures show the slave short and long frame timings. Because these are edge controlled, frame sync signals may deviate from the ideally form as shown with the dotted lines.

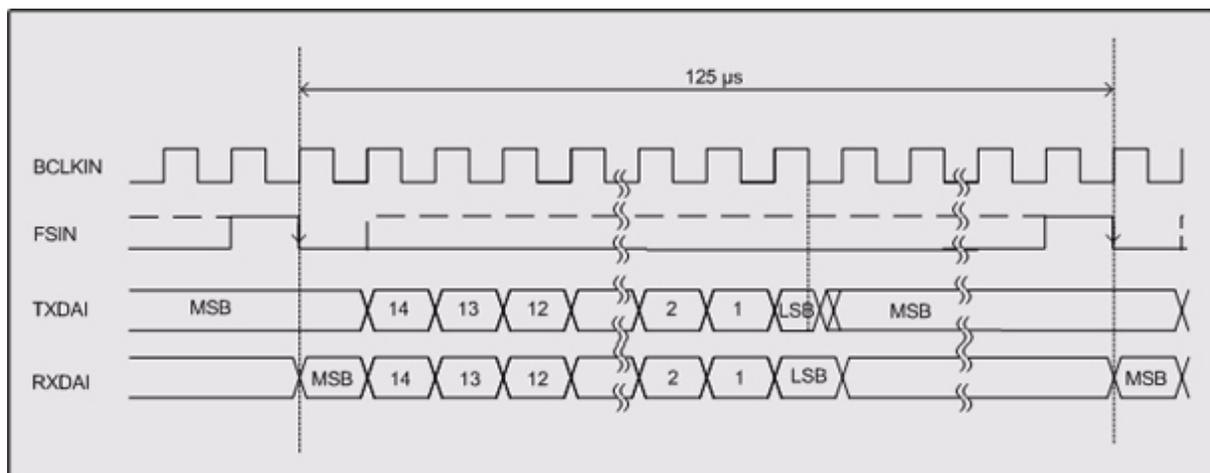


Figure 32: Slave PCM Timing, Short Frame selected

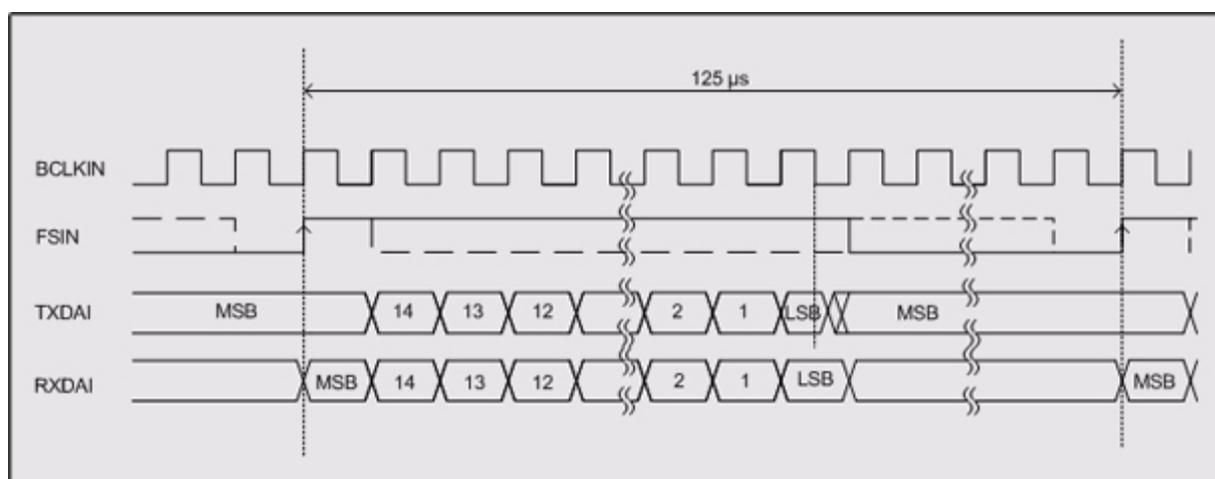


Figure 33: Slave PCM Timing, Long Frame selected

3.16 Control Signals

3.16.1 Synchronization Signal

The synchronization signal serves to indicate growing power consumption during the transmit burst. The signal is generated by the SYNC line. Please note that this line can adopt three different operating modes which you can select by using the AT[^]SSYNC command: the mode AT[^]SSYNC=0 described below, and the two LED modes AT[^]SSYNC=1 or AT[^]SSYNC=2 described in [1] and Section 3.16.2.

The first function (factory default AT[^]SSYNC=0) is recommended if you want your application to use the synchronization signal for better power supply control. Your platform design must be such that the incoming signal accommodates sufficient power supply to the EES3 module if required. This can be achieved by lowering the current drawn from other components installed in your application.

The timing of the synchronization signal is shown below. High level of the SYNC line indicates increased power consumption during transmission.

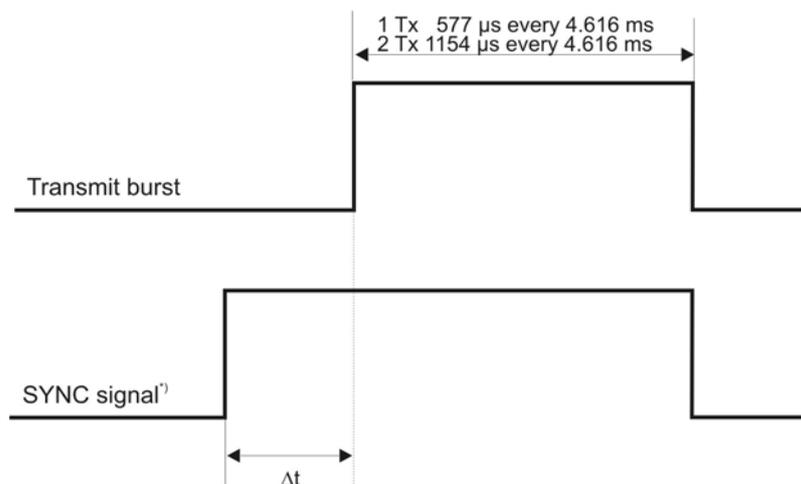


Figure 34: SYNC signal during transmit burst

^{*)}The duration of the SYNC signal is always equal, no matter whether the traffic or the access burst are active. Δt is a fixed time in the range of 100 μ s...200 μ s.

3.16.2 Using the SYNC Line to Control a Status LED

As an alternative to generating the synchronization signal, the SYNC line can be configured to drive a status LED that indicates different operating modes of the EES3 module. To take advantage of this function the LED mode must be activated with the AT[^]SSYNC command and the LED must be connected to the host application. The connected LED can be operated in two different display modes (AT[^]SSYNC=1 or AT[^]SSYNC=2). For details please refer to [1].

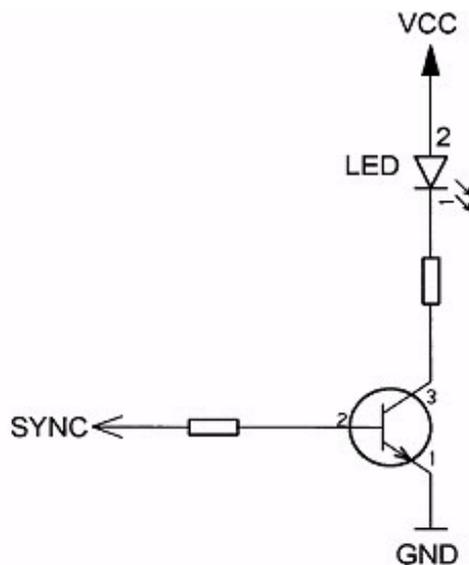


Figure 35: LED Circuit (Example)

Especially in the development and test phase of an application, system integrators are advised to use the LED mode of the SYNC line in order to evaluate their product design and identify the source of errors.

To operate the LED a buffer, e.g. a transistor or gate, must be included in your application. A sample circuit is shown in Figure 35. Power consumption in the LED mode is the same as for the synchronization signal mode. For details see Table 27, SYNC signal.

3.16.3 Behavior of the RING0 Line (ASC0 Interface only)

The RING0 line is available on the first serial interface ASC0 (see also [Section 3.10](#)). The signal serves to indicate incoming calls and other types of URCs (Unsolicited Result Code).

Although not mandatory for use in a host application, it is strongly suggested that you connect the RING0 line to an interrupt line of your application. In this case, the application can be designed to receive an interrupt when a falling edge on RING0 occurs. This solution is most effective, particularly, for waking up an application from power saving. Note that if the RING0 line is not wired, the application would be required to permanently poll the data and status lines of the serial interface at the expense of a higher current consumption. Therefore, utilizing the RING0 line provides an option to significantly reduce the overall current consumption of your application.

The behavior of the RING0 line varies with the type of event:

- When a voice/fax/data call comes in the RING0 line goes low for 1s and high for another 4s. Every 5 seconds the ring string is generated and sent over the /RXD0 line. If there is a call in progress and call waiting is activated for a connected handset or hands-free device, the RING0 line switches to ground in order to generate acoustic signals that indicate the waiting call.

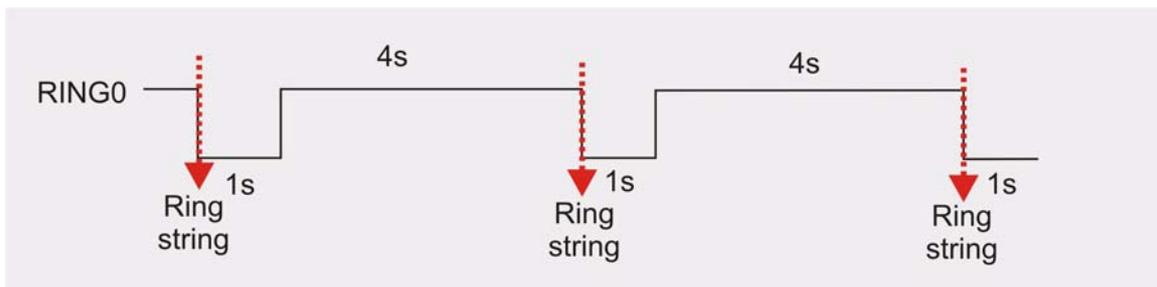


Figure 36: Incoming voice/fax/data call

- All other types of Unsolicited Result Codes (URCs) also cause the RING0 line to go low, however for 1 second only.

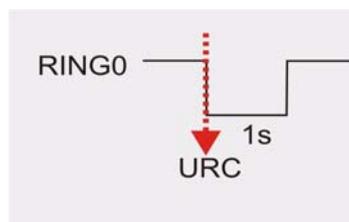


Figure 37: URC transmission

3.16.4 PWR_IND Signal

PWR_IND notifies the on/off state of the module. High state of PWR_IND indicates that the module is switched off. The state of PWR_IND immediately changes to low when IGT is pulled low. For state detection an external pull-up resistor is required.

4 Antenna Interface

The RF interface has an impedance of 50Ω. EES3 is capable of sustaining a total mismatch at the antenna interface without any damage, even when transmitting at maximum RF power.

The external antenna must be matched properly to achieve best performance regarding radiated power, modulation accuracy and harmonic suppression. Antenna matching networks are not included on the EES3 module and should be placed in the host application.

Regarding the return loss EES3 provides the following values in the active band:

Table 19: Return loss in the active band

State of module	Return loss of module	Recommended return loss of application
Receive	≥ 8dB	≥ 12dB
Transmit	not applicable	≥ 12dB

4.1 Antenna Installation

The antenna is connected by soldering the antenna pad (RF_OUT, i.e., pad #96) and its neighboring ground pads (GND, i.e., pads #81 and #119) directly to the application’s PCB.

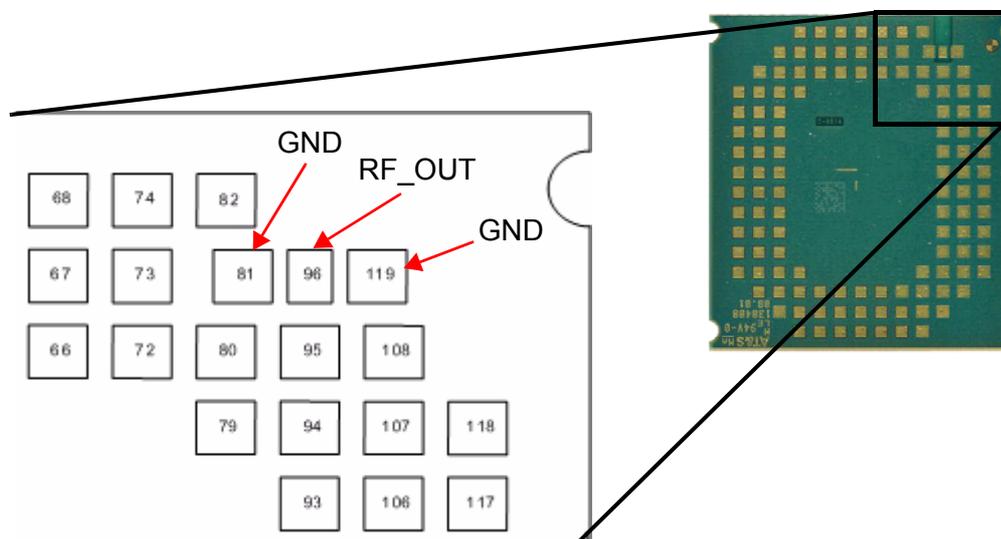


Figure 38: Antenna pads

The distance between the antenna RF_OUT pad (#96) and its neighboring GND pads (#81, #119) has been optimized for best possible impedance. To prevent mismatch, special attention should be paid to these 3 pads on the application’ PCB.

The wiring of the antenna connection, starting from the antenna pad to the application’s antenna should result in a 50Ω line impedance. Line width and distance to the GND plane needs to be optimized with regard to the PCB’s layer stack, as well as material constants.

Note: As shown in [Figure 38](#) the ground copper area between the antenna RF_OUT pad and the side of the module is slightly carved. This area should be used for the antenna line.

To prevent receiver desensitization due to interferences from components on the application PCB, the antenna connection line should be shielded, using Stripline technology rather than Microstrip. Please see [Section 4.2](#) for an example of how to design the antenna connection in order to achieve the required 50Ω line impedance.

For type approval purposes, the module can be equipped with an optional coaxial antenna connector (U.FL-R-SMT) along with other necessary components. The U.FL-R-SMT connector has been chosen as antenna reference point (ARP) for the Cinterion Wireless Modules reference equipment submitted to type approve EES3. All RF data specified throughout this document is related to the ARP.

Due to the immediate vicinity of both, the ARP and the antenna pad, no differences in the RF parameters are expected.

4.2 RF Line Routing Design

To give an example, Cinterion has developed an interface adapter board for EES3 that gives a hint of how an application board could be designed with respect to the correct RF line impedance.

The interface board has a 4 layer PCB stack - as shown in [Figure 39](#).

Layer Number	Thickness	Epsilon R	50 Ohm Microstrip Line				
1	25μm	Cu	GND	200μm	800μm	200μm	GND
	45μm	4.2					
2	25μm	Cu					GND
	1200μm	4.7					
4	25μm	Cu					GND
	45μm	4.2					
6	25μm	Cu					Routing

Figure 39: 4 layer PCB stack for EES3 interface board

Depending on specific material characteristics, on standard FR-4 glass fabric epoxy composite substrates (as here with 1.2mm thickness) a line width of $800\mu\text{m}$, within a neighbouring ground-plane with a clearance zone of $200\mu\text{m}$ to both sides, results in an RF line impedance of 50Ohms, as shown in [Figure 39](#).

These line parameters - $800\mu\text{m}$ width, $1.200\mu\text{m}$ distance to ground and $200\mu\text{m}$ distance to both sides - are used for the wiring outside the area populated by the EES3 module, i.e., the transmission line to the antenna connector as shown in [Figure 40](#).

Within the area populated by the EES3 module, the RF line width shall be reduced to $700\mu\text{m}$ and the distance to the surrounding ground area shall be increased to $450\mu\text{m}$. This modification compensates for the module's permittivity that increases the line capacitance.

The RF line on the application board populated by the module should lead directly from the antenna pads to the side of the module thereby using the slightly carved out area that is shown in [Figure 38](#).

For matching purposes, two components can be populated on the interface board. On the sample interface board the serial component is populated with a 0-Ohm-resistor (size 0402), the shunt element is set to N.C. (not populated).

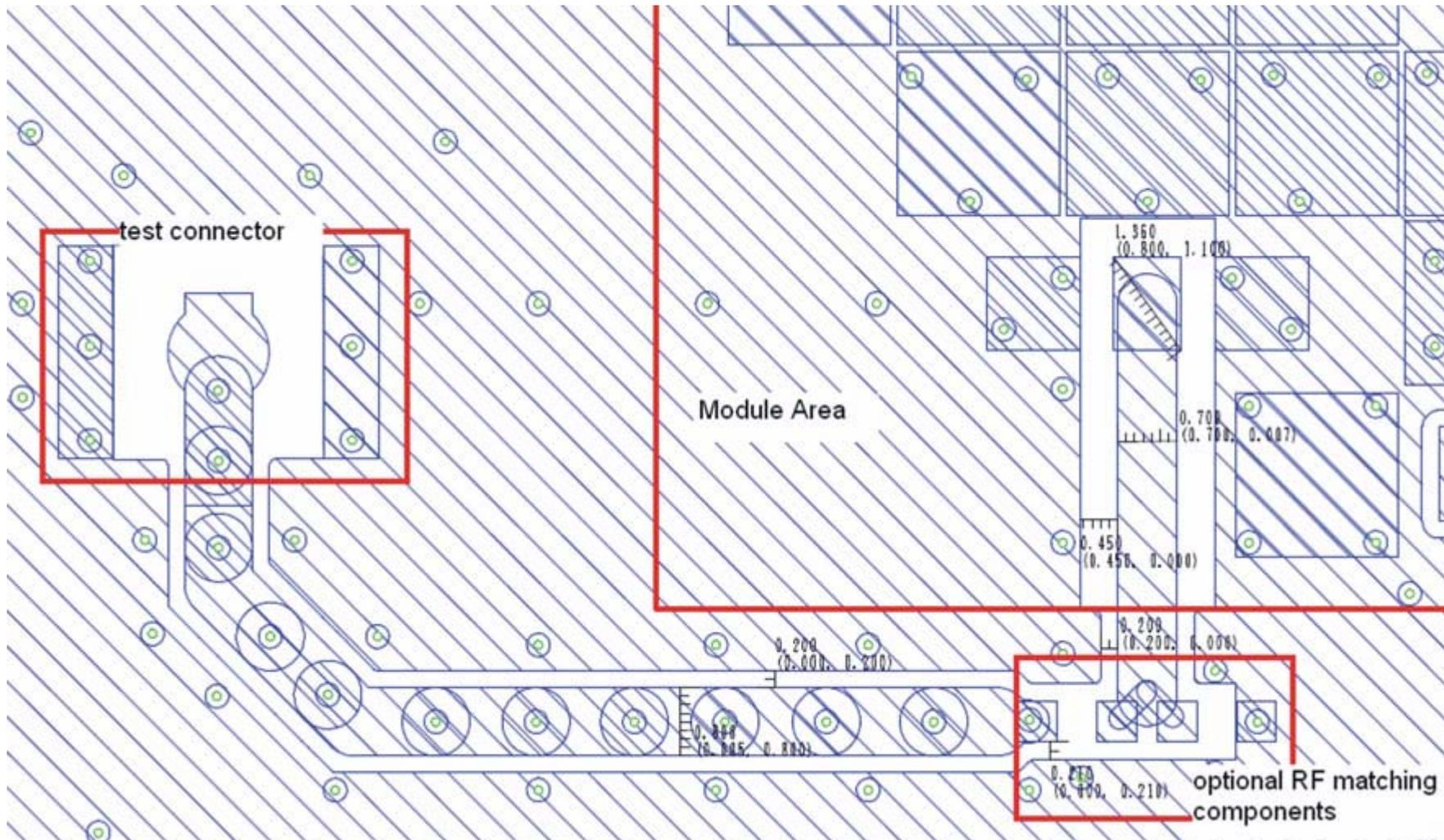


Figure 40: RF line on interface board. All dimensions are given in mm

5 Electrical, Reliability and Radio Characteristics

5.1 Absolute Maximum Ratings

The absolute maximum ratings stated in [Table 20](#) are stress ratings under any conditions. Stresses beyond any of these limits will cause permanent damage to EES3.

Table 20: Absolute maximum ratings

Parameter	Min	Max	Unit
Peak current of power supply		3.0	A
Supply voltage BATT+	-0.3	4.9	V
Voltage at digital lines in POWER DOWN mode	-0.3	0.3	V
Voltage at digital lines in normal operation	-0.3	3.05 or VEXT+0.3	V
Voltage at analog lines in POWER DOWN mode	-0.3	0.3	V
Voltage at analog lines, VMIC on ¹	-0.3	3.0	V
Voltage at analog lines, VMIC off ¹	-0.3	0.3	V
Voltage at VCHARGE line	-0.3	7.0	V
Voltage at CHARGE GATE line	-0.3	7.0	V
VUSB_IN	-0.3	5.5	V
USB_DP, USB_DN	-0.3	3.5	V
VSENSE		5.5	V
ISENSE		5.5	V
PWR_IND	-0.3	10	V
VDDL	-0.3	5.5	V

1. For normal operation the voltage at analog lines with *VMIC on* should be within the range of 0V to 2.4V and with *VMIC off* within the range of -0.25V to 0.25V.

5.2 Operating Temperatures

Table 21: Board / battery temperature

Parameter	Min	Typ	Max	Unit
Normal operation	-30	+25	+80	°C
Restricted operation ¹	-30 to -40	---	+80 to +90	°C
Automatic shutdown ²				
Temperature measured on EES3 board	-40	---	>+90	°C
Temperature measured at battery NTC	-20	---	+60	

1. Restricted operation allows normal mode speech calls or data transmission for limited time until automatic thermal shutdown takes effect. The duration of emergency calls is unlimited because automatic thermal shutdown is deferred until hang up.
2. Due to temperature measurement uncertainty, a tolerance on the stated shutdown thresholds may occur. The possible deviation is in the range of $\pm 3^{\circ}\text{C}$ at the overtemperature limit and $\pm 5^{\circ}\text{C}$ at the under-temperature limit.

Table 22: Ambient temperature according to IEC 60068-2 (without forced air circulation)¹

Parameter	Min	Typ	Max	Unit
Normal operation	-30	+25	+75	°C
Restricted operation ²	-30 to -40	---	+75 to +85	°C

1. Temperature values are based on a setup with EES3 mounted onto an adapter without any heat generating components and connected via flex cable to the Cinterion DSB75 Evaluation Kit.
2. Restricted operation allows normal mode speech calls or data transmission for limited time until automatic thermal shutdown takes effect. The duration of emergency calls is unlimited because automatic thermal shutdown is deferred until hang up.

Table 23: Charging temperature

Parameter	Min	Typ	Max	Unit
Battery temperature for software controlled fast charging (measured at battery NTC)	0	---	+45	°C

Note:

- See [Section 3.3.4](#) for further information about the NTCs for on-board and battery temperature measurement, automatic thermal shutdown and alert messages.
- When data are transmitted over EGPRS or GPRS the EES3 automatically reverts to a lower Multislot Class if the temperature increases to the limit specified for normal operation and, vice versa, returns to the higher Multislot Class if the temperature is back to normal. For details see [Section 3.4](#).

5.3 Storage Conditions

The conditions stated below are only valid for modules in their original packed state in weather protected, non-temperature-controlled storage locations. Normal storage time under these conditions is 12 months maximum.

Table 24: Storage conditions

Type	Condition	Unit	Reference
Air temperature: Low High	-25 +40	°C	IPC/JEDEC J-STD-033A
Humidity relative: Low High	10 90 at 40°C	%	IPC/JEDEC J-STD-033A
Air pressure: Low High	70 106	kPa	IEC TR 60271-3-1: 1K4 IEC TR 60271-3-1: 1K4
Movement of surrounding air	1.0	m/s	IEC TR 60271-3-1: 1K4
Water: rain, dripping, icing and frosting	Not allowed	---	---
Radiation: Solar Heat	1120 600	W/m ²	ETS 300 019-2-1: T1.2, IEC 68-2-2 Bb ETS 300 019-2-1: T1.2, IEC 68-2-2 Bb
Chemically active substances	Not recommended		IEC TR 60271-3-1: 1C1L
Mechanically active substances	Not recommended		IEC TR 60271-3-1: 1S1
Vibration sinusoidal: Displacement Acceleration Frequency range	1.5 5 2-9 9-200	mm m/s ² Hz	IEC TR 60271-3-1: 1M2
Shocks: Shock spectrum Duration Acceleration	semi-sinusoidal 1 50	ms m/s ²	IEC 68-2-27 Ea

5.4 Reliability Characteristics

The test conditions stated below are an extract of the complete test specifications.

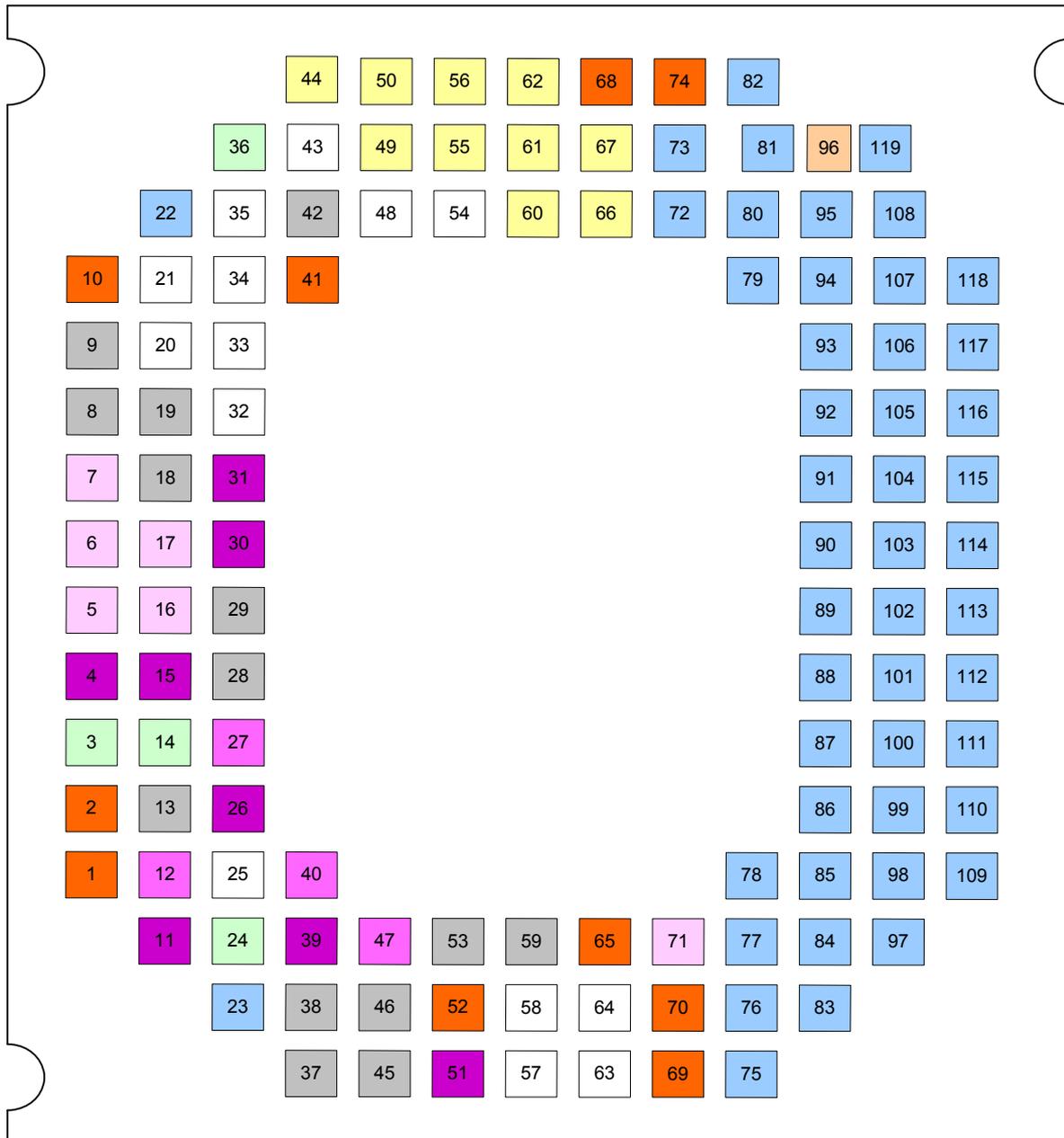
Table 25: Summary of reliability test conditions

Type of test	Conditions	Standard
Vibration	Frequency range: 10-20Hz; acceleration: 5g Frequency range: 20-500Hz; acceleration: 20g Duration: 20h per axis; 3 axes	DIN IEC 68-2-6 ¹
Shock half-sinus	Acceleration: 500g Shock duration: 1msec 1 shock per axis 6 positions (\pm x, y and z)	DIN IEC 68-2-27
Dry heat	Temperature: $+70 \pm 2^{\circ}\text{C}$ Test duration: 16h Humidity in the test chamber: $< 50\%$	EN 60068-2-2 Bb ETS 300 019-2-7
Temperature change (shock)	Low temperature: $-40^{\circ}\text{C} \pm 2^{\circ}\text{C}$ High temperature: $+85^{\circ}\text{C} \pm 2^{\circ}\text{C}$ Changeover time: $< 30\text{s}$ (dual chamber system) Test duration: 1h Number of repetitions: 100	DIN IEC 68-2-14 Na ETS 300 019-2-7
Damp heat cyclic	High temperature: $+55^{\circ}\text{C} \pm 2^{\circ}\text{C}$ Low temperature: $+25^{\circ}\text{C} \pm 2^{\circ}\text{C}$ Humidity: $93\% \pm 3\%$ Number of repetitions: 6 Test duration: 12h + 12h	DIN IEC 68-2-30 Db ETS 300 019-2-5
Cold (constant exposure)	Temperature: $-40 \pm 2^{\circ}\text{C}$ Test duration: 16h	DIN IEC 68-2-1

1. For reliability tests in the frequency range 20-500Hz the Standard's acceleration reference value was increased to 20g.

5.5 Pad Assignment and Signal Description

The SMT application interface on the EES3 provides connecting pads to integrate the module into external applications. [Figure 41](#) shows the connecting pads' numbering plan, the following [Table 26](#) lists the pads' assignments.



- Supply pads
- ASC0 pads
- RF antenna pad
- Control pads
- ASC1 pads
- Do not use
- GND pads
- SIM pads
- Analog audio pads
- Other interface pads

Figure 41: Numbering plan for connecting pads (bottom view)

Table 26: Pad assignments

Pad no.	Signal name	Pad no.	Signal name	Pad no.	Signal name
1	VDDL	41	BATTEMP	81	GND
2	VCHARGE	42	VUSB_IN	82	GND
3	EMERG_OFF	43	Do not use	83	GND
4	CTS0	44	MICN2	84	GND
5	CCRST	45	DAI3	85	GND
6	CCIO	46	DAI4	86	GND
7	CCVCC	47	CTS1	87	GND
8	USB_DP	48	Do not use	88	GND
9	USB_DN	49	EPP1	89	GND
10	VEXT	50	MICP2	90	GND
11	TXD0	51	DSR0	91	GND
12	TXD1	52	ISENSE	92	GND
13	I2CDAT_SPIDO	53	I2CCLK_SPICLK	93	GND
14	IGT	54	Do not use	94	GND
15	RXD0	55	EPN1	95	GND
16	CCIN	56	MICN1	96	RF_OUT
17	CCCLK	57	Do not use	97	GND
18	DAI6	58	Do not use	98	GND
19	DAI5	59	SPIDI	99	GND
20	Do not use	60	VMIC	100	GND
21	Do not use	61	EPP2	101	GND
22	GND	62	MICP1	102	GND
23	GND	63	Do not use	103	GND
24	SYNC	64	Do not use	104	GND
25	Do not use	65	CHARGE_GATE	105	GND
26	RTS0	66	AGND	106	GND
27	RTS1	67	EPN2	107	GND
28	SPICS	68	BATT+	108	GND
29	DAI0	69	BATT+	109	GND
30	RING0	70	VSENSE	110	GND
31	DCD0	71	CCGND	111	GND
32	Do not use	72	GND	112	GND
33	Do not use	73	GND	113	GND
34	Do not use	74	BATT+	114	GND
35	Do not use	75	GND	115	GND
36	POWER_IND	76	GND	116	GND
37	DAI2	77	GND	117	GND
38	DAI1	78	GND	118	GND
39	DTR0	79	GND	119	GND
40	RXD1	80	GND		

Please note that the reference voltages listed in [Table 27](#) are the values measured directly on the EES3 module. They do not apply to the accessories connected.

Table 27: Signal description

Function	Signal name	IO	Signal form and level	Comment
Power supply	BATT+	I	$V_{I,max} = 4.5V$ $V_{I,typ} = 3.8V$ $V_{I,min} = 3.2V$ during Tx burst on board $I \approx 2A$, during Tx burst  $n \text{ Tx} = n \times 577\mu s$ peak current every 4.616ms	Three lines of BATT+ and GND must be connected in parallel for supply purposes because higher peak currents may occur. Pads 68 and 74 are connected to module's RF power amplifier, whereas pad 69 is connected to baseband processor. Minimum voltage must not fall below 3.2V including drop, ripple, spikes.
Power supply	GND		Ground	Application Ground
Charge Interface	VCHARGE	I	$V_{I,min} = 3.1V$ $V_{I,max} = 7.00V$	This line signalizes to the processor that the charger is connected. If unused keep line open.
	BATT_TEMP	I	Connect NTC with $R_{NTC} \approx 10k\Omega$ @ 25°C to ground. See Section 3.5.3 for B value of NTC.	Battery temperature measurement via NTC resistance. NTC should be installed inside or near battery pack to enable proper charging and deliver temperature values. If unused keep line open.
	ISENSE	I	$V_{I,max} = 4.65V$ $\Delta V_{I,max}$ to $V_{BATT+} = +0.3V$ at normal condition	ISENSE is required for measuring the charge current. For this purpose, a shunt resistor for current measurement needs to be connected between ISENSE and VSENSE. If unused connect line to VSENSE.
	VSENSE	I	$V_{I,max} = 4.5V$	VSENSE must be directly connected to BATT+ at battery connector or external power supply.
	CHARGE-GATE	O	$V_{O,max} = 7.0V$ $I_{O,typ} = 5.2mA$ (for fast charging @ CHARGE-GATE = 1V)	Control line to the gate of charge FET or bipolar transistor. If unused keep line open.

Table 27: Signal description (Continued)

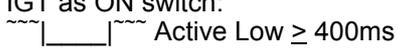
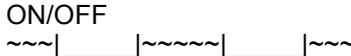
Function	Signal name	IO	Signal form and level	Comment
External supply voltage	VEXT	O	<p>Normal mode: $V_{Omin} = 2.75V$ $V_{Otyp} = 2.93V$ $V_{Omax} = 3.00V$ $I_{Omax} = -50mA$</p> <p>$C_{load,max,extern} = 1\mu F$</p>	<p>VEXT may be used for application circuits, for example to supply power for an I²C.</p> <p>If unused keep line open.</p> <p>Not available in Power-down mode. The external digital logic must not cause any spikes or glitches on voltage VEXT.</p>
Power indicator	PWR_IND	O	<p>$V_{IHmax} = 10V$ $V_{OLmax} = 0.4V$ at $I_{max} = 2mA$</p>	<p>PWR_IND (Power Indicator) notifies the module's on/off state.</p> <p>PWR_IND is an open collector that needs to be connected to an external pull-up resistor. Low state of the open collector indicates that the module is on. Vice versa, high level notifies the Power-down mode.</p> <p>Therefore, the line may be used to enable external voltage regulators which supply an external logic for communication with the module, e.g. level converters.</p>
Ignition	IGT	I	<p>Internal pull-up: $R_1 \approx 30k\Omega$, $C_1 \approx 10nF$ $V_{ILmax} = 0.8V$ at $I_{max} = -150\mu A$ $V_{OHmax} = 4.5V$ (V_{BATT+})</p> <p>IGT as ON switch:  Active Low $\geq 400ms$</p> <p>IGT as ON/OFF switch:  ON/OFF $\geq 0.4s$ $\geq 2s$ $\geq 1s$ </p>	<p>The IGT signal switches on the module. Depending on settings made with AT^SCFG, parameter "MeShutdown/OnIgnition", it may also be used as ON/OFF switch.</p> <p>This line must be driven low by an open drain or open collector driver.</p>

Table 27: Signal description (Continued)

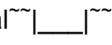
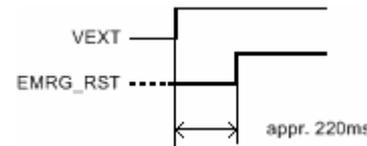
Function	Signal name	IO	Signal form and level	Comment
Emergency reset	EMERG_OFF	I	Internal pull-up: $R_I \approx 10k\Omega$ $V_{IL,max} = 0.3V$ at $I_{max} = -140\mu A$ $V_{OH,min} = 1.70V$ $V_{OH,max} = 1.90V$ Signal \sim  \sim Active Low $\geq 10ms$	Turn-off in case of emergency: Pull down and release EMERG_OFF. Falling edge turns off the module. Data stored in the volatile memory will be lost. For orderly software controlled reset rather use the AT+CFUN command (e.g. AT+CFUN=x,1). This line must be driven by open drain or open collector. If unused keep line open.
Power-on reset		O	Internal pull-up: $R_I \approx 5k\Omega$ $V_{OL,max} = 0.2V$ at $I = 2mA$ $V_{OH,min} = 1.75V$ $V_{OH,max} = 3.00V$ Reset signal driven by the module:  (see also Figure 5 and Figure 6)	Reset signal driven by the module which can be used to reset any application or device connected to the module. Only effective for approximately 220ms during the assertion of IGT when the module is about to start.
Synchronization	SYNC	O	$V_{OL,max} = 0.3V$ at $I = 0.1mA$ $V_{OH,min} = 2.3V$ at $I = -0.1mA$ $V_{OH,max} = 3.00V$  $n Tx = n \times 577\mu s$ impulse each 4.616ms, with 180 μs forward time.	There are two alternative options for using the SYNC line: a) Indicating increased current consumption during uplink transmission burst. Note that the timing of the signal is different during handover. b) Driving a status LED to indicate different operating modes of EES3. The LED must be installed in the host application. To select a) or b) use the AT^SSYNC command. If unused keep line open.
RTC backup	VDDL	I/O	$R_I \approx 1k\Omega$ $V_O,max = 4.5V$ $V_{BATT+} = 4.5V$: $V_O = 3.2V$ at $I_O = -500\mu A$ $V_{BATT+} = 0V$: $V_I = 2.7V \dots 4.5V$ at $I_{max} = 10\mu A$	If unused keep line open.

Table 27: Signal description (Continued)

Function	Signal name	IO	Signal form and level	Comment
ASC0 Serial interface	RXD0	O	$V_{OL} \text{ max} = 0.2\text{V}$ at $I = 2\text{mA}$ $V_{OH} \text{ min} = 2.55\text{V}$ at $I = -0.5\text{mA}$ $V_{OH} \text{ max} = 3.00\text{V}$ $V_{IL} \text{ max} = 0.8\text{V}$ $V_{IH} \text{ min} = 2.15\text{V}$ $V_{IH} \text{ max} = V_{EXT} \text{ min} + 0.3\text{V} = 3.05\text{V}$ Internal pull-down at TXD0: $R_I = 330\text{k}\Omega$ Internal pull-down at RTS0: $R_I = 330\text{k}\Omega$	Serial interface for AT com- mands or data stream. If unused keep lines open.
	TXD0	I		
	CTS0	O		
	RTS0	I		
	DTR0	I		
	DCD0	O		
	DSR0	O		
	RING0	O		
ASC1 Serial interface	RXD1	O	$V_{OL} \text{ max} = 0.2\text{V}$ at $I = 2\text{mA}$ $V_{OH} \text{ min} = 2.55\text{V}$ at $I = -0.5\text{mA}$ $V_{OH} \text{ max} = 3.00\text{V}$ $V_{IL} \text{ max} = 0.8\text{V}$ $V_{IH} \text{ min} = 2.15\text{V}$ $V_{IH} \text{ max} = V_{EXT} \text{ min} + 0.3\text{V} = 3.05\text{V}$ Internal pull-down at TXD1: $R_I = 330\text{k}\Omega$ Internal pull-down at RTS1: $R_I = 330\text{k}\Omega$	4-wire serial interface for AT commands or data stream. If unused keep lines open.
	TXD1	I		
	CTS1	O		
	RTS1	I		
SIM interface specified for use with 3V SIM card	CCIN	I	$R_I \approx 100\text{k}\Omega$ $V_{IL} \text{ max} = 0.6\text{V}$ at $I = -25\mu\text{A}$ $V_{IH} \text{ min} = 2.1\text{V}$ at $I = -10\mu\text{A}$ $V_O \text{ max} = 3.05\text{V}$ $R_O \approx 47\Omega$ $V_{OL} \text{ max} = 0.25\text{V}$ at $I = +1\text{mA}$ $V_{OH} \text{ min} = 2.5\text{V}$ at $I = -0.5\text{mA}$ $V_{OH} \text{ max} = 2.95\text{V}$ $R_I \approx 4.7\text{k}\Omega$ $V_{IL} \text{ max} = 0.75\text{V}$ $V_{IL} \text{ min} = -0.3\text{V}$ $V_{IH} \text{ min} = 2.1\text{V}$ $V_{IH} \text{ max} = CCVCC \text{ min} + 0.3\text{V} = 3.05\text{V}$ $R_O \approx 100\Omega$ $V_{OL} \text{ max} = 0.3\text{V}$ at $I = +1\text{mA}$ $V_{OH} \text{ min} = 2.5\text{V}$ at $I = -0.5\text{mA}$ $V_{OH} \text{ max} = 2.95\text{V}$ $R_O \approx 100\Omega$ $V_{OL} \text{ max} = 0.3\text{V}$ at $I = +1\text{mA}$ $V_{OH} \text{ min} = 2.5\text{V}$ at $I = -0.5\text{mA}$ $V_{OH} \text{ max} = 2.95\text{V}$ $V_O \text{ min} = 2.75\text{V}$ $V_O \text{ typ} = 2.85\text{V}$ $V_O \text{ max} = 2.95\text{V}$ $I_O \text{ max} = -20\text{mA}$	CCIN = Low, SIM card holder closed Maximum cable length or cop- per track 100mm to SIM card holder. All signals of SIM interface are protected against ESD with a special diode array. Usage of CCGND is manda- tory.
	CCRST	O		
	CCIO	I/O		
	CCCLK	O		
	CCVCC	O		
	CCGND			

Table 27: Signal description (Continued)

Function	Signal name	IO	Signal form and level	Comment
SIM interface specified for use with 1.8V SIM card	CCIN	I	$R_I \approx 100k\Omega$ $V_{ILmax} = 0.6V$ at $I = -25\mu A$ $V_{IHmin} = 2.1V$ at $I = -10\mu A$ $V_{Omax} = 3.05V$	CCIN = Low, SIM card holder closed
	CCRST	O	$R_O \approx 47\Omega$ $V_{OLmax} = 0.25V$ at $I = +1mA$ $V_{OHmin} = 1.45V$ at $I = -0.5mA$ $V_{OHmax} = 1.90V$	Maximum cable length or copper track 100mm to SIM card holder.
	CCIO	I/O	$R_I \approx 4.7k\Omega$ $V_{ILmax} = 0.45V$ $V_{IHmin} = 1.35V$ $V_{IHmax} = CCVCCmin + 0.3V = 2.00V$ $R_O \approx 100\Omega$ $V_{OLmax} = 0.3V$ at $I = +1mA$ $V_{OHmin} = 1.45V$ at $I = -0.5mA$ $V_{OHmax} = 1.90V$	All signals of SIM interface are protected against ESD with a special diode array.
	CCCLK	O	$R_O \approx 100\Omega$ $V_{OLmax} = 0.3V$ at $I = +1mA$ $V_{OHmin} = 1.45V$ at $I = -0.5mA$ $V_{OHmax} = 1.90V$	Usage of CCGND is mandatory.
	CCVCC	O	$V_{Omin} = 1.70V$, $V_{Otyp} = 1.80V$ $V_{Omax} = 1.90V$ $I_{Omax} = -20mA$	
	CCGND		Ground	
I ² C interface	I2CCLK_SPICLK	O	$V_{OLmax} = 0.2V$ at $I = 2mA$ $V_{OHmin} = 2.55V$ at $I = -0.5mA$ $V_{OHmax} = 3.00V$	I ² C interface is only available if the two lines are not used as SPI interface.
	I2CDAT_SPID0	I/O	$V_{OLmax} = 0.2V$ at $I = 2mA$ $V_{ILmax} = 0.8V$ $V_{IHmin} = 2.15V$ $V_{IHmax} = VEXTmin + 0.3V = 3.05V$	<p>I2CDAT is configured as Open Drain and needs a pull-up resistor in the host application.</p> <p>According to the I²C Bus Specification Version 2.1 for the fast mode a rise time of max. 300ns is permitted. There is also a maximum VOL=0.4V at 3mA specified.</p> <p>The value of the pull-up depends on the capacitive load of the whole system (I²C Slave + lines). The maximum sink current of I2CDAT and I2CCLK is 4mA.</p> <p>If unused keep lines open.</p>

Table 27: Signal description (Continued)

Function	Signal name	IO	Signal form and level	Comment
SPI Serial Periph- eral Inter- face	SPIDI	I	$V_{OLmax} = 0.2V$ at $I = 2mA$ $V_{OHmin} = 2.55V$ at $I = -0.5mA$ $V_{OHmax} = 3.00V$	If the Serial Peripheral Interface is active the I ² C interface is not available. If unused keep lines open.
	I2CDAT_SPID O	O		
	I2CCLK_SPIC LK	O	$V_{ILmax} = 0.8V$ $V_{IHmin} = 2.15V$, $V_{IHmax} = VEXTmin + 0.3V = 3.05V$	
	SPICS	O		
USB	VUSB_IN	I	$V_{INmin} = 4.0V$ $V_{INmax} = 5.25V$	If unused keep lines open.
	USB_DN	I/O	Differential Output Crossover voltage Range $V_{CRSmin} = 1.5V$, $V_{CRSmax} = 2.0V$ Line to GND: $V_{OHmax} = 3.6V$ $V_{OHtyp} = 3.2V$ $V_{OHmin} = 3.0V$ at $I=-0.5mA$ $V_{OLmax} = 0.2V$ at $I=2mA$ $V_{IHmin} = 2.24V$ $V_{ILmax} = 0.96V$ Driver Output Resistance $Z_{typ} = 32\Omega$ Pullup at USB_DP $R_{typ}=1.5k\Omega$	
	USB_DP	I/O		
Digital Audio interface	DAI0	O	$V_{OLmax} = 0.2V$ at $I = 2mA$ $V_{OHmin} = 2.55V$ at $I = -0.5mA$ $V_{OHmax} = 3.00V$ $V_{ILmax} = 0.8V$ $V_{IHmin} = 2.15V$ $V_{IHmax} = VEXTmin + 0.3V = 3.05V$	See Table 18 for details. Unused input lines should be tied to GND via pull down resistors. DAI1 requires a 47kOhm pull down resistor to be placed as close as possible to the module. Unused output lines must be left open.
	DAI1	I		
	DAI2	O		
	DAI3	O		
	DAI4	I		
	DAI5	I		
	DAI6	I		

Table 27: Signal description (Continued)

Function	Signal name	IO	Signal form and level	Comment
Analog Audio interface	VMIC	O	$V_{Omin} = 2.4V$ $V_{Otyp} = 2.5V$ $V_{Omax} = 2.6V$ $I_{max} = 2mA$	Microphone supply for customer feeding circuits
	EPP2	O	3.0Vpp differential typical @ 0dBm0	The audio output can directly operate a 32-Ohm-loud-speaker. If unused keep lines open.
	EPN2	O	4.2Vpp differential maximal @ 3.14dBm0 Measurement conditions: Audio mode: 6 Outstep 3 No load Minimum differential resp. single ended load 27Ohms	
	EPP1	O	4.2Vpp (differential) typical @ 0dBm0	The audio output can directly operate an 8-Ohm-loud-speaker. If unused keep lines open.
	EPN1	O	6.0Vpp differential maximal @ 3.14dBm0 Measurement conditions: Audio mode: 5 Outstep 4 No load Minimum differential load 7.5Ohms	
	MICP1	I	Full Scale Input Voltage: 1.6 Vpp 0dBm0 Input Voltage: 1.1 Vpp At MICN1, apply external bias from 1.0V to 1.6V. Measurement conditions: Audio mode: 5	Balanced or single ended microphone or line input with external feeding circuit (using VMIC and AGND). If unused keep lines open.
	MICN1	I		
	MICP2	I	Full Scale Input Voltage 1.6 Vpp 0dBm0 Input Voltage 1.1 Vpp At MICN2, apply external bias from 1.0V to 1.6V. Measurement conditions: Audio mode: 6	Balanced or single ended microphone or line input with external feeding circuit (using VMIC and AGND) and accessory detection circuit. If unused keep lines open.
	MICN2	I		
	AGND			Analog Ground

5.6 Power Supply Ratings

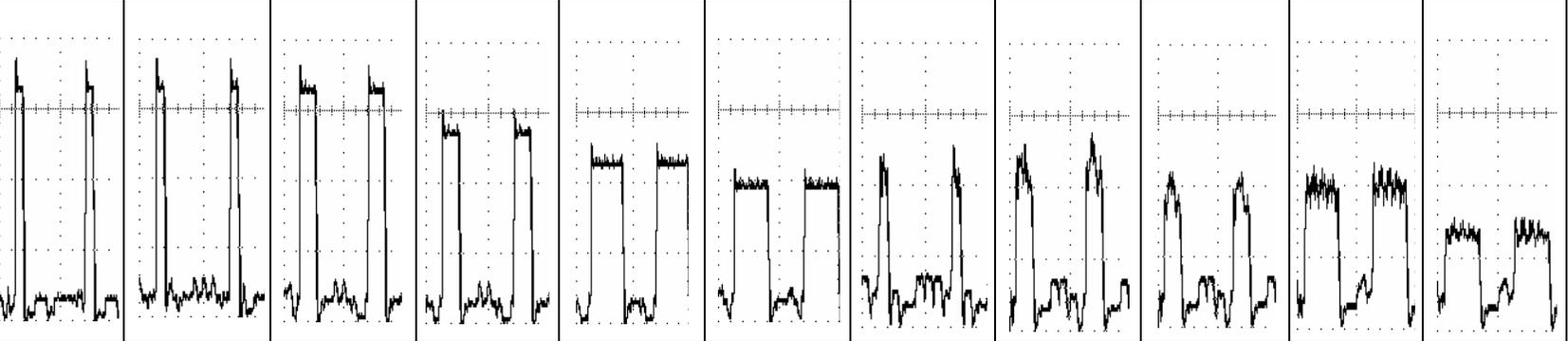
Table 28: Power supply ratings

Parameter	Description	Conditions	Min	Typ	Max	Unit
BATT+	Supply voltage	Directly measured at reference point TP BATT+ and TP GND, see Section 3.2.2 . Voltage must stay within the min/max values, including voltage drop, ripple, spikes.	3.2	3.8	4.5	V
	Voltage drop during transmit burst	Normal condition, power control level for $P_{out\ max}$			400	mV
	Voltage ripple	Normal condition, power control level for $P_{out\ max}$ @ $f < 200\text{kHz}$ @ $f > 200\text{kHz}$			50 2	mV mV
$I_{VDDL P}$	OFF State supply current	RTC backup @ BATT+ = 0V		6		μA
I_{BATT+}	OFF State supply current	POWER DOWN mode		50	100	μA
	Average standby supply current ¹	SLEEP mode @ DRX = 9		1.5		mA
		SLEEP mode @ DRX = 5		2.0		mA
		SLEEP mode @ DRX = 2		3.5		mA
IDLE mode			17		mA	

1. Additional conditions:

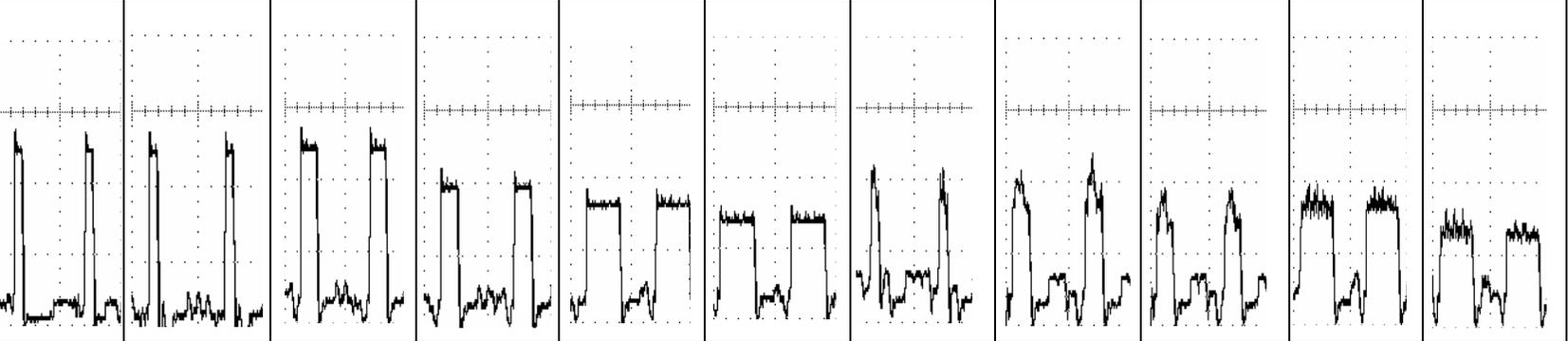
- SLEEP and IDLE mode measurements started 5 minutes after switching ON the module
- Averaging times: SLEEP mode - 3 minutes; IDLE mode - 1.5 minutes
- Communication tester settings: no neighbor cells, no cell reselection
- USB interface disabled

Table 29: Current consumption during Tx burst for GSM 850MHz and GSM 900MHz

Mode	GSM call	GPRS Class 8	GPRS Class10		GPRS Class 12		EGPRS Class 8	EGPRS Class 10		EGPRS Class 12	
Timeslot configuration	1Tx / 1Rx	1Tx / 4Rx	2Tx / 3Rx		4Tx / 1Rx		1Tx/4Rx	2Tx / 3Rx		4Tx / 1Rx	
RF power nominal	2W (33dBm)	2W (33dBm)	2W (33dBm)	1.26W (31dBm)	0.8W (29dBm)	0.5W (27dBm)	0.5W (27dBm)	0.5W (27dBm)	0.316W (25dBm)	0.5W (27dBm)	0.125W (21dBm)
Radio output power reduction with AT^SCFG, parameter <ropr>	<ropr> = 1 ... 3	<ropr> = 1 ... 3	<ropr> = 1	<ropr> = 2 or 3	<ropr> = 1	<ropr> = 2 or 3	<ropr> = 1 ... 3	<ropr> = 1or 2	<ropr> = 3	<ropr> = 1or 2	<ropr> = 3
Current characteristics											
Burst current @ 50Ω antenna (typ.)	1.9A	1.9A	1.9A	1.8A	1.5A	1.3A	1.5A	1.5A	1.3A	1.5A	950mA
Burst current @ total mismatch	3.0A	3.0A	3.0A	2.3A	1.8A	1.6A	1.8A	1.8A	1.6A	1.8A	1.1A
Average current @ 50Ω antenna (typ.)	310mA	325mA	560mA	480mA	700mA	600mA	200mA	340mA	300mA	590mA	380mA
Average current @ total mismatch	460mA	495mA	680mA	600mA	850mA	730mA	220mA	380mA	360mA	700mA	450mA

AT parameters are given in brackets <...> and marked *italic*. Test conditions: $V_{BATT} = 4.5V$, $T_{ambient} = 25^{\circ}$.

Table 30: Current consumption during Tx burst for GSM 1800MHz and GSM 1900MHz

Mode	GSM call	GPRS Class 8	GPRS Class10		GPRS Class 12		EPGRS Class 8	EGPRS Class 10		EGPRS Class 12	
Timeslot configuration	1Tx / 1Rx	1Tx / 4Rx	2Tx / 3Rx		4Tx / 1Rx		1Tx/4Rx	2Tx / 3Rx		4Tx / 1Rx	
RF power nominal	1W (30dBm)	1W (30dBm)	1W (30dBm)	0.63W (28dBm)	0.4W (26dBm)	0.25W (24dBm)	0.4W (26dBm)	0.4W (26dBm)	0.25W (24dBm)	0.4W (26dBm)	0.1W (20dBm)
Radio output power reduction with AT^SCFG, parameter <ropr>	<ropr> = 1 ... 3	<ropr> = 1 ... 3	<ropr> = 1	<ropr> = 2 or 3	<ropr> = 1	<ropr> = 2 or 3	<ropr> = 1 ... 3	<ropr> = 1or 2	<ropr> = 3	<ropr> = 1or 2	<ropr> = 3
Current characteristics											
Burst current @ 50Ω antenna (typ.)	1.5A	1.5A	1.5A	1.25A	1.1A	900mA	1A	1A	820mA	1A	650mA
Burst current @ total mismatch	1.9A	1.9A	1.9A	1.6A	1.3A	1.1A	1.2A	1.2A	950mA	1.2A	820mA
Average current @ 50Ω antenna (typ.)	230mA	255mA	400mA	350mA	510mA	445mA	200mA	290mA	260mA	490mA	320mA
Average current @ total mismatch	275mA	300mA	500mA	420mA	620mA	530mA	230mA	330mA	290mA	570mA	370mA

AT parameters are given in brackets <.> and marked *italic*. Test conditions: $V_{BATT} = 4.5V$, $T_{ambient} = 25^{\circ}$.

5.7 Electrical Characteristics of the Voiceband Part

5.7.1 Setting Audio Parameters by AT Commands

The audio modes 2 to 6 can be adjusted according to the parameters listed below. Each audio mode is assigned a separate set of parameters.

Table 31: Audio parameters adjustable by AT commands

Parameter	Influence to	Range	Gain range	Calculation
inBbcGain	MICP/MICN analogue amplifier gain of baseband controller before ADC	0...7	0...42dB	6dB steps
inCalibrate	Digital attenuation of input signal after ADC	0...32767	$-\infty$...0dB	$20 * \log(\text{inCalibrate}/32768)$
outBbcGain	EPP/EPN analogue output gain of baseband controller after DAC	0...3	0...-18dB	6dB steps
outCalibrate[n] n = 0...4	Digital attenuation of output signal after speech decoder, before summation of sidetone and DAC Present for each volume step[n]	0...32767	$-\infty$...+6dB	$20 * \log(2 * \text{outCalibrate}[n]/32768)$
sideTone	Digital attenuation of sidetone Is corrected internally by outBbcGain to obtain a constant sidetone independent of output volume	0...32767	$-\infty$...0dB	$20 * \log(\text{sideTone}/32768)$

Note: The parameters outCalibrate and sideTone accept also values from 32768 to 65535. These values are internally truncated to 32767.

5.7.2 Audio Programming Model

The audio programming model shows how the signal path can be influenced by varying the AT command parameters. The parameters *inBbcGain* and *inCalibrate* can be set with AT^SNFI. All the other parameters are adjusted with AT^SNFO.

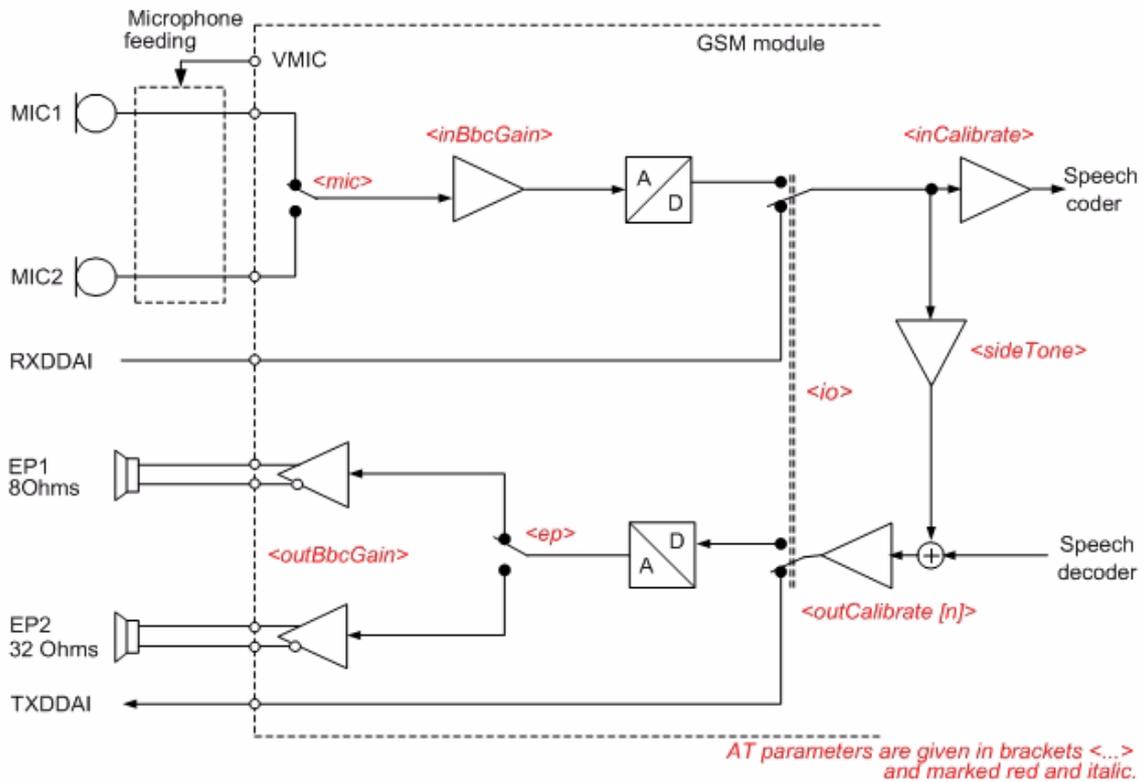


Figure 42: Audio programming model

5.7.3 Characteristics of Audio Modes

The electrical characteristics of the voiceband part depend on the current audio mode set with the AT[^]SNFS command. All values are noted for default gains e.g. all parameters of AT[^]SNFI and AT[^]SNFO are left unchanged.

Table 32: Voiceband characteristics (typical)

Audio mode no. AT [^] SNFS=	1 (Default settings, not adjustable)	2	3	4	5	6
Name	Default Handset	Basic Handsfree	Headset	User Handset	Plain Codec 1	Plain Codec 2
Purpose	DSB with Votronic handset	Car Kit	Headset	DSB with individual handset	Direct access to speech coder	Direct access to speech coder
Gain setting via AT command. Defaults:	Fix	Adjustable	Adjustable	Adjustable	Adjustable	Adjustable
inBbcGain	5	2	5	5	0	0
outBbcGain	2	2	1	2	1	0
Default audio interface	1	2	2	1	1	2
Power supply VMIC	ON	ON	ON	ON	ON	ON
Sidetone	Fix	---	Adjustable	Adjustable	Adjustable	Adjustable
Volume control	Fix	Adjustable	Adjustable	Adjustable	Adjustable	Adjustable
Echo canceller	ON	ON	ON	ON	OFF	OFF
Noise reduction	6dB	12dB	12dB	6dB	OFF	OFF
MIC input signal for 0dBm0 ¹ -10dBm0 f=1024 Hz	16mV 5mV	--- ² 90mV	18mV 16mV	16mV 5mV	400mV 126mV	400mV 126mV
EP output signal in mV rms. @ 0dBm0, 1024 Hz, no load (default gain) / @ 3.14 dBm0	660mV	240mV default @ max volume	740mV default @ max volume	660mV default @ max volume	1.47V Vpp=6.2V	1.47V Vpp=4.2V ³
Sidetone gain at default settings	21dB	-∞ dB	10.0dB	21dB	-∞ dB	-∞ dB

1. All values measured before the noise reduction attenuates the sine wave after a few seconds.

2. 0dBm0 cannot be achieved at 1024Hz due to attenuation of the frequency correction filter for the sending direction at this frequency.

3. Output voltage is limited to 4.2V.

Note: With regard to acoustic shock, the cellular application must be designed to avoid sending false AT commands that might increase amplification, e.g. for a highly sensitive earpiece. A protection circuit should be implemented in the cellular application.

5.7.4 Voiceband Receive Path

Test conditions:

- The values specified below were tested to 1kHz with default audio mode settings, unless otherwise stated.
- Default audio mode settings are: mode=5 for EPP1 to EPN1 and mode=6 for EPP2 to EPN2, outBbcGain=1 (Mode 5) or outBbcGain=0 (Mode 6), OutCalibrate=16384 (volume=4) or OutCalibrate=11585 (volume=3), sideTone=0.

Table 33: Voiceband receive path

Parameter	Min	Typ	Max	Unit	Test condition / remark
Maximum differential output voltage (peak to peak) ¹ EPP1 to EPN1		6.0 6.2		V V	8Ω, no load, Volume 4 @ 3.14 dBm0 (Full Scale) Batt+ = 3.6V
Maximum differential output voltage (peak to peak) EPP2 to EPN2		4.0 4.2		V V	32Ω, no load Volume 3 ² @ 3.14 dBm0 (Full Scale)
Nominal differential output voltage (peak to peak) EPP1 to EPN1		4.2 4.3		V V	8Ω, no load, Volume 4 @ 0 dBm0 (Nominal level)
Nominal differential output voltage (peak to peak) EPP2 to EPN2		2.8 2.9		V V	32Ω, no load Volume 3 ² @ 0 dBm0 (Nominal level)
Output bias voltage		Batt+/2		V	from EPP1 or EPN1 to AGND
Output bias voltage		1.2		V	from EPP2 or EPN2 to AGND
Differential output gain settings (gs) at 6dB stages (outBbcGain)	-18		0	dB	Set with AT^SNFO
Fine scaling by DSP (outCalibrate)	-∞		0	dB	Set with AT^SNFO
Differential output load resistance	7.5	8		Ω	From EPP1 to EPN1
Differential output load resistance	27	32		Ω	From EPP2 to EPN2
Single ended output load resistance	27	32		Ω	From EPP2 or EPN2 to AGND
Absolute gain error	-0.1		0.1	dB	outBbcGain=2
Idle channel noise ³		-83	-75	dBm0p	outBbcGain=2
Signal to noise and distortion ⁴	47			dB	outBbcGain=2

Table 33: Voiceband receive path

Parameter	Min	Typ	Max	Unit	Test condition / remark
Frequency Response ⁵					
0Hz - 100Hz			-34	dB	
200Hz		-1.1			
300Hz - 3350Hz	-0.2		0.1		
3400Hz		-0.7			
4000Hz		-39			
≥4400Hz			-75		

1. That means the differential voltage at EPP1/EPN1 for a sine wave must not exceed 3.8 Vpp at 8 Ohm. At 16 Ohm it can be 6 Vpp.
2. Full scale of EPP2/EPN2 is lower than full scale of EPP1/EPN1 but the default gain is the same.
3. 14dBm0 will lead to clipping if the default gain is used.
3. The idle channel noise was measured with digital zero signal fed to decoder. This can be realized by setting outCalibrate and sideTone to 0 during a call.
4. The test signal is a 1 kHz, 0 dbm0 sine wave.
5. This is the frequency response from a highpass and lowpass filter combination in the DAC of the base-band chip set. If the PCM interface is used, this filter is not involved in the audio path. Audio mode 1 to 4 incorporate additional frequency response correction filters in the digital signal processing unit and are adjusted to their dedicated audio devices (see [Table 32](#)).

gs = gain setting

5.7.5 Voiceband Transmit Path

Test conditions:

- The values specified below were tested to 1kHz and default audio mode settings, unless otherwise stated.
- Parameter setup: Audio mode=5 for MICP1 to MICN1 and 6 for MICP2 to MICN2, inBbcGain=0, inCalibrate=32767, sideTone=0

Table 34: Voiceband transmit path

Parameter	Min	Typ	Max	Unit	Test condition / Remark
Full scale input voltage (peak to peak) for 3.14dBm0 MICP1 to MICN1 or AGND, MICP2 to MICN2 or AGND		1.6		V	MICPx must be biased with 1.25V (VMIC/2)
Nominal input voltage (peak to peak) for 0dBm0 MICP1 to MICN1 or AGND, MICP2 to MICN2 or AGND		1.1		V	MICPx must be biased with 1.25V (VMIC/2)
Input amplifier gain in 6dB steps (inBbcGain)	0		42	dB	Set with AT^SNFI
Fine scaling by DSP (inCalibrate)	-∞		0	dB	Set with AT^SNFI
Microphone supply voltage VMIC	2.4	2.5	2.6	V	
VMIC current			2	mA	
Idle channel noise		-83	-76	dBm0p	
Signal to noise and distortion	70	77		dB	
Frequency response ¹ 0Hz - 100Hz 200Hz 300Hz - 3350Hz 3400Hz 4000Hz ≥4400Hz	-0.2	-1.1 -0.7 -39	-34 0.1 -75	dB	

1. This is the frequency response from a highpass and lowpass filter combination in the DAC of the base-band chip set. If the PCM interface is used, this filter is not involved in the audio path. Audio mode 1 to 4 incorporate additional frequency response correction filters in the digital signal processing unit and are adjusted to their dedicated audio devices (see [Table 32](#)).

5.8 Air Interface

Test conditions: All measurements have been performed at $T_{amb} = 25^{\circ}\text{C}$, $V_{BATT+ nom} = 4.0\text{V}$. The reference points used on EES3 are the BATT+ and GND contacts (test points are shown in [Figure 4](#)).

Table 35: Air interface

Parameter		Min	Typ	Max	Unit
Frequency range Uplink (MS → BTS)	GSM 850	824		849	MHz
	E-GSM 900	880		915	MHz
	GSM 1800	1710		1785	MHz
	GSM 1900	1850		1910	MHz
Frequency range Downlink (BTS → MS)	GSM 850	869		894	MHz
	E-GSM 900	925		960	MHz
	GSM 1800	1805		1880	MHz
	GSM 1900	1930		1990	MHz
RF power @ ARP with 50Ω load	GSM 850	31	33	35	dBm
	E-GSM 900 ¹	31	33	35	dBm
	GSM 1800 ²	28	30	32	dBm
	GSM 1900	28	30	32	dBm
Number of carriers	GSM 850		124		
	E-GSM 900		174		
	GSM 1800		374		
	GSM 1900		299		
Duplex spacing	GSM 850		45		MHz
	E-GSM 900		45		MHz
	GSM 1800		95		MHz
	GSM 1900		80		MHz
Carrier spacing			200		kHz
Multiplex, Duplex	TDMA / FDMA, FDD				
Time slots per TDMA frame			8		
Frame duration			4.615		ms
Time slot duration			577		μs
Modulation	GMSK				
Receiver input sensitivity @ ARP BER Class II < 2.4% (static input level)	GSM 850	-102	-108		dBm
	E-GSM 900	-102	-108		dBm
	GSM 1800	-102	-107		dBm
	GSM 1900	-102	-107		dBm

1. Power control level PCL 5
2. Power control level PCL 0

5.9 Electrostatic Discharge

The GSM module is not protected against Electrostatic Discharge (ESD) in general. Consequently, it is subject to ESD handling precautions that typically apply to ESD sensitive components. Proper ESD handling and packaging procedures must be applied throughout the processing, handling and operation of any application that incorporates a EES3 module.

Special ESD protection provided on EES3:

- SIM interface: clamp diodes for protection against overvoltage.

The remaining ports of EES3 are not accessible to the user of the final product (since they are installed within the device) and therefore, are only protected according to the "Human Body Model" requirements.

EES3 has been tested according to the EN 61000-4-2 standard. The measured values can be gathered from the following table.

Table 36: Measured electrostatic values

Specification / Requirements	Contact discharge	Air discharge
ETSI EN 301 489-1/7		
SIM interface	± 4kV	± 8kV
JEDEC JESD22-A114D		
All other interfaces	± 1kV Human Body Model	n.a.

Note: Please note that the values may vary with the individual application design. For example, it matters whether or not the application platform is grounded over external devices like a computer or other equipment, such as the Cinterion Wireless Modules reference application described in [Chapter 8](#).

6 Mechanics, Mounting and Packaging

6.1 Mechanical Dimensions of EES3

Figure 43 shows the top view of EES3 and provides an overview of the board's mechanical dimensions. For further details see Figure 44.

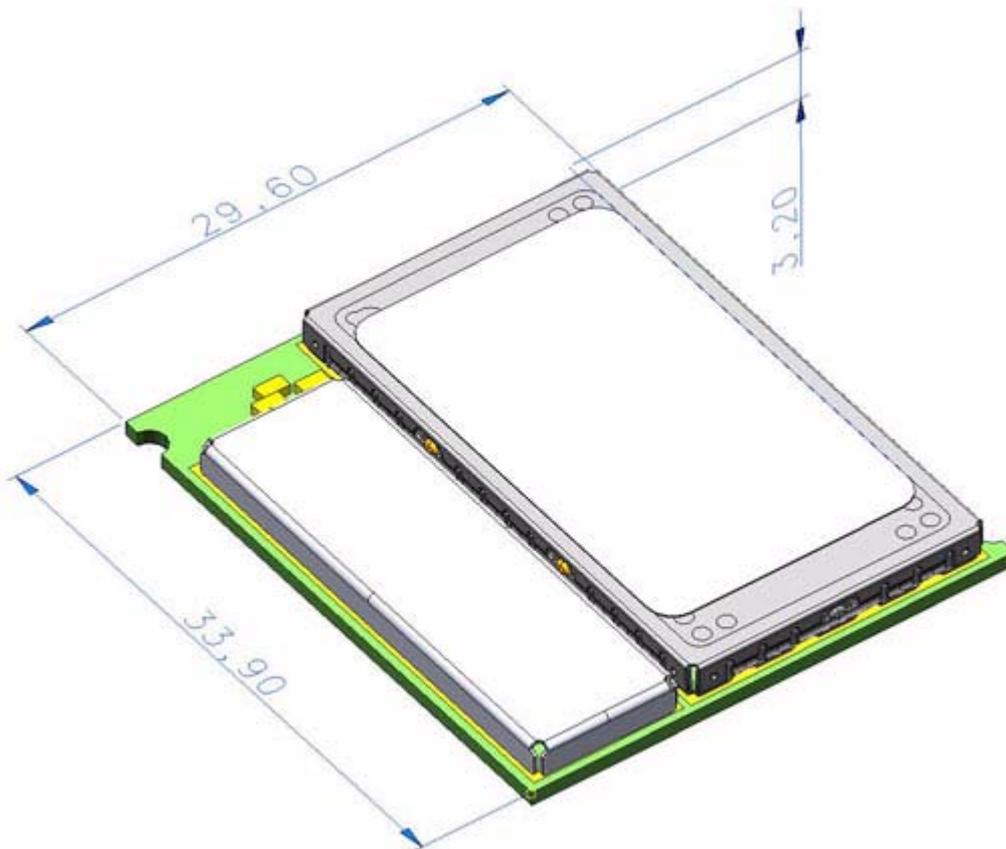


Figure 43: EES3– top view

6.2 Mounting EES3 onto the Application Platform

This section describes how to mount EES3 onto the PCBs (=printed circuit boards), including land pattern and stencil design, board-level characterization, soldering conditions, durability and mechanical handling. For more information on issues related to SMT module integration see also [11].

Note: All SMT module pads need to be soldered to the application's PCB. Not only must all supply pads and signals be connected appropriately, but all pads denoted as "Do not use" will also have to be soldered (but not electrically connected) in order to ensure the best possible mechanical stability.

6.2.1 SMT PCB Assembly

6.2.1.1 Land Pattern and Stencil

The land pattern and stencil design as shown in Figure 45 and Figure 46 is based on Cinterion characterizations for lead-free solder paste on a four-layer test PCB and a 120 micron-thick stencil.

Taking the copper pad area as base, maximum possible overprinting is 85% of this area. However, Cinterion tests have shown that for most pads an overprinting of 40% is well suited, i.e., 1.3mm x 1.3mm. An exception is the RF pad: Because of the smaller distance to the adjacent ground pads, there should be no overprinting to optimize RF performance. Figure 46 shows the recommended stencil design.

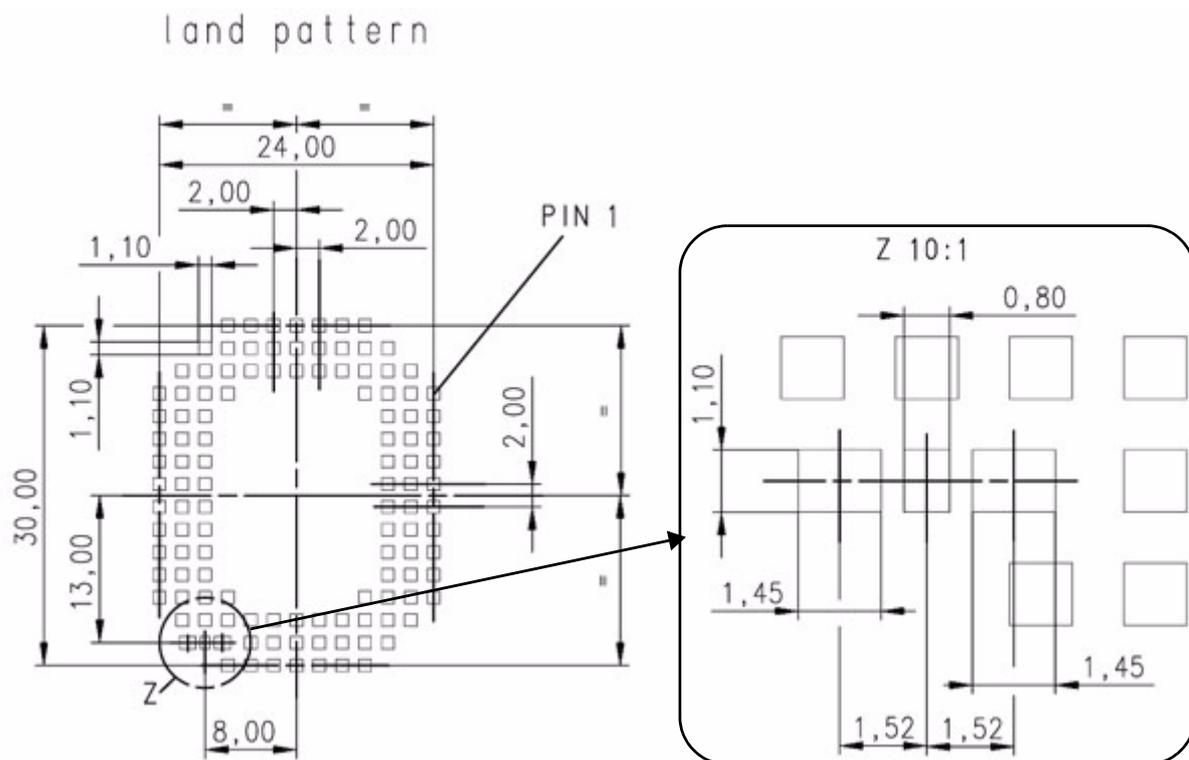


Figure 45: Land pattern (bottom view)

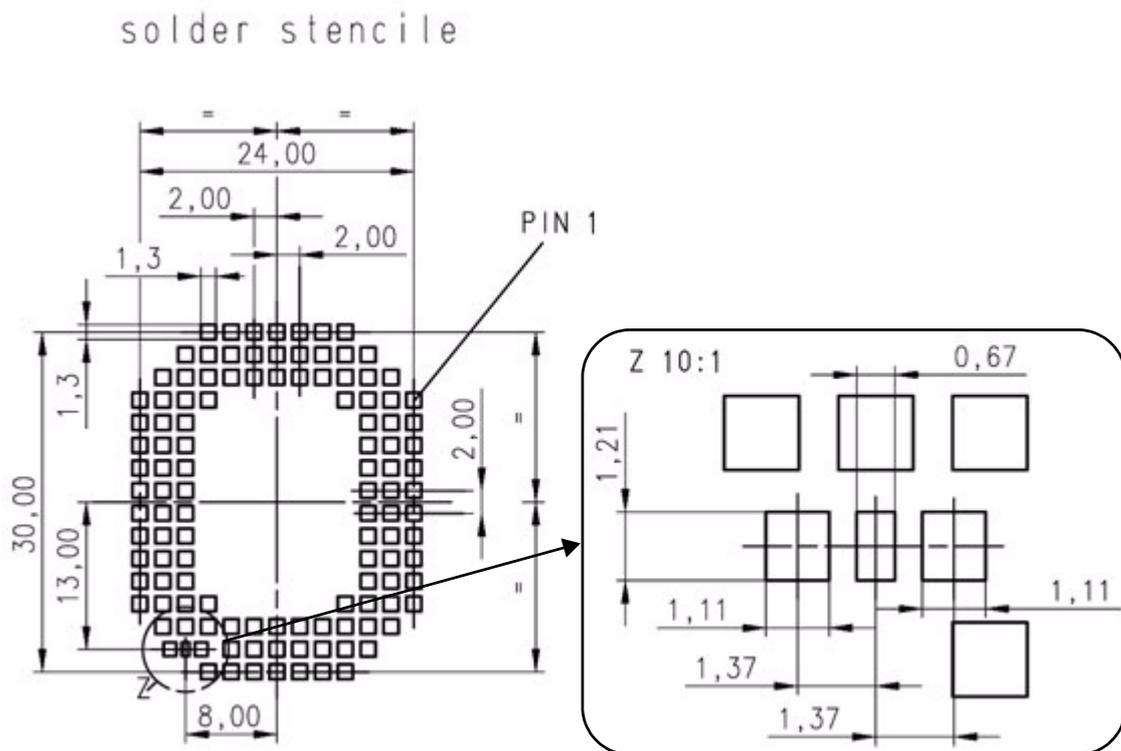


Figure 46: Recommended stencil design (bottom view)

6.2.1.2 Board Level Characterization

Board level characterization issues should also be taken into account if devising an SMT process.

Characterization tests should attempt to optimize the SMT process with regard to board level reliability. This can be done by performing the following physical tests on sample boards: Peel test, bend test, tensile pull test, drop shock test and temperature cycling. Sample surface mount checks are described in [11].

It is recommended to characterize land patterns before an actual PCB production, taking individual processes, materials, equipment, stencil design, and reflow profile into account. For land and stencil pattern design recommendations see also Section 6.2.1.1. Optimizing the solder stencil pattern design and print process is necessary to ensure print uniformity, to decrease solder voids, and to increase board level reliability.

Daisy chain modules for SMT characterization are available on request. For details refer to [11].

Generally, solder paste manufacturer recommendations for screen printing process parameters and reflow profile conditions should be followed. Maximum ratings are described in Section 6.2.3.

6.2.2 Moisture Sensitivity Level

EES3 comprises components that are susceptible to damage induced by absorbed moisture.

Cinterion's EES3 module complies with the latest revision of the IPC/JEDEC J-STD-020 Standard for moisture sensitive surface mount devices and is classified as MSL 4.

For additional MSL (=moisture sensitivity level) related information see [Section 6.2.4](#) and [Section 6.3.2](#).

6.2.3 Soldering Conditions and Temperature

6.2.3.1 Reflow Profile

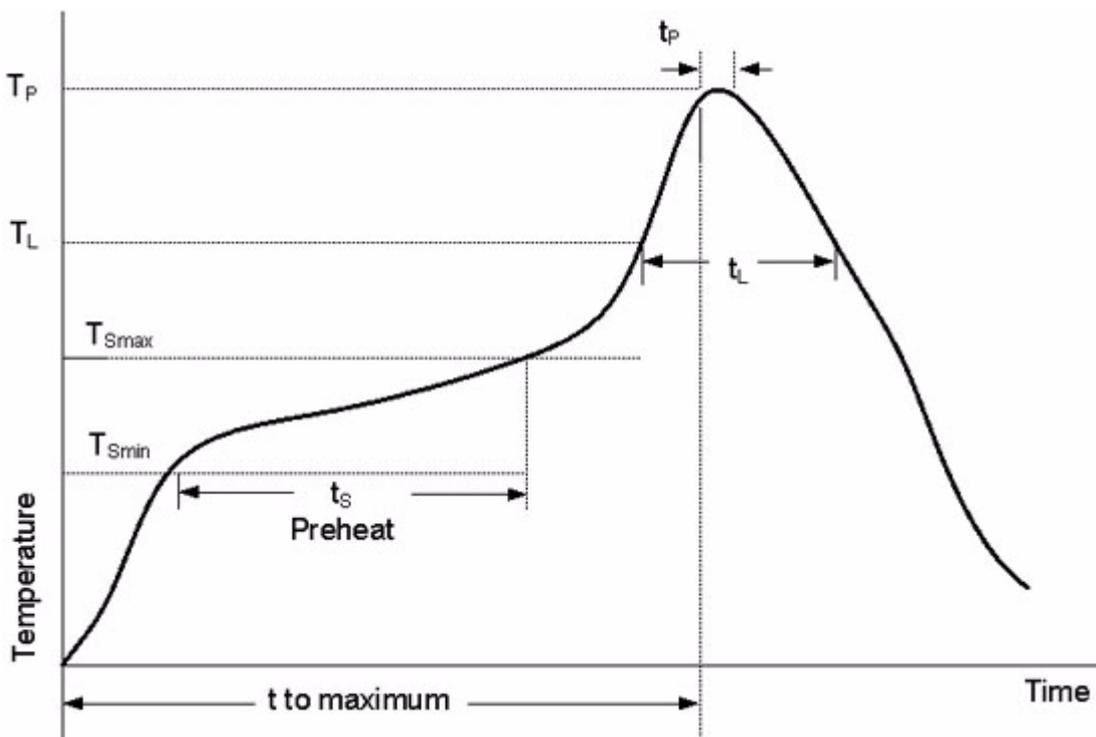


Figure 47: Reflow Profile

Table 37: Reflow temperature ratings

Profile Feature	Pb-Free Assembly
Preheat & Soak Temperature Minimum (T_{Smin}) Temperature Maximum (T_{Smax}) Time (t_{Smin} to t_{Smax}) (t_S)	150°C 200°C 60-120 seconds
Average ramp up rate (T_{Smax} to T_P)	3K/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	217°C 60-90 seconds
Peak package body temperature (T_P)	245°C +0/-5°C
Time (t_P) within 5 °C of the peak package body temperature (T_P)	30 seconds max.
Average ramp-down rate (T_P to T_{Smax})	6 K/second max.
Time 25°C to maximum temperature	8 minutes max.

6.2.3.2 Maximum Temperature and Duration

The following limits are recommended for the SMT board-level soldering process to attach the module:

- A maximum module temperature of 245°C. This specifies the temperature as measured at the module's top side.
- A maximum duration of 30 seconds at this temperature.

Please note that while the solder paste manufacturers' recommendations for best temperature and duration for solder reflow should generally be followed, the limits listed above must not be exceeded.

EES3 is specified for one soldering cycle only. Once EES3 is removed from the application, the module will very likely be destroyed and cannot be soldered onto another application.

6.2.4 Durability and Mechanical Handling

6.2.4.1 Storage Life

EES3 modules, as delivered in tape and reel carriers, must be stored in sealed, moisture barrier anti-static bags. The shelf life in a sealed moisture bag is an estimated 12 month. However, such a life span requires a non-condensing atmospheric environment, ambient temperatures below 40°C and a relative humidity below 90%. Additional storage conditions are listed in [Table 24](#).

6.2.4.2 Processing Life

EES3 must be soldered to an application within 72 hours after opening the MBB (=moisture barrier bag) it was stored in.

As specified in the IPC/JEDEC J-STD-033 Standard, the manufacturing site processing the modules should have ambient temperatures below 30°C and a relative humidity below 60%.

6.2.4.3 Baking

Baking conditions are specified on the moisture sensitivity label attached to each MBB (see [Figure 52](#) for details):

- It is *not necessary* to bake EES3, if the conditions specified in [Section 6.2.4.1](#) and [Section 6.2.4.2](#) were not exceeded.
- It is *necessary* to bake EES3, if any condition specified in [Section 6.2.4.1](#) and [Section 6.2.4.2](#) was exceeded.

If baking is necessary, the modules must be put into trays that can be baked to at least 125°C. Devices should not be baked in tape and reel carriers at any temperature.

6.2.4.4 Electrostatic Discharge

ESD (=electrostatic discharge) may lead to irreversible damage for the module. It is therefore advisable to develop measures and methods to counter ESD and to use these to control the electrostatic environment at manufacturing sites.

Please refer to [Section 5.9](#) for further information on electrostatic discharge.

6.3 Packaging

6.3.1 Tape and Reel

The single-feed tape carrier for EES3 is illustrated in Figure 48. The figure also shows the proper part orientation. The tape width is 56 mm and the EES3 modules are placed on the tape with a 36-mm pitch. The reels are 330mm in diameter with 150mm hubs. Each reel contains 300 modules.

6.3.1.1 Orientation

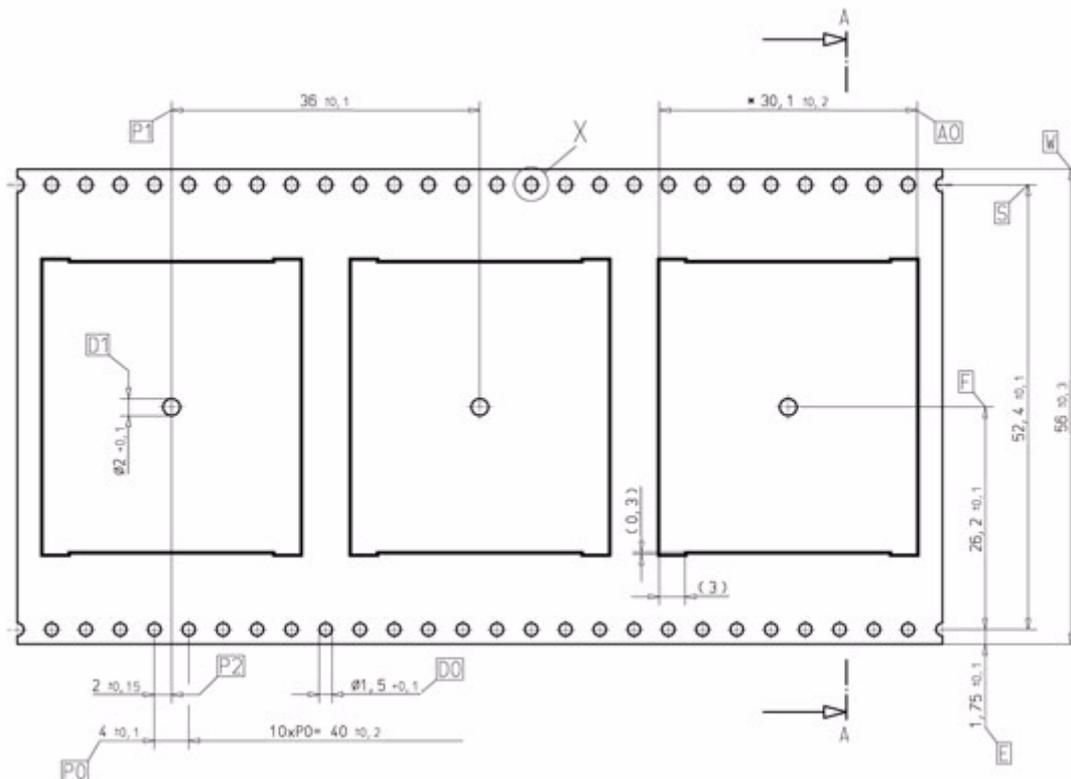


Figure 48: Carrier tape

Reel direction of the completely equipped tape

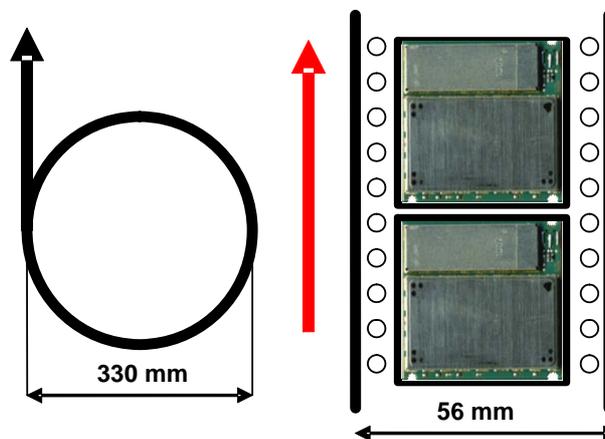


Figure 49: Reel direction

6.3.1.2 Barcode Label

A barcode label provides detailed information on the tape and its contents. It is attached to the reel.

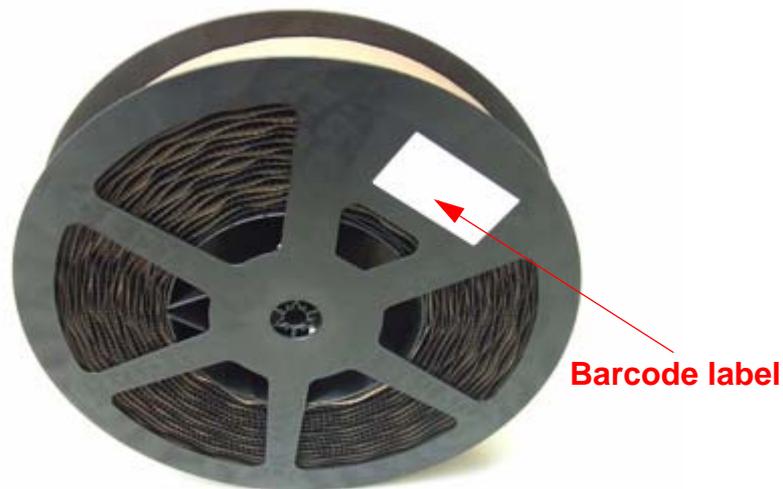


Figure 50: Barcode label on tape reel

6.3.2 Shipping Materials

EES3 is distributed in tape and reel carriers. The tape and reel carriers used to distribute EES3 are packed as described below, including the following required shipping materials:

- Moisture barrier bag, including desiccant and humidity indicator card
- Transportation bag

6.3.2.1 Moisture Barrier Bag

The tape reels are stored inside an MBB (=moisture barrier bag), together with a humidity indicator card and desiccant pouches - see [Figure 51](#). The bag is ESD protected and delimits moisture transmission. It is vacuum-sealed and should be handled carefully to avoid puncturing or tearing. The bag protects the EES3 modules from moisture exposure. It should not be opened until the devices are ready to be soldered onto the application.

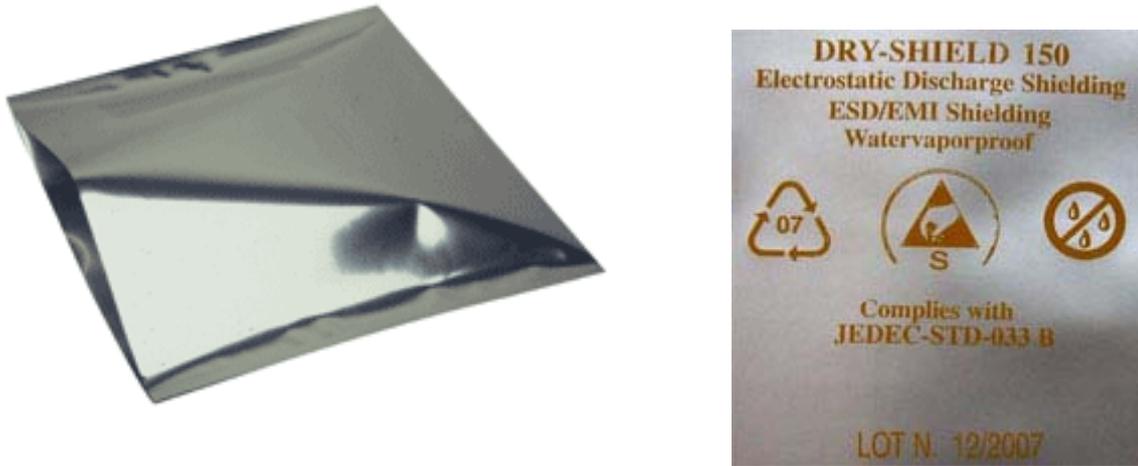


Figure 51: Moisture barrier bag (MBB) with imprint

The label shown in [Figure 52](#) summarizes requirements regarding moisture sensitivity, including shelf life and baking requirements. It is attached to the outside of the moisture barrier bag.



CAUTION

This bag contains

MOISTURE-SENSITIVE DEVICES

LEVEL

4

If blank, see adjacent bar code label

1. Calculated shelf life in sealed bag: months at < 40 °C and < 90% relative humidity (RH)
2. Peak package body temperature: 245 °C
If blank, see adjacent bar code label
3. After bag is opened, devices that will be subjected to reflow solder or other high temperature process must
 - a) Mounted within: 72 hours of factory
If blank, see adjacent bar code label
conditions < 30 °C/60%
 - b) stored at < 10% RH
4. Devices require bake, before mounting, if:
 - a) Humidity Indicator Card is > 10% when read at 23 ± 5 °C
 - b) 3a or 3b not met
5. If baking is required, device may be baked for 48 hours at 125 ± 5 °C

Note: If device containers cannot be subjected to high temperature or shorter bake times are desired, reference IPC/JEDEC J-STD-033 for bake procedure

Bag Seal Date: 01.01.2009
If blank, see adjacent bar code label

Note: Level and body temperature defined by IPC/JEDEC J-STD-020

CINTERION

INFO2 DEVICE PART NUMBER

Peak package body temperature: 245 °C Qty.: 300

Mounted within: 72 hours of factory

Bag Seal Date (MMDDYY) : **0 1 0 1 2 0 0 9**



Package ID: **WM8 0 0 0 1 2 3 4 1 2**



Figure 52: Moisture Sensitivity Label

MBBs contain one or more desiccant pouches to absorb moisture that may be in the bag. The humidity indicator card described below should be used to determine whether the enclosed components have absorbed an excessive amount of moisture.

The desiccant pouches should not be baked or reused once removed from the MBB.

The humidity indicator card is a moisture indicator and is included in the MBB to show the approximate relative humidity level within the bag. Sample humidity cards are shown in [Figure 53](#). If the components have been exposed to moisture above the recommended limits, the units will have to be rebaked.

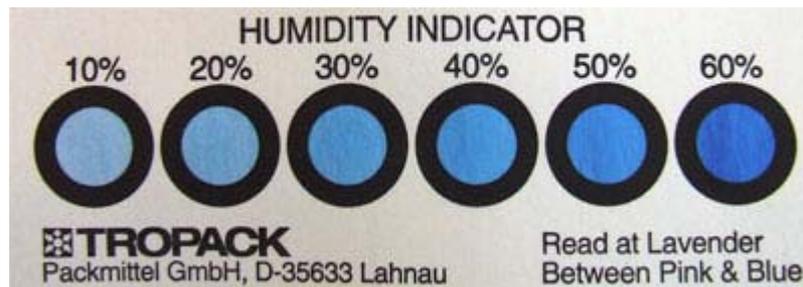


Figure 53: Humidity Indicator Card - HIC

A baking is required if the humidity indicator inside the bag indicates 10% RH or more.

6.3.2.2 Transportation Box

Tape and reel carriers are distributed in a box, marked with a barcode label for identification purposes. A box contains two reels with 300 modules each.

7 Sample Application

Figure 54 shows a typical example of how to integrate a EES3 module into the GSM part of a mobile application. Usage of the various host interfaces depends on the desired features of the application.

Audio interface 1 demonstrates the balanced connection of microphone and earpiece. This solution is particularly well suited for internal transducers. Audio interface 2 uses an unbalanced microphone and earpiece connection typically found in headset applications.

The charging circuit is optimized for the charging stages (trickle charging and software controlled charging) as well as the battery and charger specifications described in Section 3.5.

The PWR_IND line is an open collector that needs an external pull-up resistor which connects to the voltage supply VCC μ C of the microcontroller. Low state of the open collector pulls the PWR_IND signal low and indicates that the EES3 module is active, high level notifies the Power-down mode.

If the module is in Power-down mode avoid current flowing from any other source into the module circuit, for example reverse current from high state external control lines. Therefore, the controlling application must be designed to prevent reverse flow. This is not necessary for the USB interface.

If the I2C bus is active the two lines I2CCLK and I2DAT are locked for use as SPI lines. Vice versa, the activation of the SPI locks both lines for I2C. Settings for either interface are made by using the AT^SSPI command.

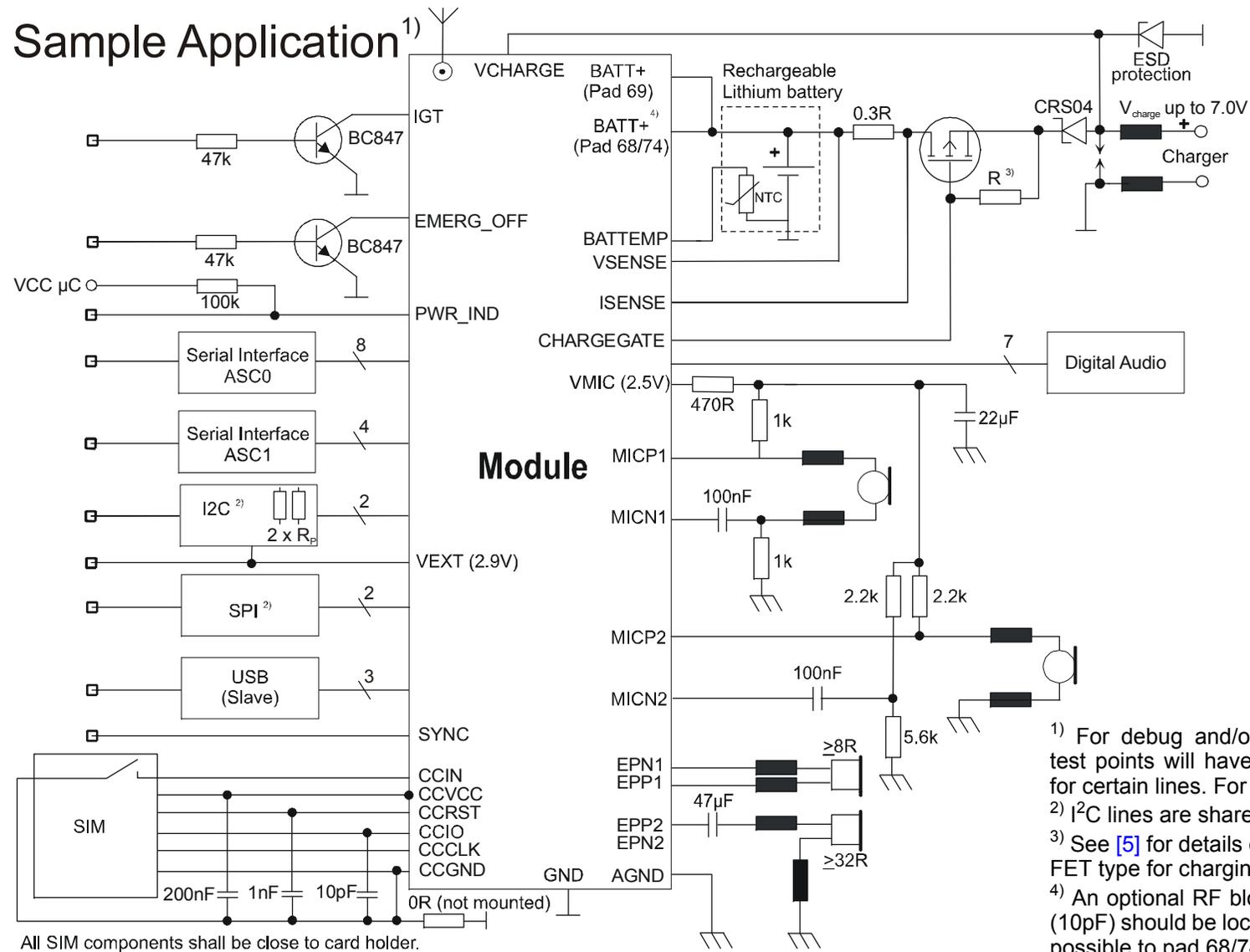
The internal pull-up resistors (R_p) of the I2C interface can be connected to an external power supply or to the VEXT line of EES3. The advantage of using VEXT is that when the module enters the Power-down mode, the I2CI interface is shut down as well. If you prefer to connect the resistors to an external power supply, take care that the interface is shut down when the PWR_IND signal goes high in Power-down mode.

While developing SMT applications it is strongly recommended to provide test points for certain signals resp. lines to and from the module - for debug and/or test purposes. The SMT application should allow for an easy access to these signals. For details on how to implement test points see [11].

The EMC measures are best practice recommendations. In fact, an adequate EMC strategy for an individual application is very much determined by the overall layout and, especially, the position of components. For example, mounting the internal acoustic transducers directly on the PCB eliminates the need to use the ferrite beads shown in the sample schematic. However, when connecting cables to the module's interfaces it is strongly recommended to add appropriate ferrite beads for reducing RF radiation.

Disclaimer

No warranty, either stated or implied, is provided on the sample schematic diagram shown in Figure 54 and the information detailed in this section. As functionality and compliance with national regulations depend to a great amount on the used electronic components and the individual application layout manufacturers are required to ensure adequate design and operating safeguards for their products using EES3 modules.



- 1) For debug and/or test purposes test points will have to be provided for certain lines. For details see [11].
- 2) I²C lines are shared with SPI
- 3) See [5] for details on size of R and FET type for charging circuit.
- 4) An optional RF blocking capacitor (10pF) should be located as close as possible to pad 68/74.

Figure 54: EES3 sample application

8 Reference Approval

8.1 Reference Equipment for Type Approval

The Cinterion Wireless Modules reference setup submitted to type approve EES3 consists of the following components:

- Cinterion Wireless Module EES3 (mounted on adapter)
- Development Support Box DSB75
- SIM card reader integrated on DSB75
- U.FL-R-SMT antenna connector and U.FL-LP antenna cable
- Handset type Votronic HH-SI-30.3/V1.1/0
- Li-Ion battery (capacity: 1200mAh)
- PC as MMI

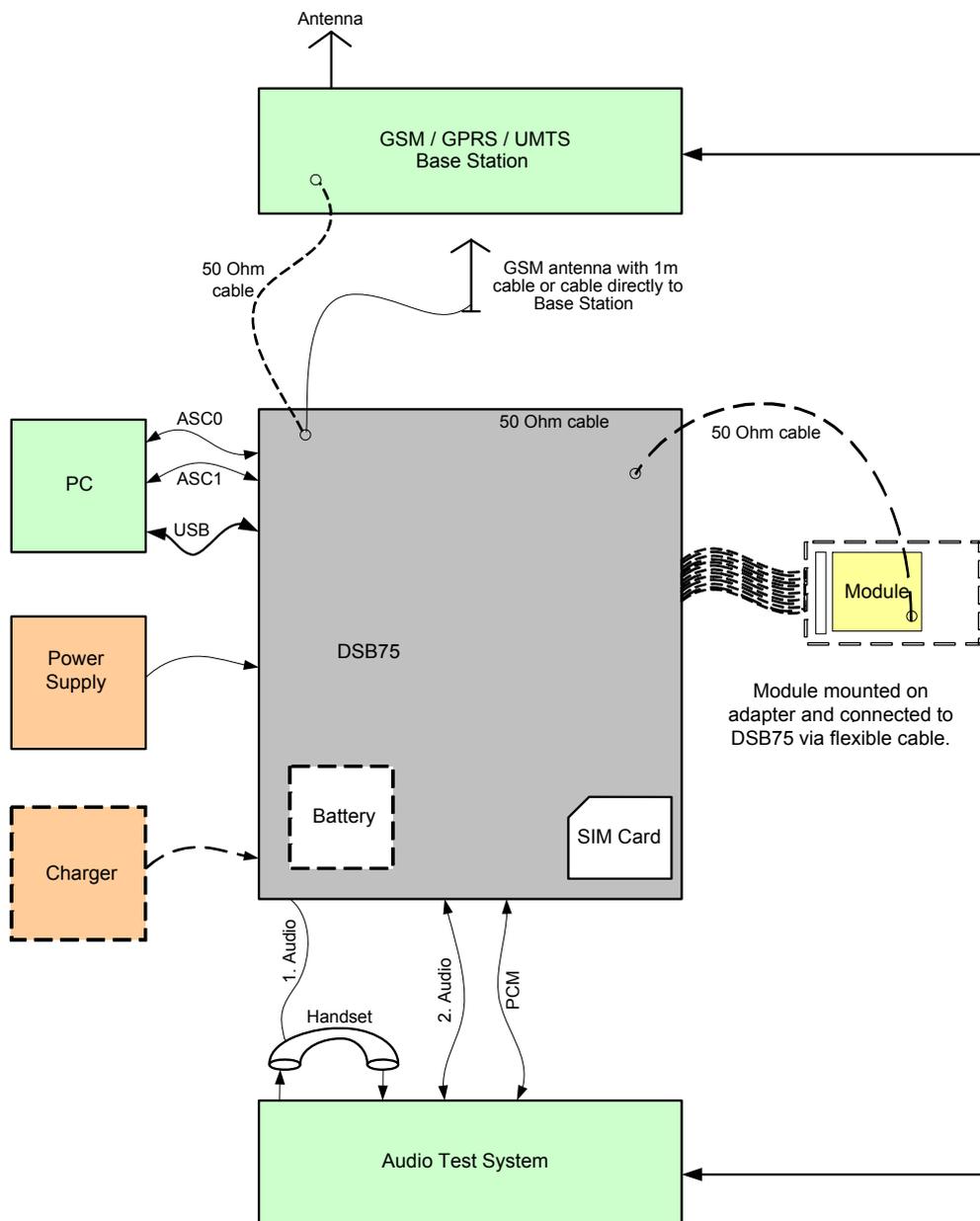


Figure 55: Reference equipment for Type Approval

8.2 Compliance with FCC and IC Rules and Regulations

The Equipment Authorization Certification for the Cinterion Wireless Modules reference application described in [Section 8.1](#) will be registered under the following identifiers:

FCC Identifier: QIPEES3

Industry Canada Certification Number: 7830A-EES3

Granted to Cinterion Wireless Modules GmbH

Manufacturers of mobile or fixed devices incorporating EES3 modules are authorized to use the FCC Grants and Industry Canada Certificates of the EES3 modules for their own final products according to the conditions referenced in these documents. In this case, an FCC/ IC label of the module shall be visible from the outside, or the host device shall bear a second label stating "Contains FCC ID QIPEES3", and accordingly "Contains IC 7830A-EES3".

IMPORTANT:

Manufacturers of portable applications incorporating EES3 modules are required to have their final product certified and apply for their own FCC Grant and Industry Canada Certificate related to the specific portable mobile. This is mandatory to meet the SAR requirements for portable mobiles (see [Section 1.3.2](#) for detail).

Changes or modifications not expressly approved by the party responsible for compliance could void the user's authority to operate the equipment.

The EES3 reference application registered under the above identifiers is certified to be in accordance with the following Rules and Regulations of the Federal Communications Commission (FCC) and Industry Canada Certificate (IC):

FCC Section 15.105 (b)

"This equipment has been tested and found to comply with the limits for a Class B digital device, pursuant to part 15 of the FCC Rules. These limits are designed to provide reasonable protection against harmful interference in a residential installation. This equipment generates, uses and can radiate radio frequency energy and, if not installed and used in accordance with the instructions, may cause harmful interference to radio communications. However, there is no guarantee that interference will not occur in a particular installation. If this equipment does cause harmful interference to radio or television reception, which can be determined by turning the equipment off and on, the user is encouraged to try to correct the interference by one or more of the following measures:

- Reorient or relocate the receiving antenna.
- Increase the separation between the equipment and receiver.
Connect the equipment into an outlet on a circuit different from that to which the receiver is connected.
- Consult the dealer or an experienced radio/TV technician for help."

FCC Section 15.19 Labelling requirements

"This device complies with Part 15 of the FCC Rules.

Operation is subject to the following two conditions:

1. This device may not cause harmful interference, and
2. This device must accept any interference received, including interference that may cause undesired operation."

FCC RF Radiation Exposure Statement

"This equipment complies with FCC RF radiation exposure limits set forth for an uncontrolled environment. The antenna used for this transmitter must be installed to provide a separation distance of at least 20 cm from all persons and must not be co-located or operating in conjunction with any other antenna or transmitter."

IC

"This Class B digital apparatus complies with Canadian ICES-003. Cet appareil numérique de la classe B est conforme à la norme NMB-003 du Canada."

If the final product is not approved for use in U.S. territories the application manufacturer shall take care that the 850 MHz and 1900 MHz frequency bands be deactivated and that band settings be inaccessible to end users. If these demands are not met (e.g. if the AT interface is accessible to end users), it is the responsibility of the application manufacturer to always ensure that the application be FCC approved regardless of the country it is marketed in. The frequency bands can be set using the command

```
AT^SCFG="Radio/Band"[,<rbp>][, <rba>]
```

A detailed command description can be found in [\[1\]](#).

9 Appendix

9.1 List of Parts and Accessories

Table 38: List of parts and accessories

Description	Supplier	Ordering information
EES3	Cinterion	Standard module (CWM IMEI): Cinterion ordering number: L30960-N1500-A100 Customer IMEI mode: (CS IMEI) Cinterion ordering number: L30960-N1505-A100
DSB75 Evaluation Kit	Cinterion	Ordering number: L36880-N8811-A100
Votronic Handset	VOTRONIC	Votronic HH-SI-30.3/V1.1/0 VOTRONIC Entwicklungs- und Produktionsgesellschaft für elektronische Geräte mbH Saarbrücker Str. 8 66386 St. Ingbert Germany Phone: +49-(0)6 89 4 / 92 55-0 Fax: +49-(0)6 89 4 / 92 55-88 Email: contact@votronic.com
SIM card holder incl. push button ejector and slide-in tray	Molex	Ordering numbers: 91228 91236 Sales contacts are listed in Table 39 .
U.FL-R-SMT antenna connector	Hirose or Molex	Sales contacts are listed in Table 40 .

Table 39: Molex sales contacts (subject to change)

<p>Molex For further information please click: http://www.molex.com</p>	<p>Molex Deutschland GmbH Felix-Wankel-Str. 11 4078 Heilbronn-Biberach Germany Phone: +49-7066-9555 0 Fax: +49-7066-9555 29 Email: mxgermany@molex.com</p>	<p>American Headquarters Lisle, Illinois 60532 U.S.A. Phone: +1-800-78MOLEX Fax: +1-630-969-1352</p>
<p>Molex China Distributors Beijing, Room 1319, Tower B, COFCO Plaza No. 8, Jian Guo Men Nei Street, 100005 Beijing P.R. China Phone: +86-10-6526-9628 Phone: +86-10-6526-9728 Phone: +86-10-6526-9731 Fax: +86-10-6526-9730</p>	<p>Molex Singapore Pte. Ltd. Jurong, Singapore Phone: +65-268-6868 Fax: +65-265-6044</p>	<p>Molex Japan Co. Ltd. Yamato, Kanagawa, Japan Phone: +81-462-65-2324 Fax: +81-462-65-2366</p>

Table 40: Hirose sales contacts (subject to change)

<p>Hirose Ltd. For further information please click: http://www.hirose.com</p>	<p>Hirose Electric (U.S.A.) Inc 2688 Westhills Court Simi Valley, CA 93065 U.S.A. Phone: +1-805-522-7958 Fax: +1-805-522-3217</p>	<p>Hirose Electric GmbH Herzog-Carl-Strasse 4 73760 Ostfildern Germany Phone: +49-711-456002-1 Fax: +49-711-456002-299 Email: info@hirose.de</p>
<p>Hirose Electric UK, Ltd Crownhill Business Centre 22 Vincent Avenue, Crownhill Milton Keynes, MK8 OAB Great Britain Phone: +44-1908-305400 Fax: +44-1908-305401</p>	<p>Hirose Electric Co., Ltd. 5-23, Osaki 5 Chome, Shinagawa-Ku Tokyo 141 Japan Phone: +81-03-3491-9741 Fax: +81-03-3493-2933</p>	<p>Hirose Electric Co., Ltd. European Branche First class Building 4F Beechavenue 46 1119PV Schiphol-Rijk Netherlands Phone: +31-20-6557-460 Fax: +31-20-6557-469</p>